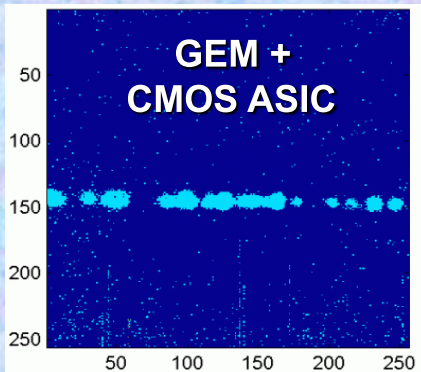
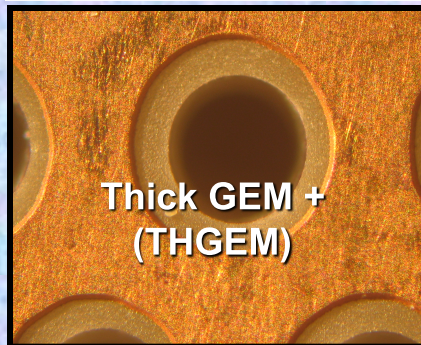
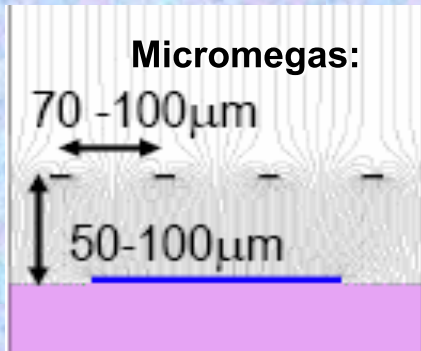


The RD51 Collaboration, Development of Micro-Pattern Gas Detector Technologies

Maxim Titov, CEA Saclay, France



- SEMINAR OUTLINE:**
- **RD51 Motivation and Main Objectives**
 - **Micro-Pattern Gas Detectors (GEM, Micromegas, Thick GEM)**
 - **RD51 Collaboration Activities and Results**
 - **Summary and Outlook**

Research Technique Seminar, Fermilab, December 1, 2009

RD51 Collaboration: Motivation and Main Objectives

World-wide coordination of the research in the field to advance technological development of Micropattern Gas Detectors

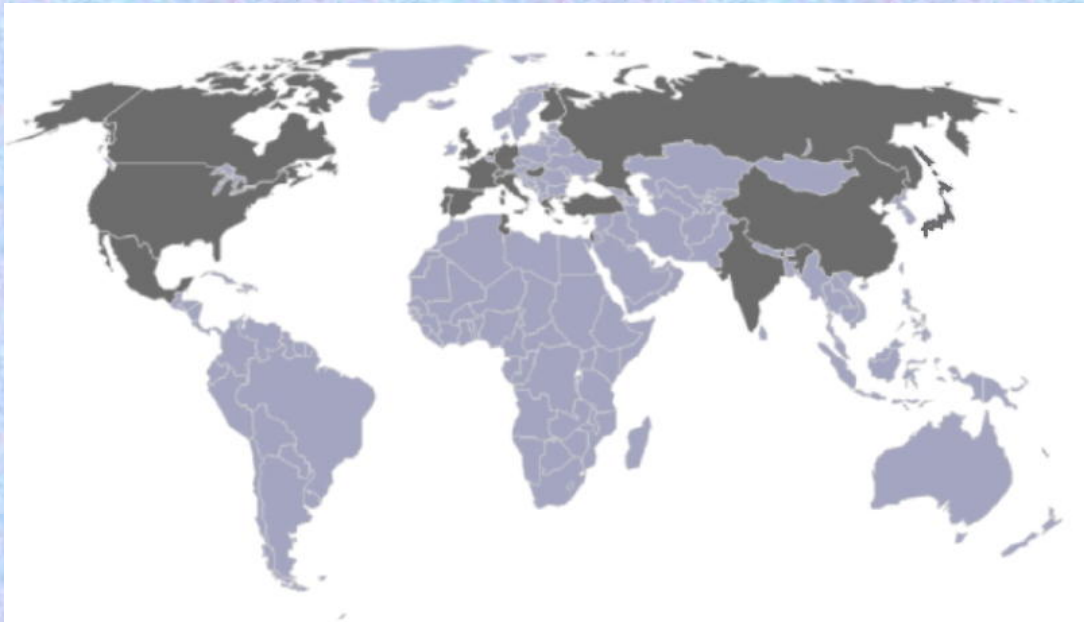
- **Foster collaboration between different R&D groups; optimize communication and sharing of knowledge/experience/results concerning MPGD technology within and beyond the particle physics community**
- **Investigate world-wide needs of different scientific communities in the MPGD technology**
- **Optimize finances by creation of common projects (e.g. technology and electronics development) and common infrastructure (e.g. test beam and radiation hardness facilities, detectors and electronics production facilities)**
- **The RD51 collaboration will steer ongoing R&D activities but will not direct the effort and direction of individual R&D projects**
- **Applications area will benefit from the technological developments developed by the collaborative effort; however the responsibility for the completion of the application projects lies with the institutes themselves.**

RD51 Collaboration Milestones

- **CERN MPGD workshop (10-11 September 2007)**
[Micro Pattern Gas Detectors. Towards an R&D Collaboration. \(10-11 September 2007\)](#)
- **1st draft of the proposal presentation during Nikhef meeting (17 April 2008)**
[Micro-Pattern Gas Detectors \(RD-51\) Workshop, Nikhef, April 16-18, 2008](#)
[Gas detectors advance into a second century - CERN Courier](#)
- **Proposal presentation in CERN/LHCC open session (2 July 2008)**
[94th LHCC Meeting Agenda \(02-03 July 2008\);](#)
[CERN-LHCC-2008-011 \(LHCC-P-011\)](#)
- **CERN/LHCC committee close session (24 September 2008)**
[Meeting with LHCC referees \(23 September 2008\); LHCC-095 minutes](#)
- **2nd RD51 Collaboration meeting (Paris 13-15 October 2008)**
[2nd RD51 Collaboration Meeting \(13-15 October 2008\)](#)
- **CERN Research Board approval(5 December 2008)**
[186th Research Board meeting minutes](#)
- [WG2 meeting \(10 December 2008\)](#)
- [WG1 meeting: large area MPGDs \(21 January 2009\)](#)
- [GEM & Micromegas detector assembly training session \(16 February 2009\)](#)
- [RD51 Mini-Week \(27-29 April 2009\)](#)
- [3rd RD51 Collaboration Meeting \(Kolympari, Crete, June 16-17, 2009\) and MPGD2009 Conference](#)
- [RD51 Mini-Week \(CERN, September 23-25, 2009\)](#)
- [4th RD51 Collaboration Meeting \(CERN, Nov. 23-25, 2009\)](#)



RD 51 : Development of Micro-Pattern Gas Detector Technologies



Collaboration of ~70 institutes worldwide, ~ 400 authors

“RD51 aims at facilitating the development of advanced gas-avalanche detector technologies and associated electronic-readout systems, for applications in basic and applied research.”

Co-Spokespersons: L.Ropelewski, M.Titov
CB Chair and Deputy: S.Dalla Torre, A. White
Management Board members: A.Breskin, I.Giomataris, F.Sauli, H. Taureg, H. van der Graaf, A.White

Collaboration Meetings:

1st - Amsterdam April 16-18, 2008 : <http://indico.cern.ch/conferenceDisplay.py?confId=25069>

2nd - Paris, October 13-15, 2008 : <http://indico.cern.ch/conferenceDisplay.py?confId=35172>

3rd - Crete (Greece), June 12-16, 2009 : <http://candia.inp.demokritos.gr/mpgd2009/>

4th – CERN, November 23-25, 2009 : <http://indicobeta.cern.ch/conferenceDisplay.py?confId=72610>

Public Web Site: <http://rd51-public.web.cern.ch/RD51-Public>

RD 51 Collaboration - Working Groups

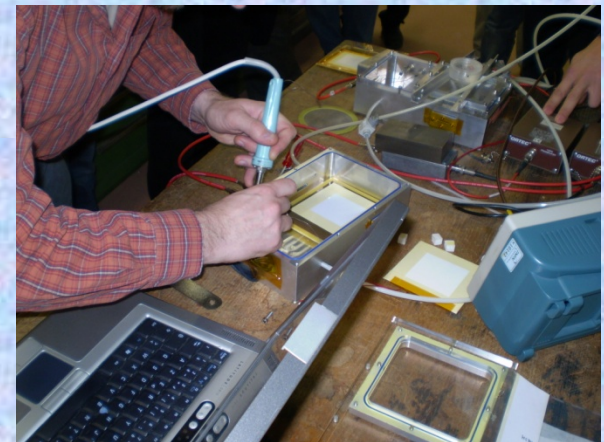
“Transverse organization” of MPGD activities in 7 Working Groups

RD51 – Micropattern Gas Detectors

| | WG1 MPGD Technology & New Structures | WG2 Characterization | WG3 Applications | WG4 Software & Simulation | WG5 Electronics | WG6 Production | WG7 Common Test Facilities |
|-----------------------------------|---|---|---|---|--|--|--|
| Objectives | Design optimization Development of new geometries and techniques | Common test standards Characterization and understanding of physical phenomena in MPGD | Evaluation and optimization for specific applications | Development of common software and documentation for MPGD simulations | Readout electronics optimization and integration with MPGD detectors | Development of cost-effective technologies and industrialization | Sharing of common infrastructure for detector characterization |
| Tasks | Large Area MPGDs | Common Test Standards | Tracking and Triggering | Algorithms | FE electronics requirements definition | Common Production Facility | Testbeam Facility |
| | Design Optimization New Geometries Fabrication | Discharge Protection | Photon Detection | | General Purpose Pixel Chip | | |
| | | Ageing & Radiation Hardness | Calorimetry | Simulation Improvements | Large Area Systems with Pixel Readout | | |
| | Development of Rad-Hard Detectors | Charging up and Rate Capability | Cryogenic Detectors | Common Platform (Root, Geant4) | Portable Multi-Channel System | Industrialization | |
| Development of Portable Detectors | Study of Avalanche Statistics | X-Ray and Neutron Imaging | Electronics Modeling | | Discharge Protection Strategies | Collaboration with Industrial Partners | |
| | | | Astroparticle Physics Appl. | | | | Irradiation Facility |
| | | | Medical Applications | | | | |
| | | | Synchrotron Rad. Plasma Diagn. Homeland Sec. | | | | |

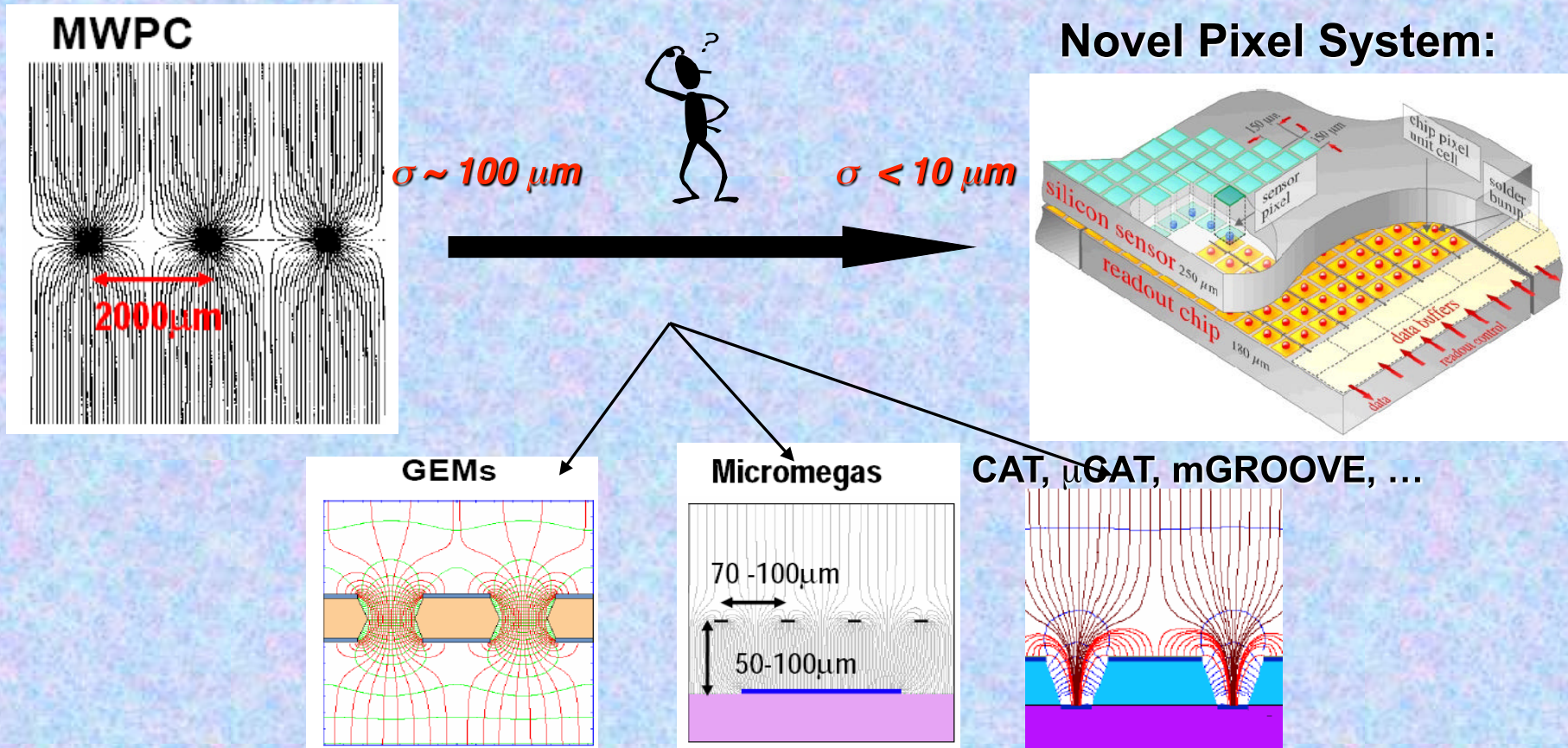
RD51 / MPGD Training Session

February 16-20, 2009 @ CERN: GEM and Micromegas detector design and assembly training - lecture session



<http://rd51-public.web.cern.ch/RD51-Public/Meetings/TrainingSessions.html>

Closing the Gap between Wire Chambers and Silicon Detectors



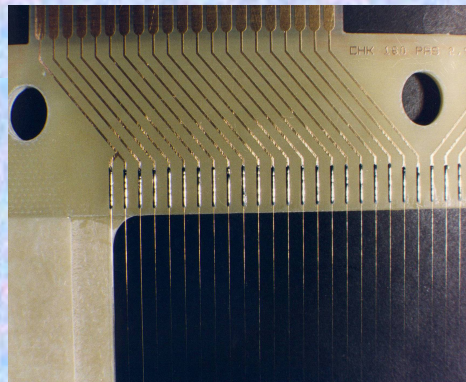
Evolution is always driven by the physics requirements and experimental conditions

→ Trade-offs between read-out, S/N, power, and segmentation
(Often defined by state-of-the-art in microelectronics or etching technology):

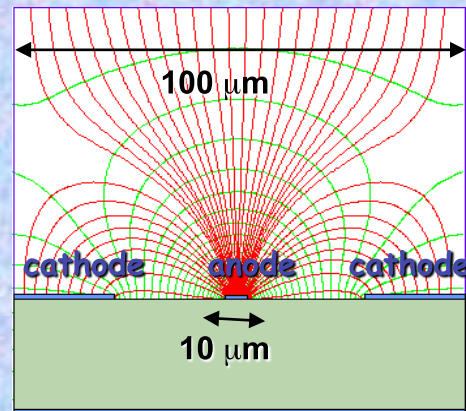
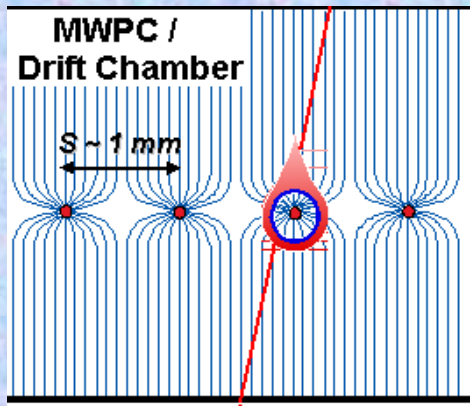
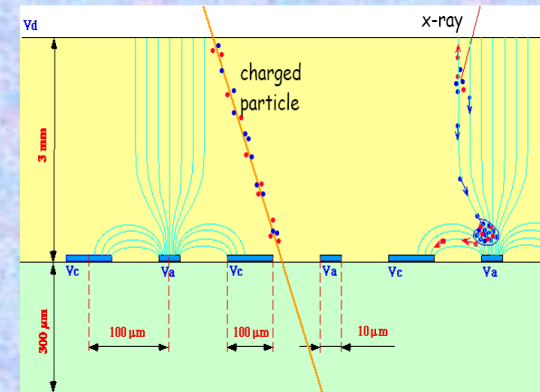
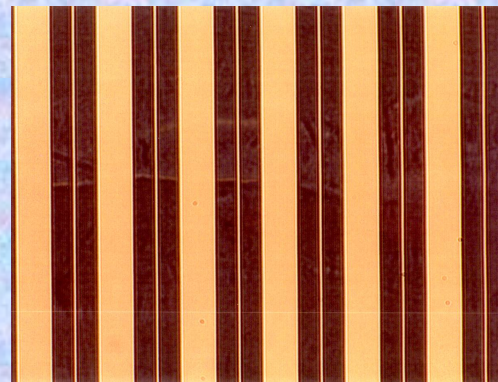
- Microelectronics – eg. Silicon pixels
- Bump bonding technology – low capacitance connections
- **Modern etching technology – eg. Micro pattern Gaseous Detectors**

Micro-Strip Gas Chamber (MSGC)

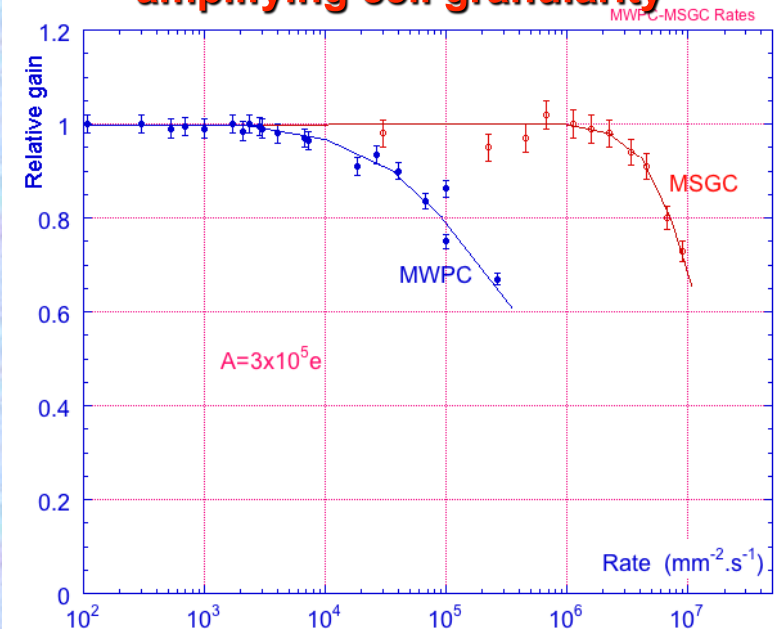
MWPC



MSGC



Rate capability limit due to space charge overcome by increased amplifying cell granularity

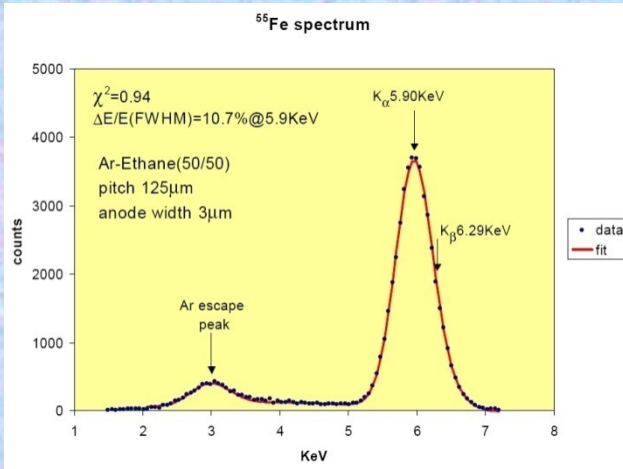


Typical distance between wires limited to 1 mm due to mechanical and electrostatic forces

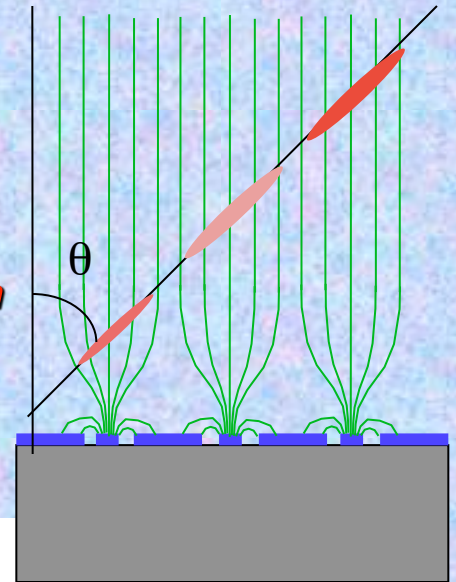
Typical distance between anodes 200 μm thanks to semiconductor etching technology

MSGC Performance

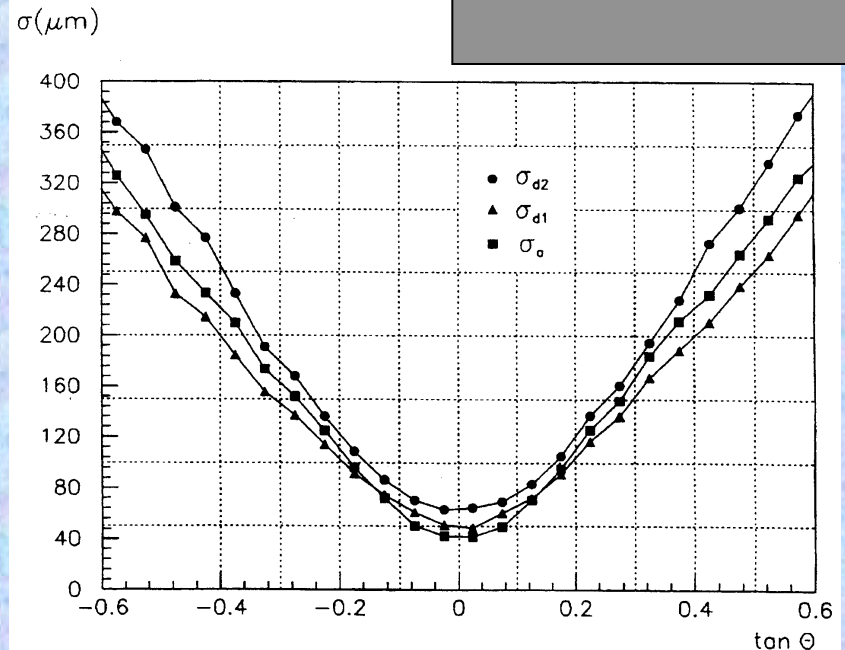
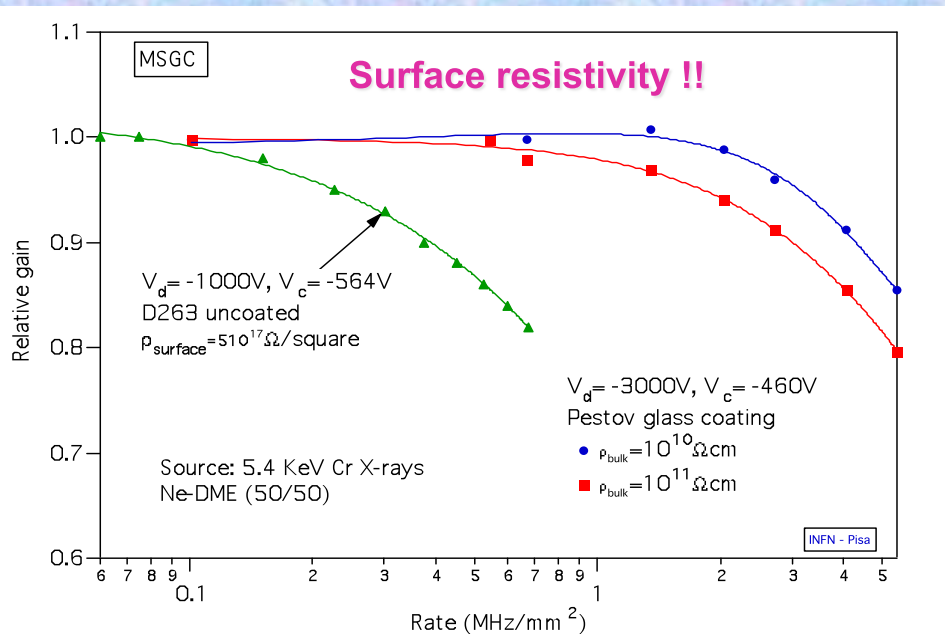
EXCELLENT RATE CAPABILITY, SPATIAL AND MULTI-TRACK RESOLUTION



**RATE CAPABILITY > 10⁶/mm² s
 SPACE ACCURACY ~ 40 μm rms
 2-TRACK RESOLUTION ~ 400 μm**



ENERGY RESOLUTION ~11% for 5.9 keV

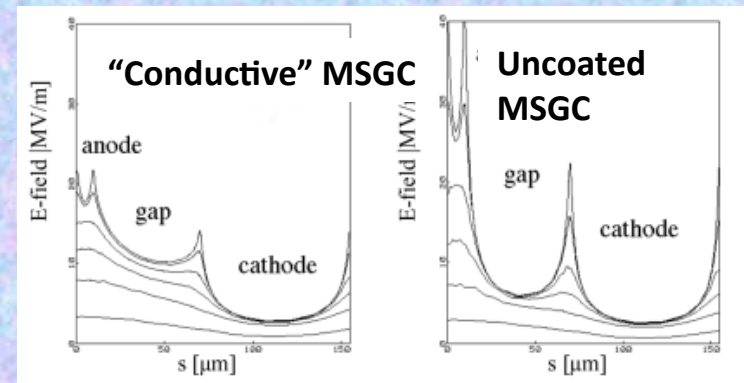
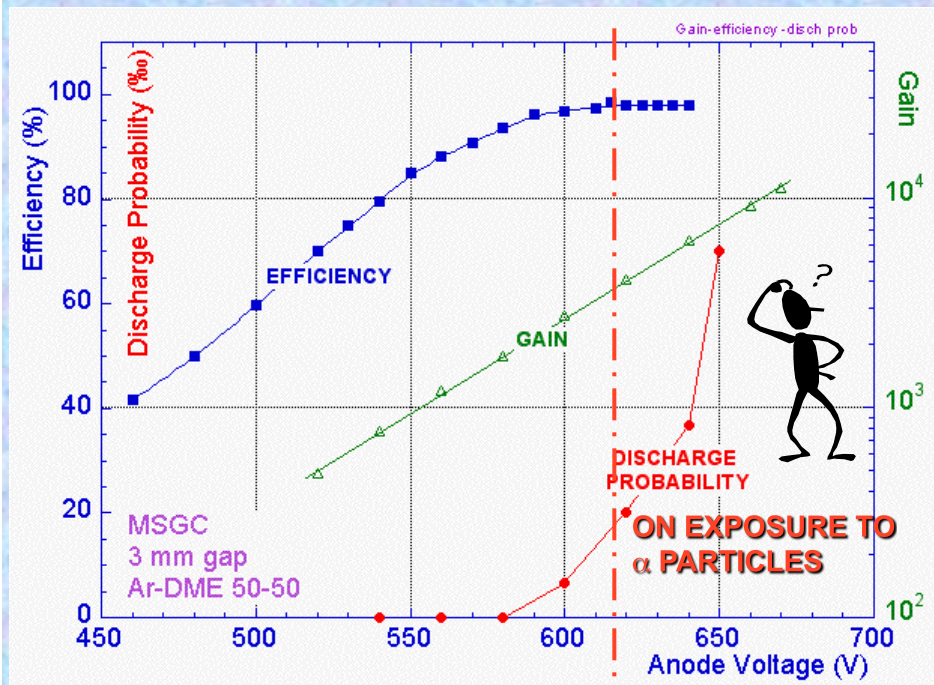


F. Van den Berg et al, NIMA A349 (1994) 438

Micro-Strip Gas Chambers: Discharge Problems

Major processes leading at high rates to MSGC operating instabilities:

- Substrate charging-up and time-dependent modification of the E field
→ slightly conductive support

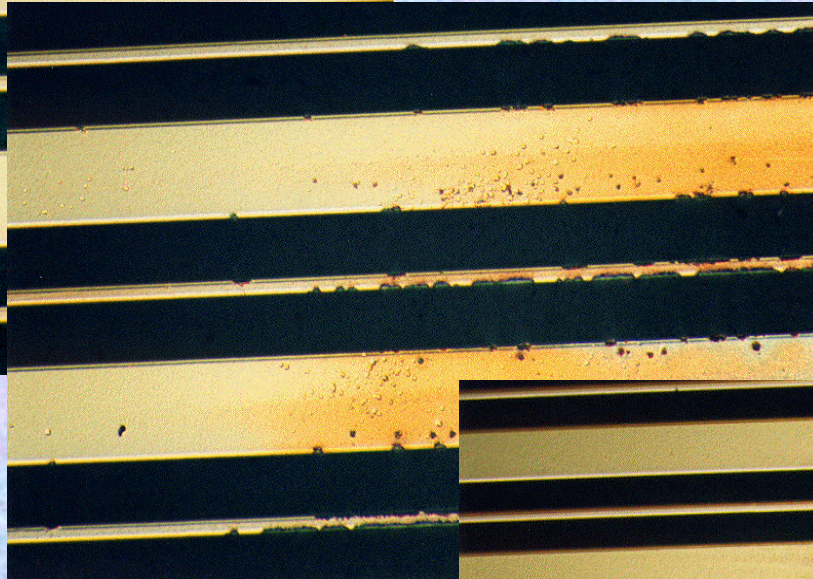
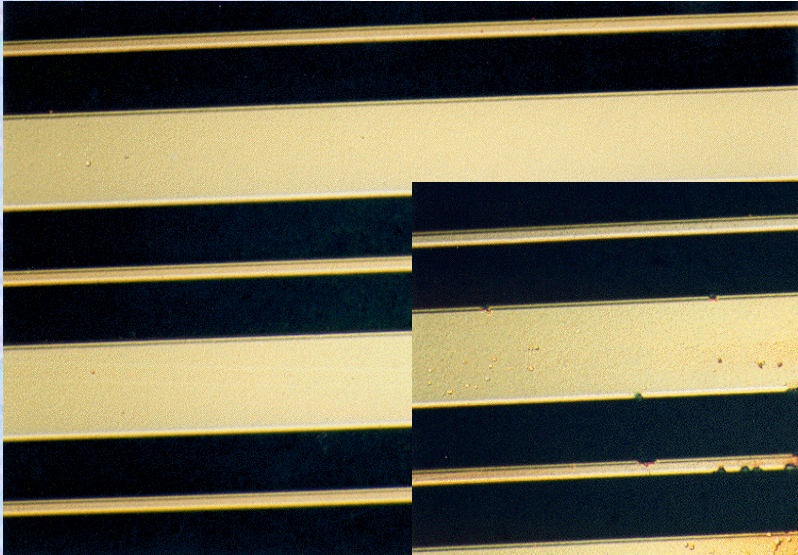


- Deposition of polymers (aging)
→ validation of gases, materials, gas systems
- Discharges under exposure to highly ionizing particles
→ multistage amplification, resistive anodes

Induced discharges are intrinsic property of all single stage micropattern detectors in hadronic beams (MSGC turned out to be prone to irreversible damages)

MSGC Discharge Problems

*Discharge is very fast (~ns)
Difficult to predict or prevent*



MICRODISCHARGES

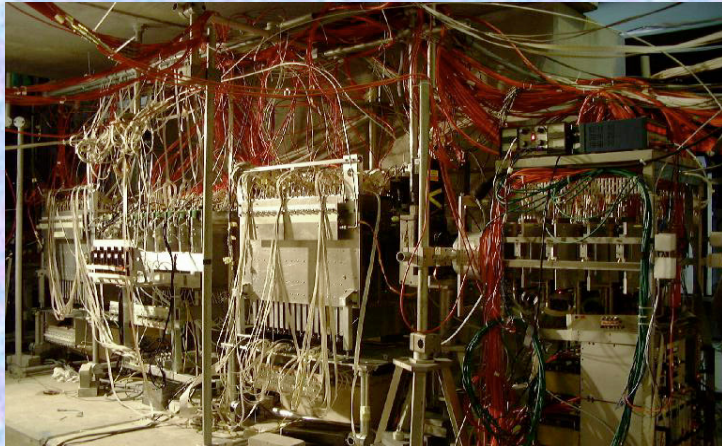
Owing to very small distance between anode and cathode the transition from proportional mode to streamer can be followed by spark, discharge, if the avalanche size exceeds
RAETHER'S LIMIT
 $Q \sim 10^7 - 10^8$ electrons



FULL BREAKDOWN



Micro-Strip Gas Chamber (MSGC)



Telescope of **32 MSGCs**
tested at PSI in Nov99
(CMS Milestone)



**The D20 diffractometer MSGC
is working since Sept 2000**

1D localisation

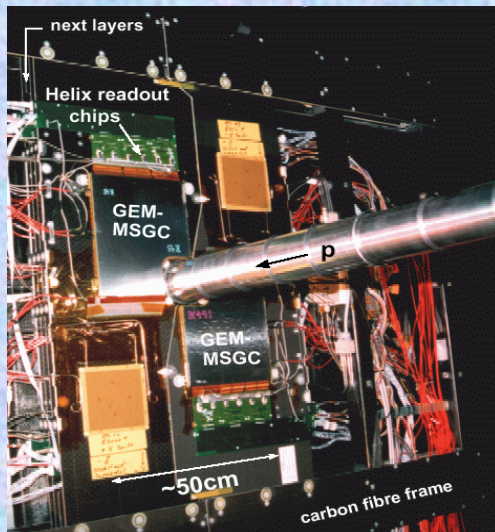
48 MSGC plates (8 cm x 15 cm)

Substrate: Schott S8900

Angular coverage : $160^\circ \times 5,8^\circ$

Position resolution : 2.57 mm ($0,1^\circ$)

5 cm gap; 1.2 bar CF4 + 2.8 bars 3He



**HERA-B Inner Tracker
MSGC-GEM detectors**

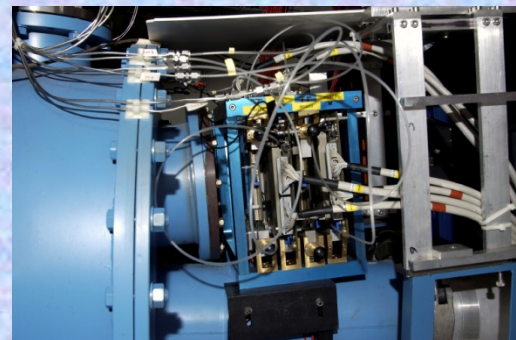
$R_{\min} \sim 6 \text{ cm}$

$\Rightarrow 10^6 \text{ particles/cm}^2 \cdot \text{sec}$

300 mm pitch

184 chambers: max $25 \times 25 \text{ cm}^2$

$\sim 10 \text{ m}^2$; 140.000 channels



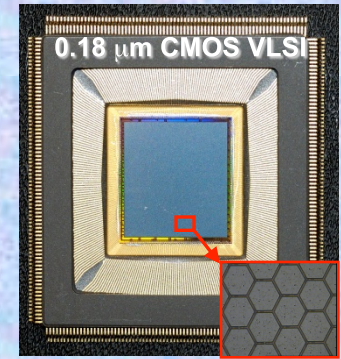
DIRAC

4 planes MSGC-GEM

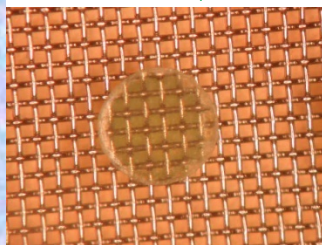
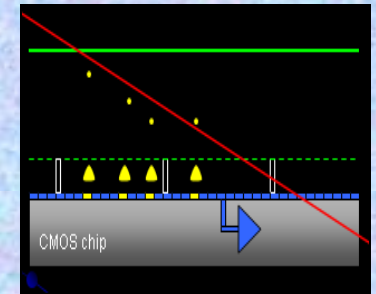
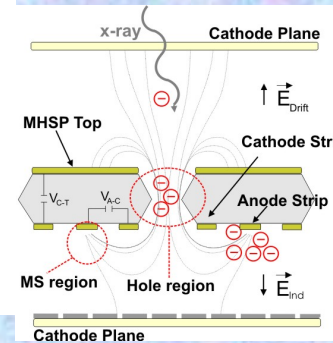
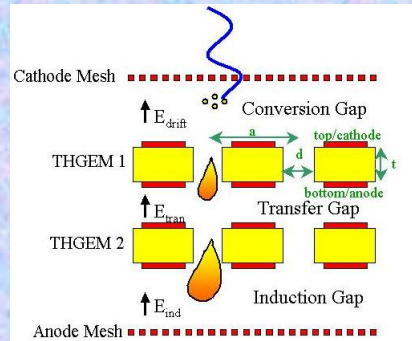
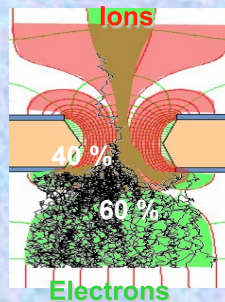
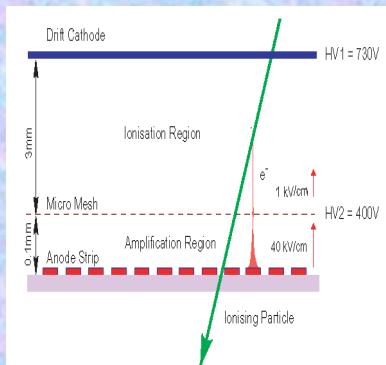
Planes $10 \times 10 \text{ cm}^2$

Current Trends in Micro-Pattern Gas Detectors (Technologies)

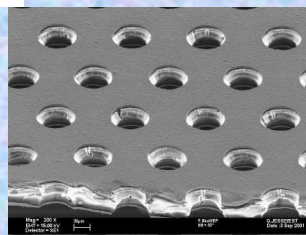
- **Micromegas**
- **GEM**
- **Thick-GEM, Hole-Type Detectors and RETGEM**
- **MPDG with CMOS pixel ASICs**
- **Ingrid Technology**



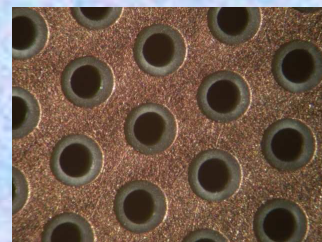
CMOS high density readout electronics



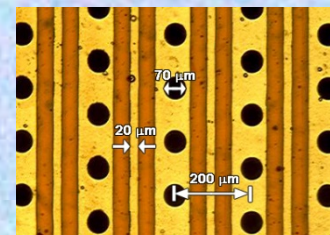
Micromegas



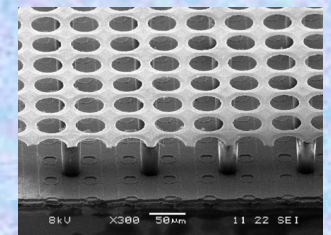
GEM



THGEM



MHSP



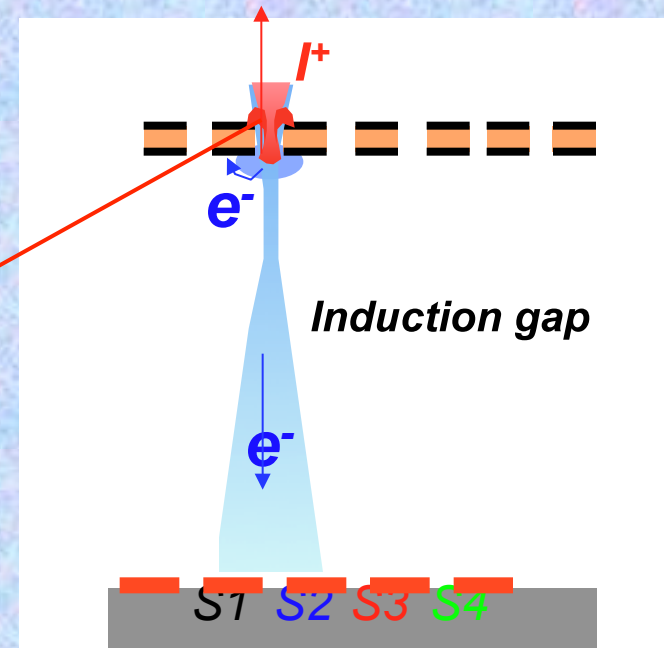
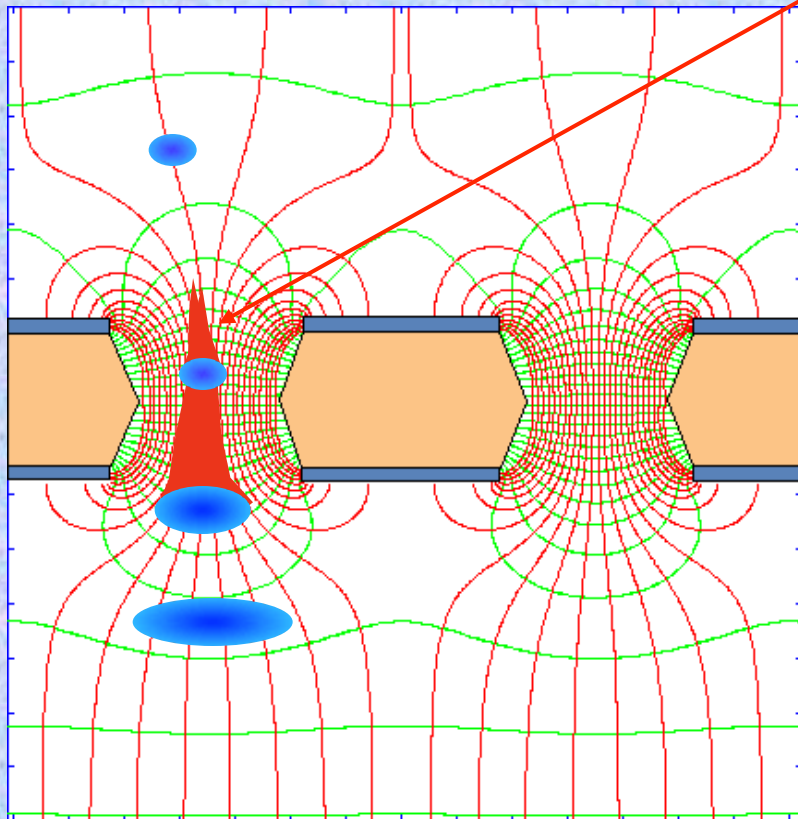
Ingrid

GEM (Gas Electron Multiplier)

Thin metal-coated polymer foil chemically pierced by a high density of holes

A difference of potentials of $\sim 500\text{V}$ is applied between the two GEM electrodes.

The primary electrons released by the ionizing particle, drift towards the holes where the high electric field triggers the electron multiplication process.



Electrons are collected on patterned readout board.

A fast signal can be detected on the lower GEM electrode for triggering or energy discrimination.

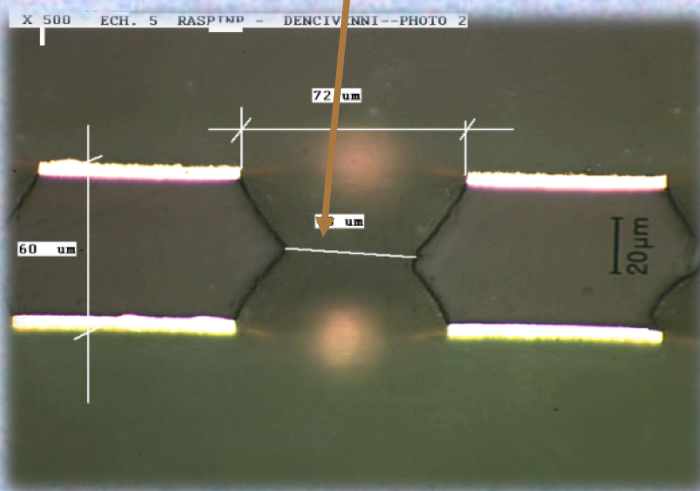
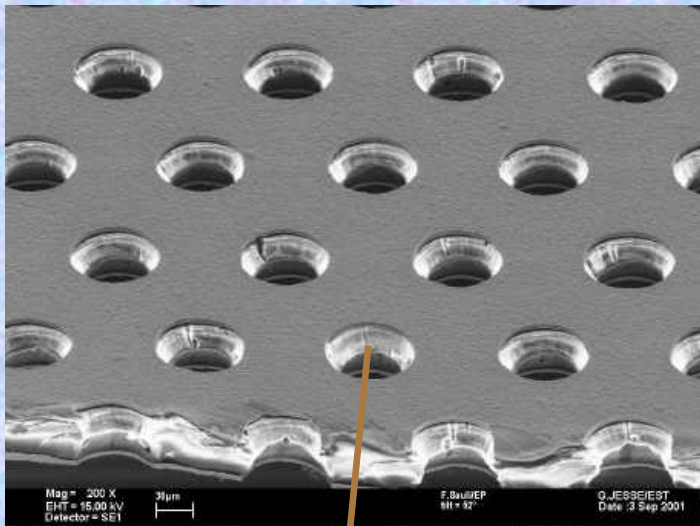
All readout electrodes are at ground potential.

F. Sauli, Nucl. Instrum. Methods A386(1997)531

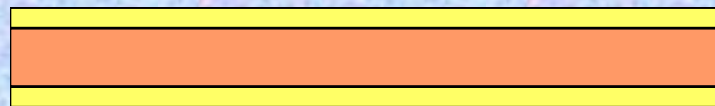
F. Sauli, <http://www.cern.ch/GDD>

GEM Manufacturing

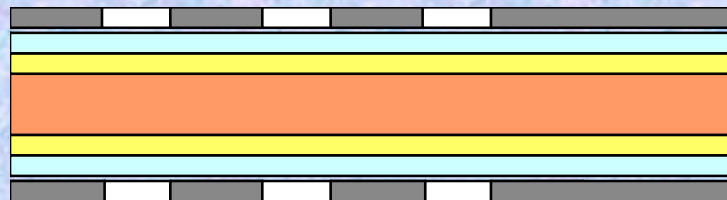
Typical geometry:
5 μm Cu on 50 μm Kapton
70 μm holes at 140 mm pitch



50 μm Kapton
5 μm Cu both sides



Photoresist coating,
masking and
exposure to UV light



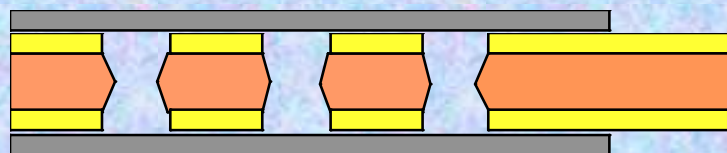
Metal chemical
etching



Kapton chemical
etching



Second masking



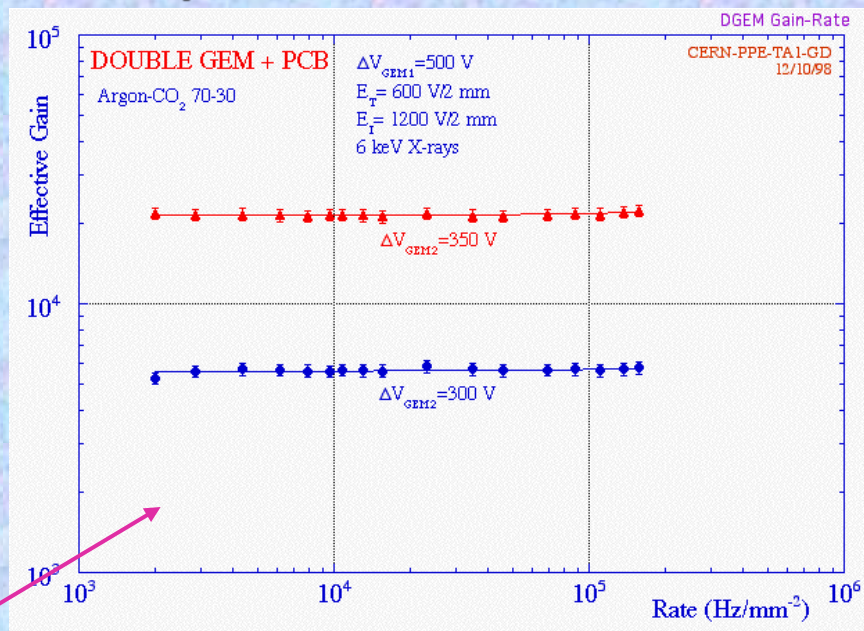
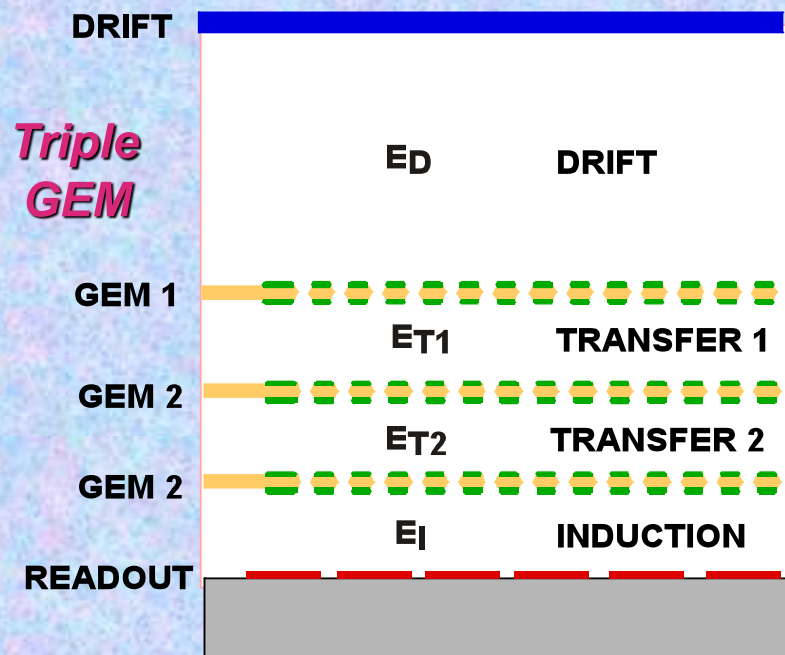
Metal etching
and cleaning



4/5/09

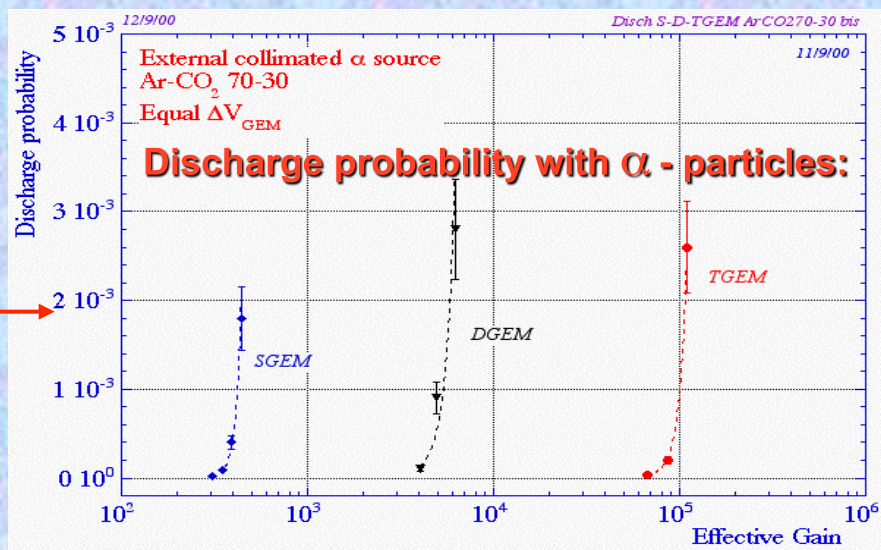
Multiple GEM Structures

Cascaded GEMs achieve larger gains and safer operation in harsh environments



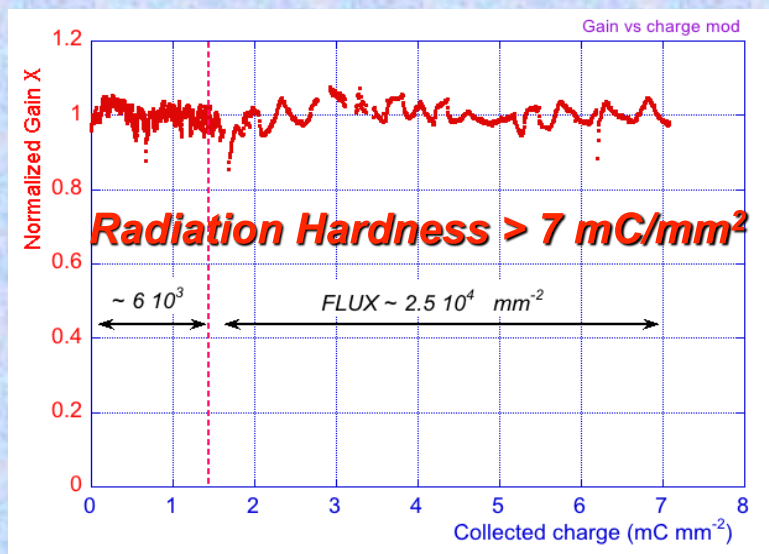
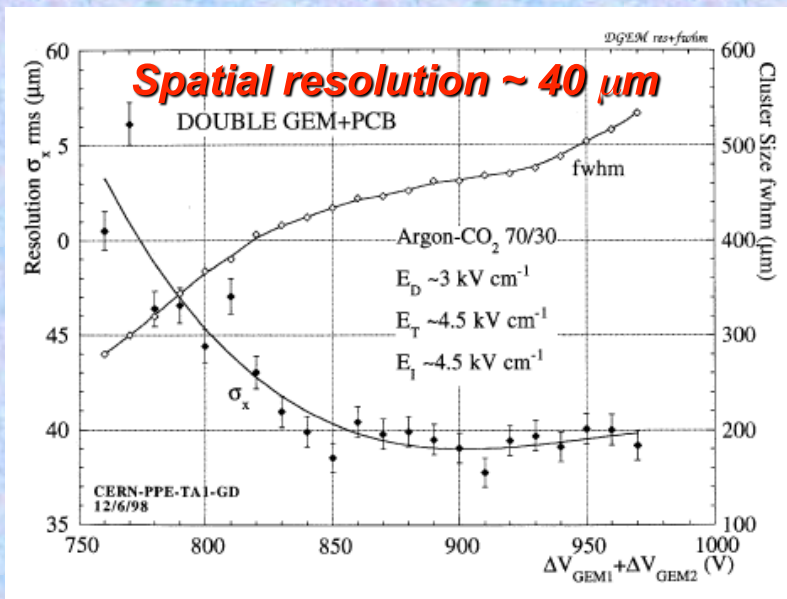
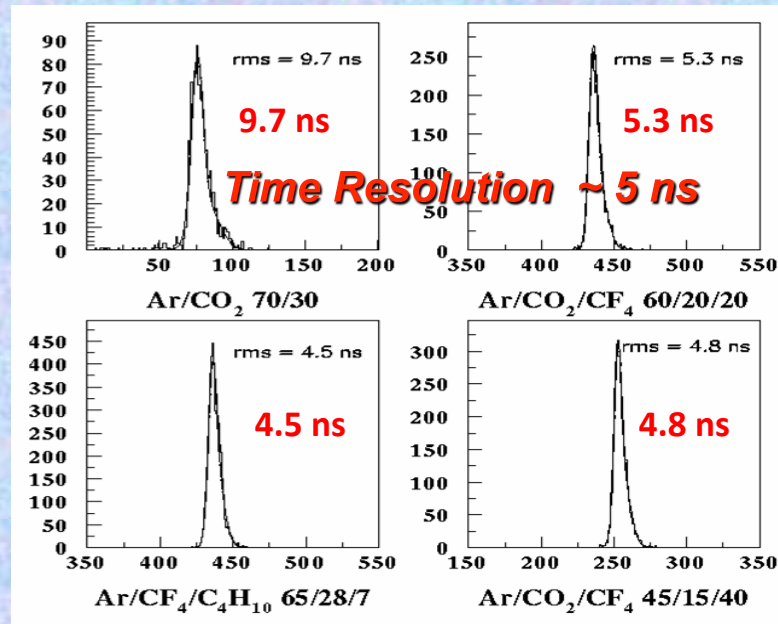
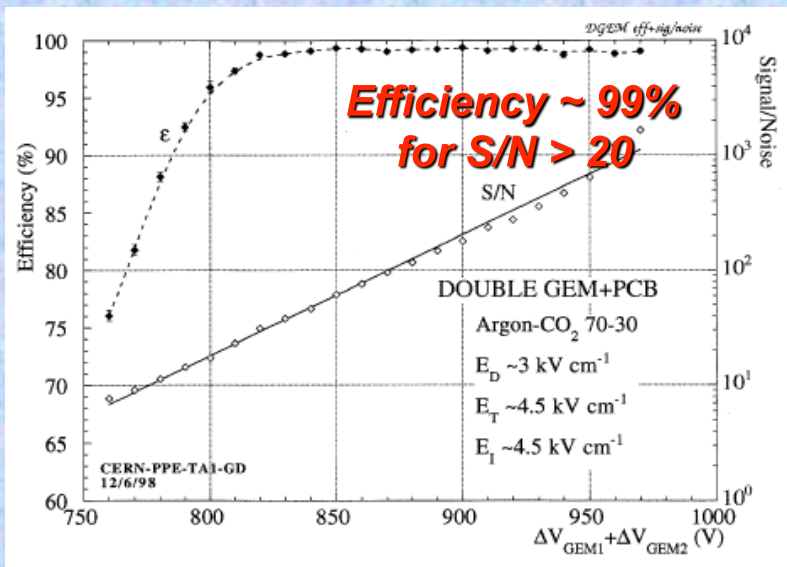
**High-rate capability $> 10^5$ Hz/mm²;
No space-charge phenomena**

**Multiple GEM structure strongly
reduces probability of
discharges**



C. Buttner et al, NIM A 409(1998)79
S. Bachmann et al, NIM A A 443(1999)464

Multiple GEM Performance



A. Bressan et al, Nucl. Instr. and Meth. A425 (1999) 262

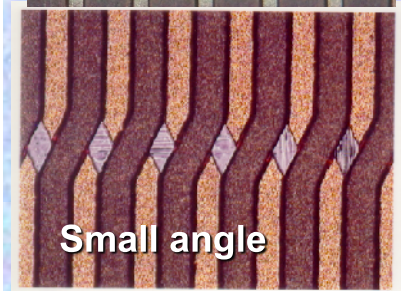
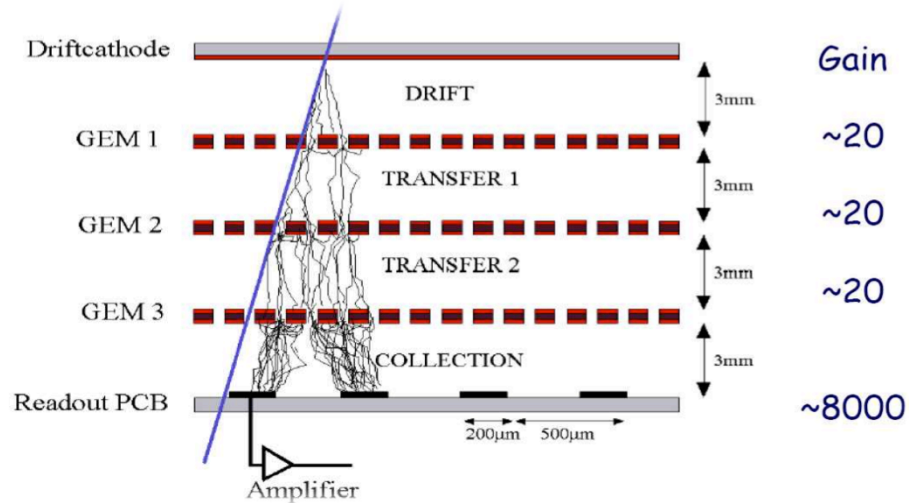
J. Benloch et al, IEEE NS-45(1998)234; C. Altunbas et al, Nucl. Instr. and Meth. A515

Gas Electron Multiplier (GEM)

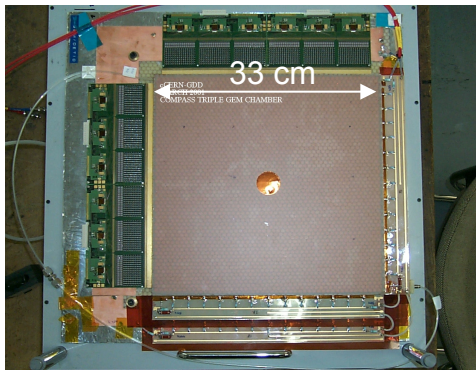
F. Sauli, NIM A386(1997) 531;
F. Sauli, <http://www.cern.ch/GDD>



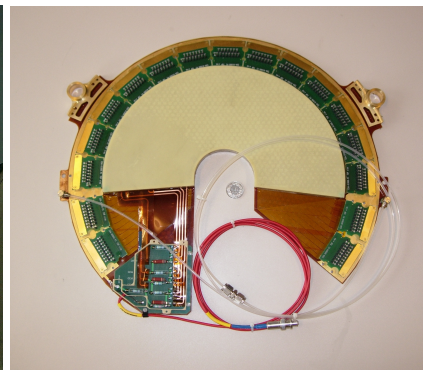
Full decoupling of amplification stage (GEM) and readout stage (PCB, anode)



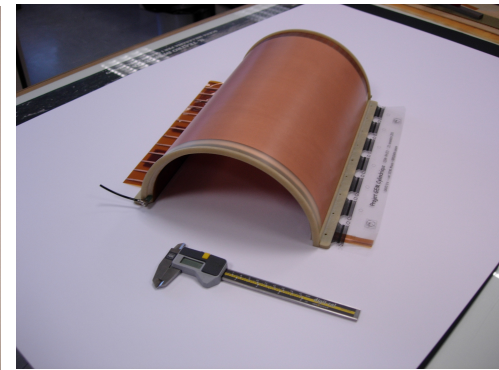
Amplification and readout structures can be optimized independently !



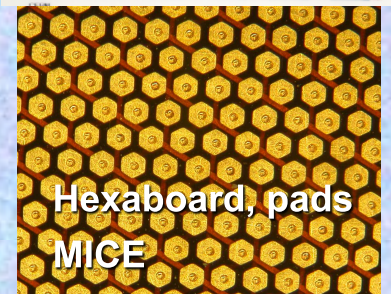
Compass



Totem



NA49-future

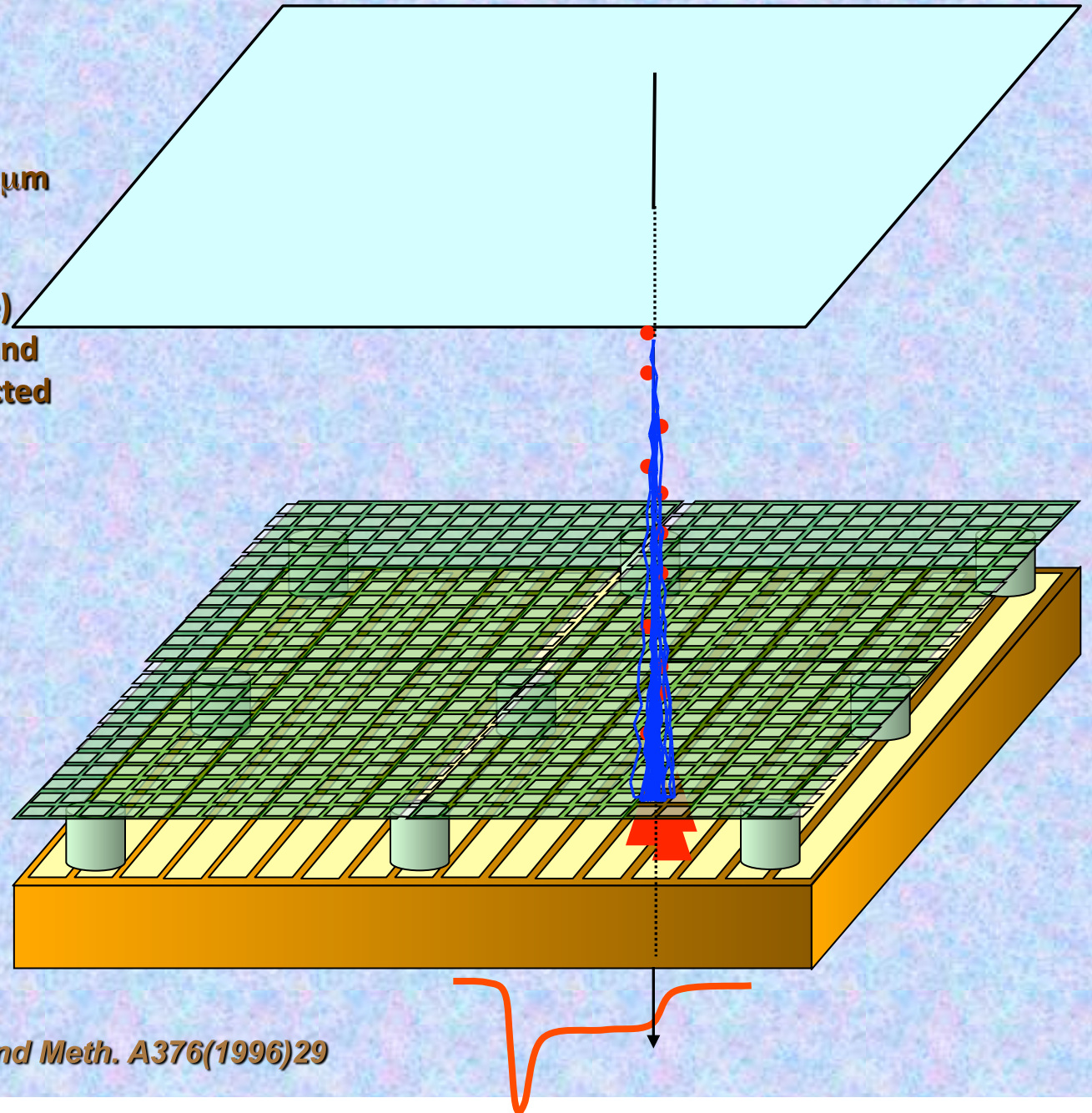
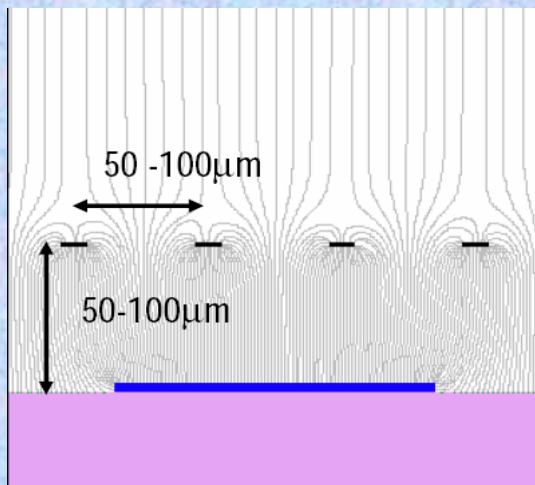


MICro MESH Gaseous Structure (MICROME GAS)

Micromesh Gaseous Chamber: a micromesh supported by 50-100 μm insulating pillars

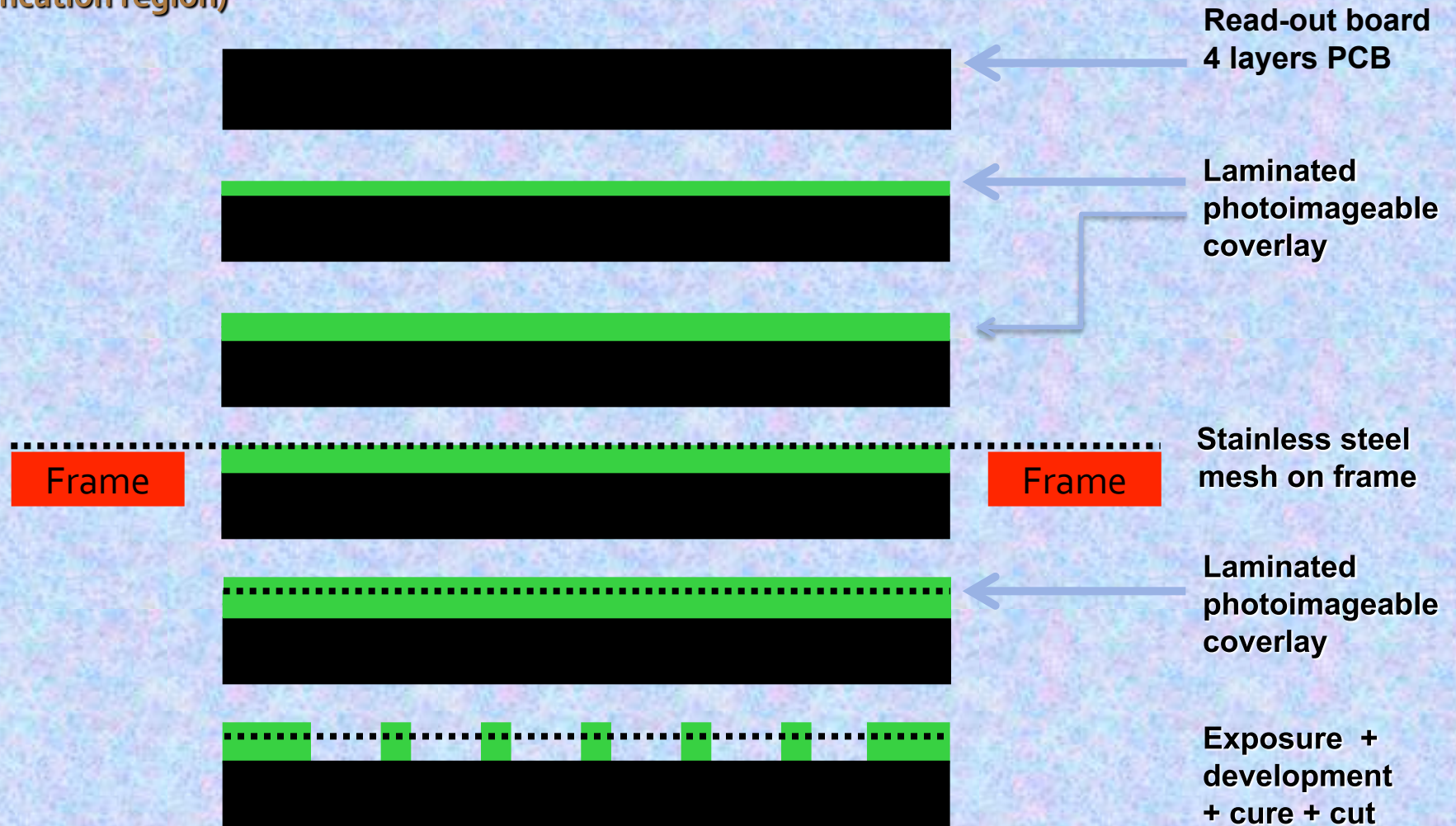
Multiplication (up to 10^5 or more) takes place between the anode and the mesh and the charge is collected on the anode (one stage)

Small gap: fast collection of ions



Manufacturing Bulk Micromegas

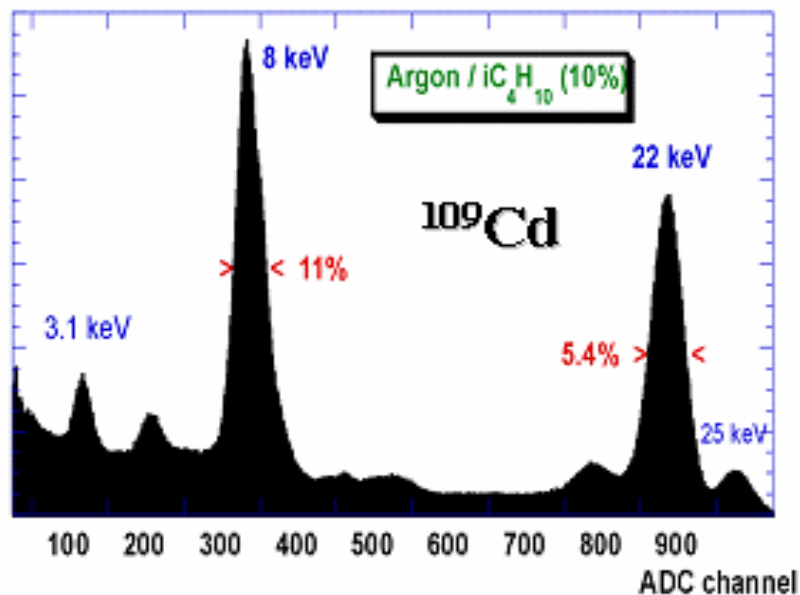
The micro mesh consist of 18um μm thick stainless steel 400 Lpi woven microstrings. This micro mesh is embedded between two photoimageable coverlay layers with a micron precision (to define the amplification region)



Easy manufacturing - Large size compatible - Low cost
Robust and electrically testable at the production time

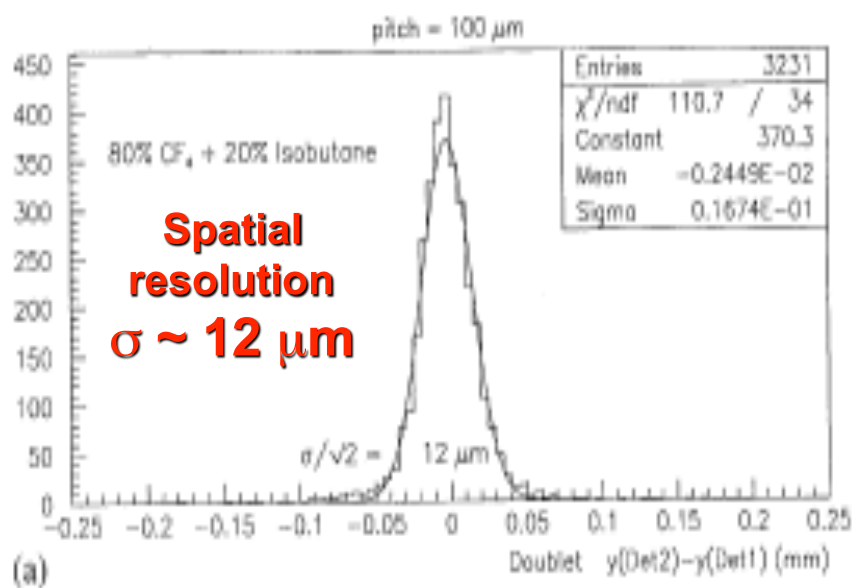
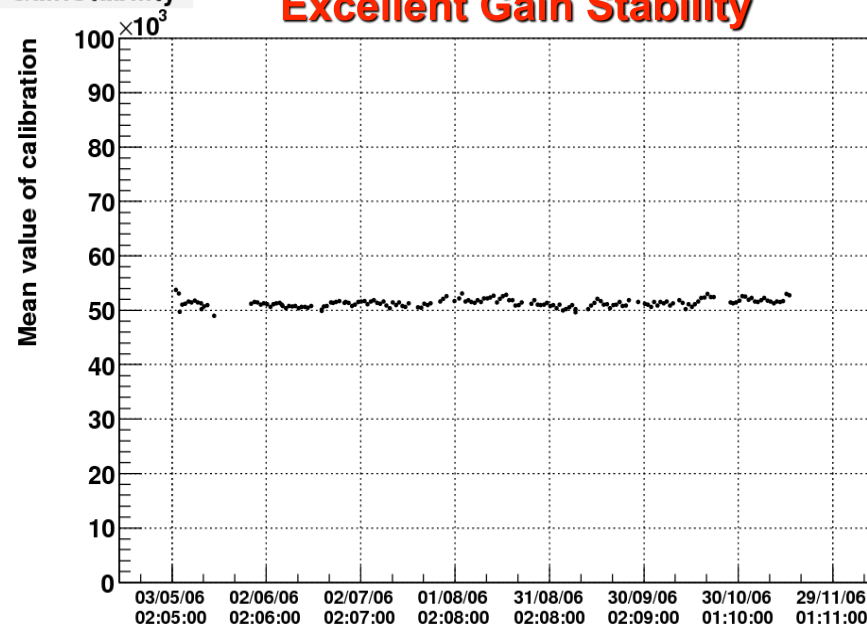
Micromegas Performance

Small gap → good energy resolution

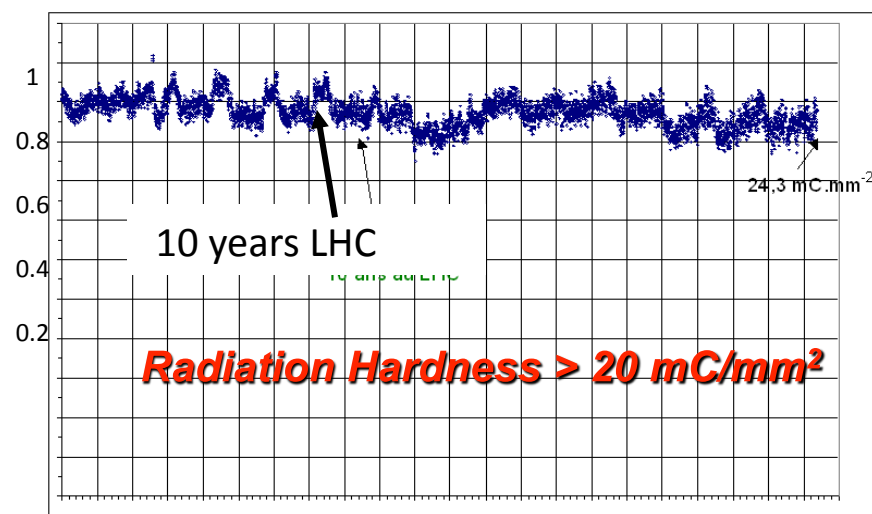


GainStability

Excellent Gain Stability



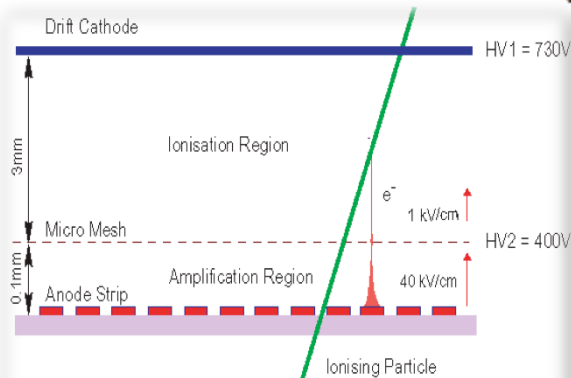
ageing: Ar- $i\text{C}_4\text{H}_{10}$ 94-6% up to 24.3 mC/mm^2



Radiation Hardness > 20 mC/mm^2

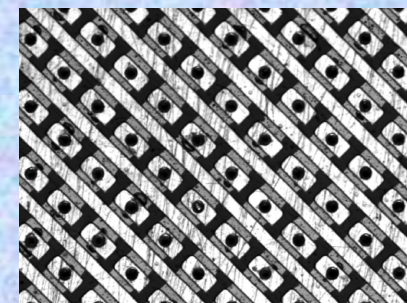
MICROME GAS

Parallel plate multiplication in thin gaps between a fine mesh and anode plate

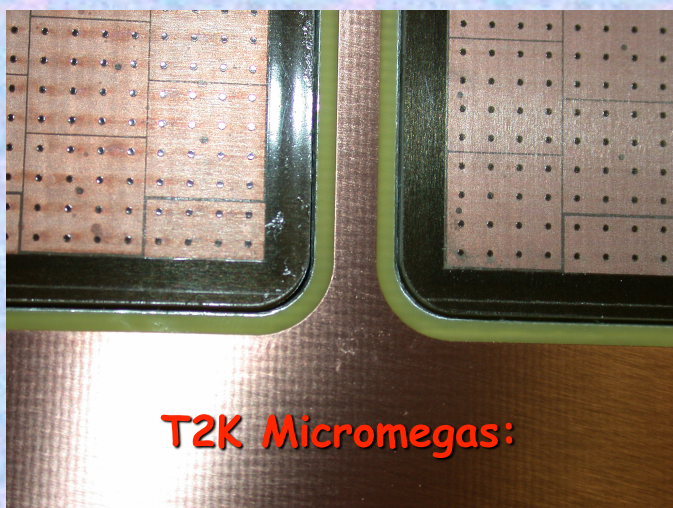
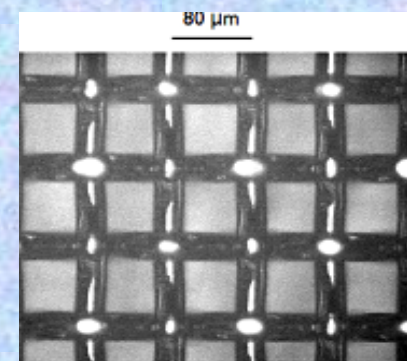


- Discharges are not destructive,
- Further studies to mitigate discharges (minimize dead time) by resistive coating, GEM preamplification

CAST readout:



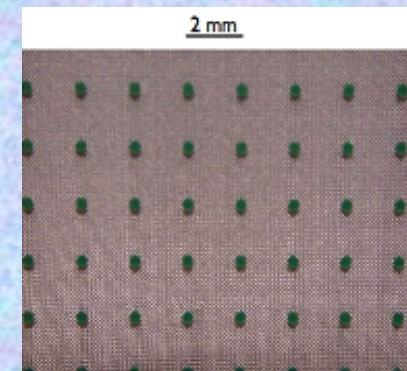
"Bulk" Micromegas:



T2K Micromegas:

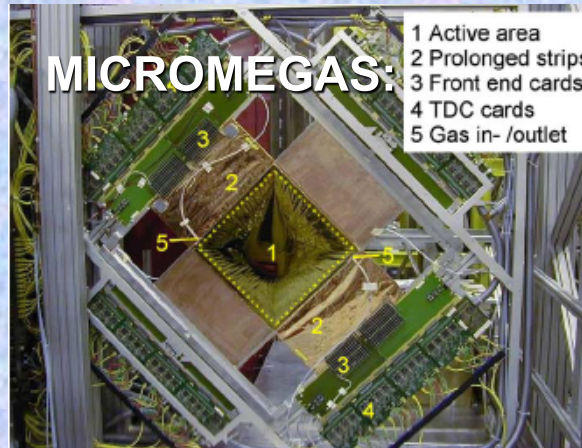
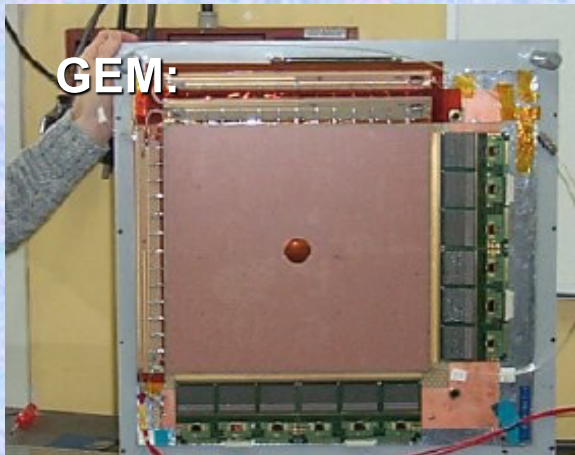


Piccolo Micromegas in Casaccia Reactor



GEM / Micromegas in COMPASS - Textbook of Modern Detectors

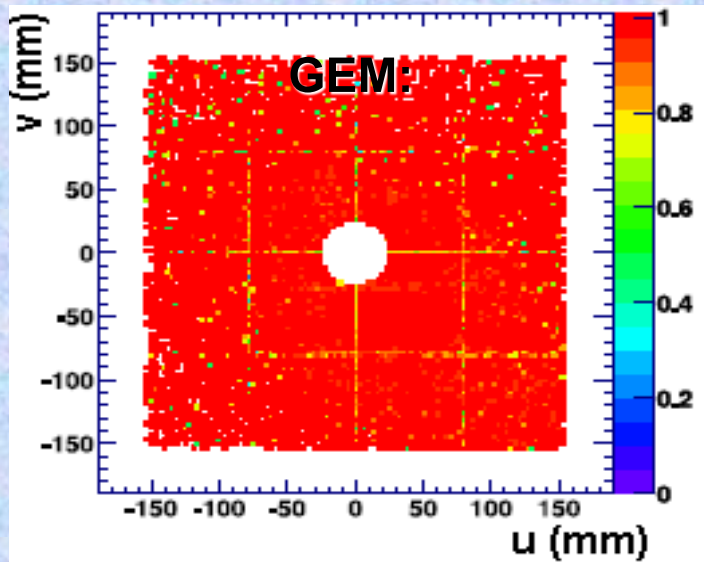
High Rate Forward spectrometer:
COMPASS beam $\sim 5 \cdot 10^7$ muons/s on ${}^6\text{LiD}$ target



22 TRIPLE GEM DETECTORS
(31*31 cm²)
& 12 MICROMEAS PLANES
(40*40 cm²)

High Rate /
High Precision /
Low Mass Detectors:

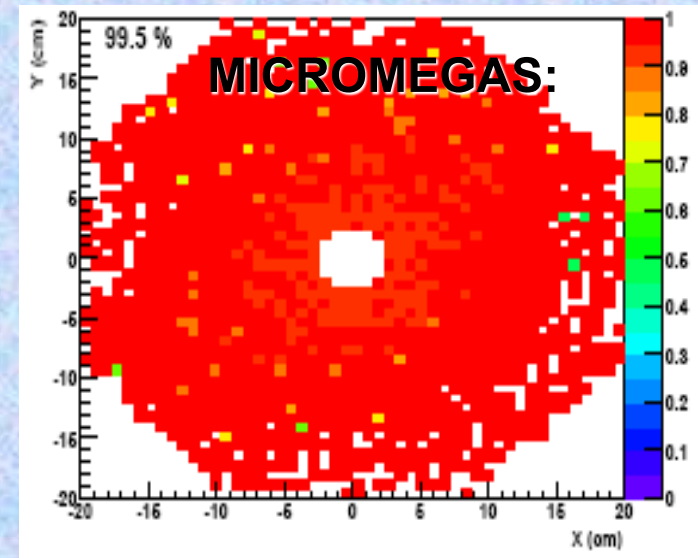
25 kHz/mm²



UNIFORMITY
OF
TRACKING
EFFICIENCY:
($\epsilon > 95\%$)

RELIABLE
OPERATION
in 2002 – 2006

NO SIGN
OF AGING

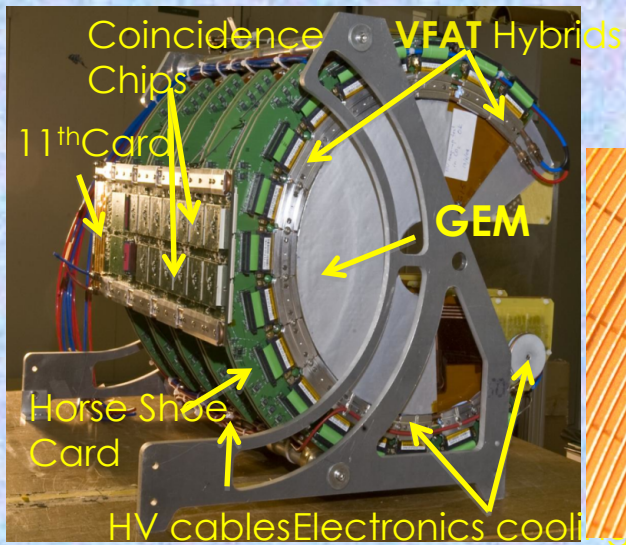


B. Ketzer et al, NIM A535 (2004) 314
F. Kunne, 2006 IEEE NSS/MIC Proceedings

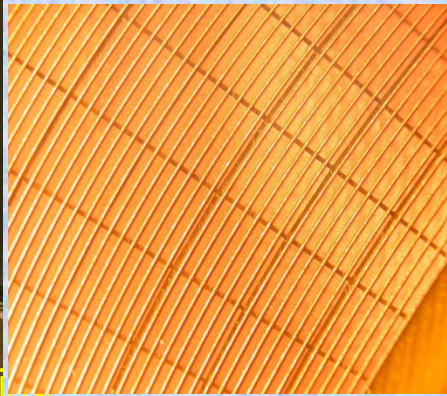
GEM in the LHC Experiments

GEMs are used in the TOTEM (tracking and triggering) and LHCb Muon (triggering)

TOTEM GEMs:



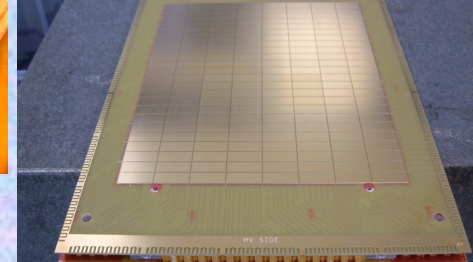
**2D readout
(strips & pads)**



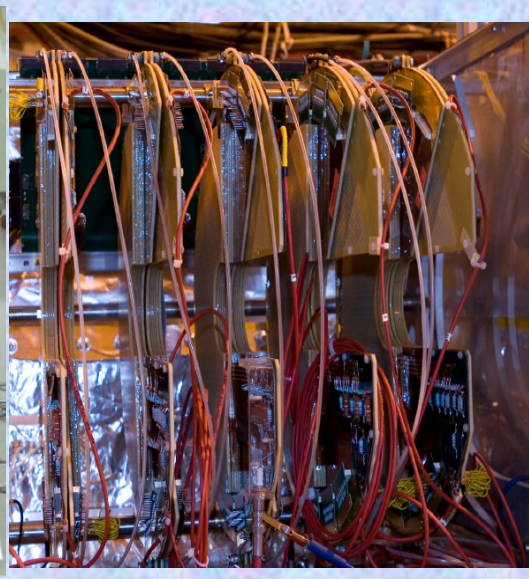
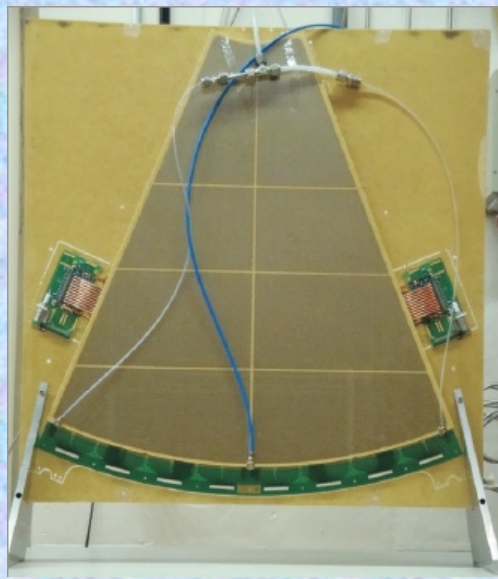
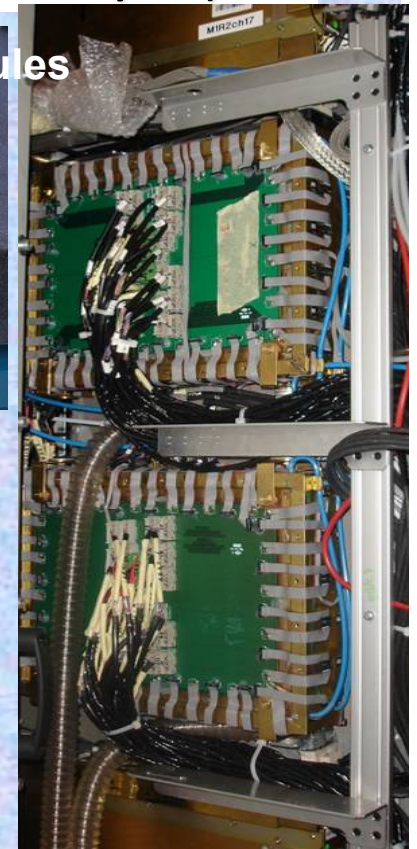
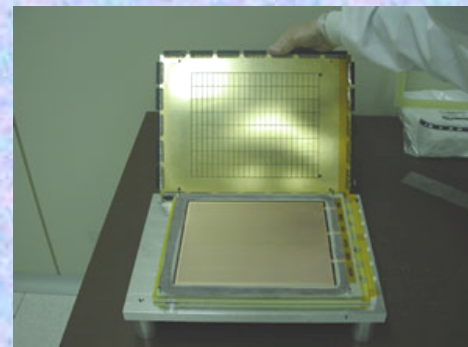
**LHCb Muon Trigger:
(12 double TGEM detectors)**

**Rate - 5 kHz mm⁻²
Time resolution 4.5 ns rms
Radiation hard up to integrated charge
of 20 mC mm⁻² (15 LHCb years)**

20x24 cm² GEM modules



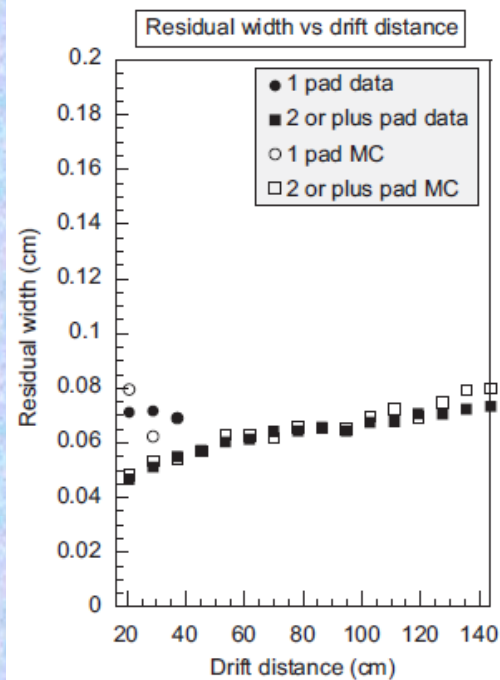
Pad readout plane



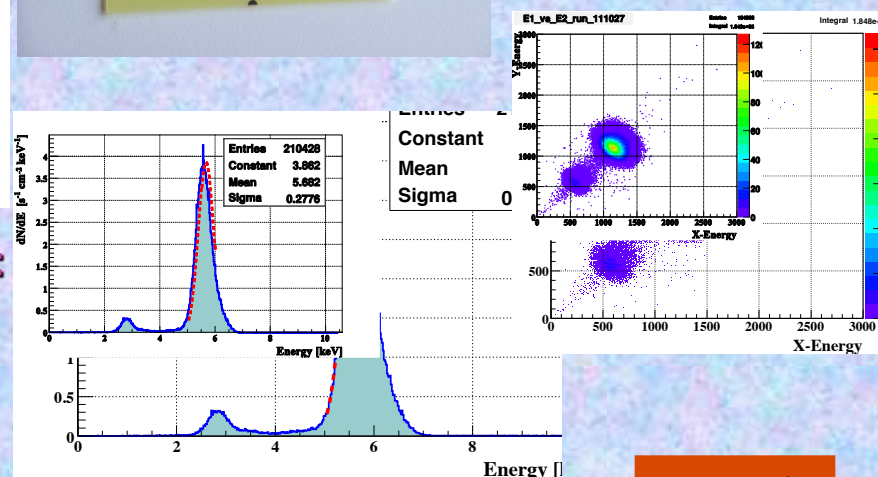
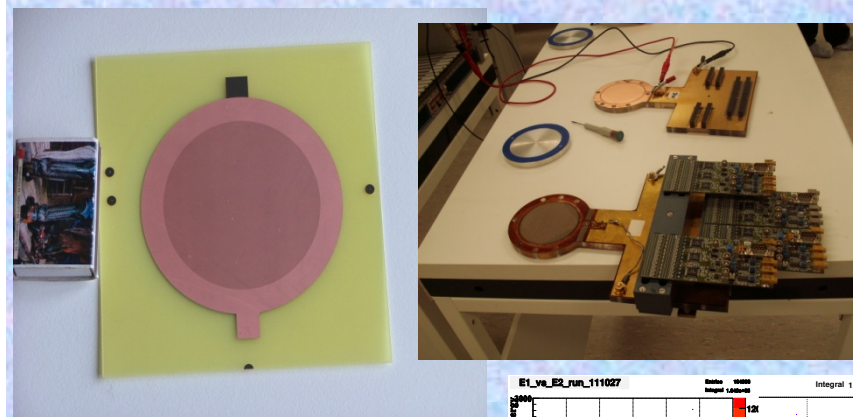
Micromegas in the Neutrino & Astrophysics Experiments

T2K TPC:

24 bulk-Micromegas
3 m² of bulk Micromegas
41472 FEE channels

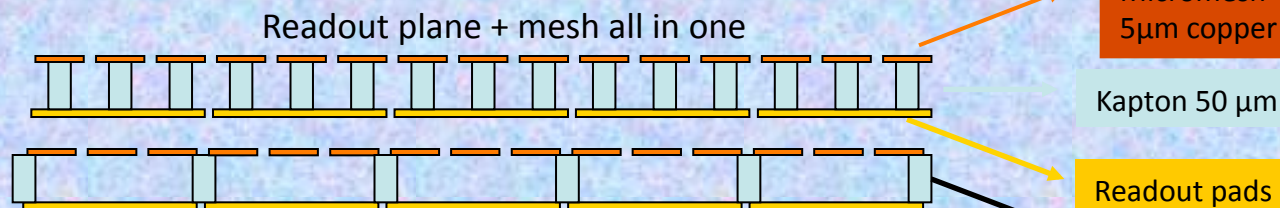


CAST (Micro-Bulk Technology):



Micro-Bulk Technology:

⁵⁵Fe with Ar – 5%
iC4H10 @ 1 bar
FWHM @ 6 keV = 11.5 %



An I. Giomataris and R. De Oliveira idea

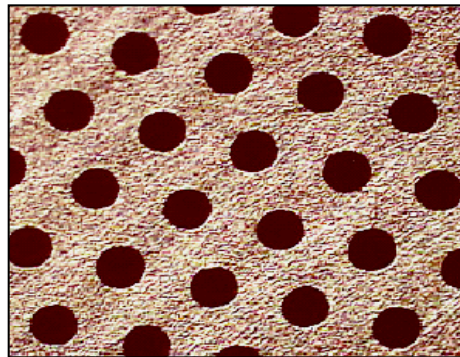
Lower capacitance
Under development

Thick-GEM Multipliers (TGEM)

Simple & Robust → Manufactured by standard PCB techniques of precise drilling in G-10 (and other materials) and Cu etching

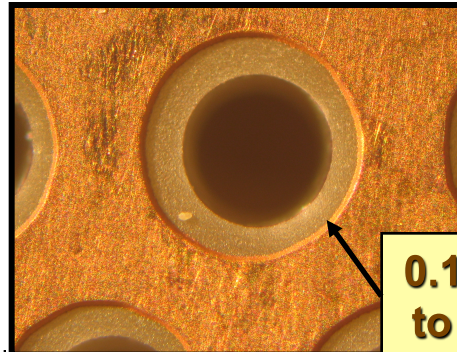


STANDARD GEM
 10^3 GAIN IN SINGLE GEM



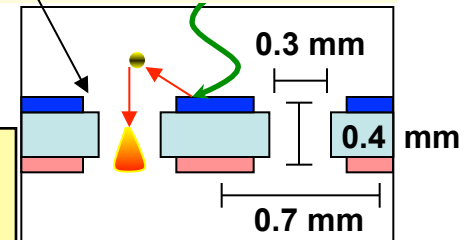
1 mm

THGEM
 10^5 gain in single-THGEM



0.1 mm rim
to prevent
discharges

Reflective CsI PC

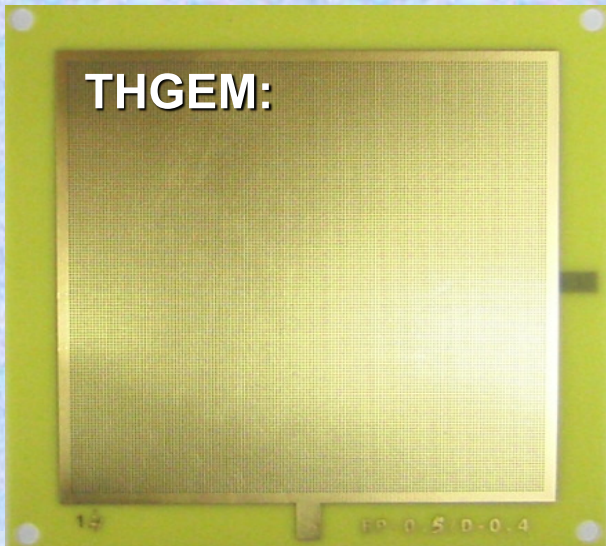


Similar to V. Peskov "Optimized GEM"

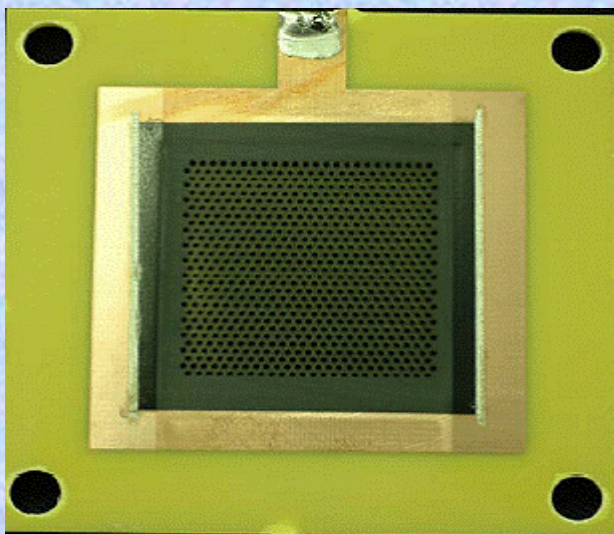
- Microlithography + etching
- High Spatial resolution ($\sim 30 \mu\text{m}$)
- $>10^3$ gain in single GEM, 10^6 gain in cascaded GEMs
- Fast (ns)
- Low pressure – gain ~ 30
- PCB tech - etching + drilling, Simple & robust
- Sub-mm to mm spatial resolution
- 10^5 gain in single- & 10^7 double-TGEM
- Fast (ns)
- Low pressure ($<1\text{Torr}$) gain 10^4

THGEM- Thick GEM / RETGEM Resistive Thick GEM

THGEM:

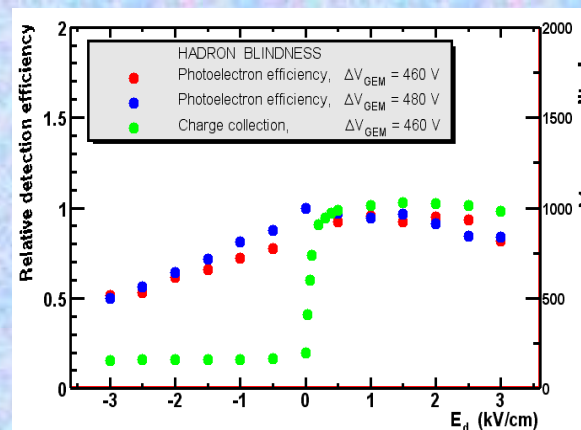


Resistive Electrode Thick GEM (RETGEM):



3 Advantages of THGEM/ RETGEM for RICH:

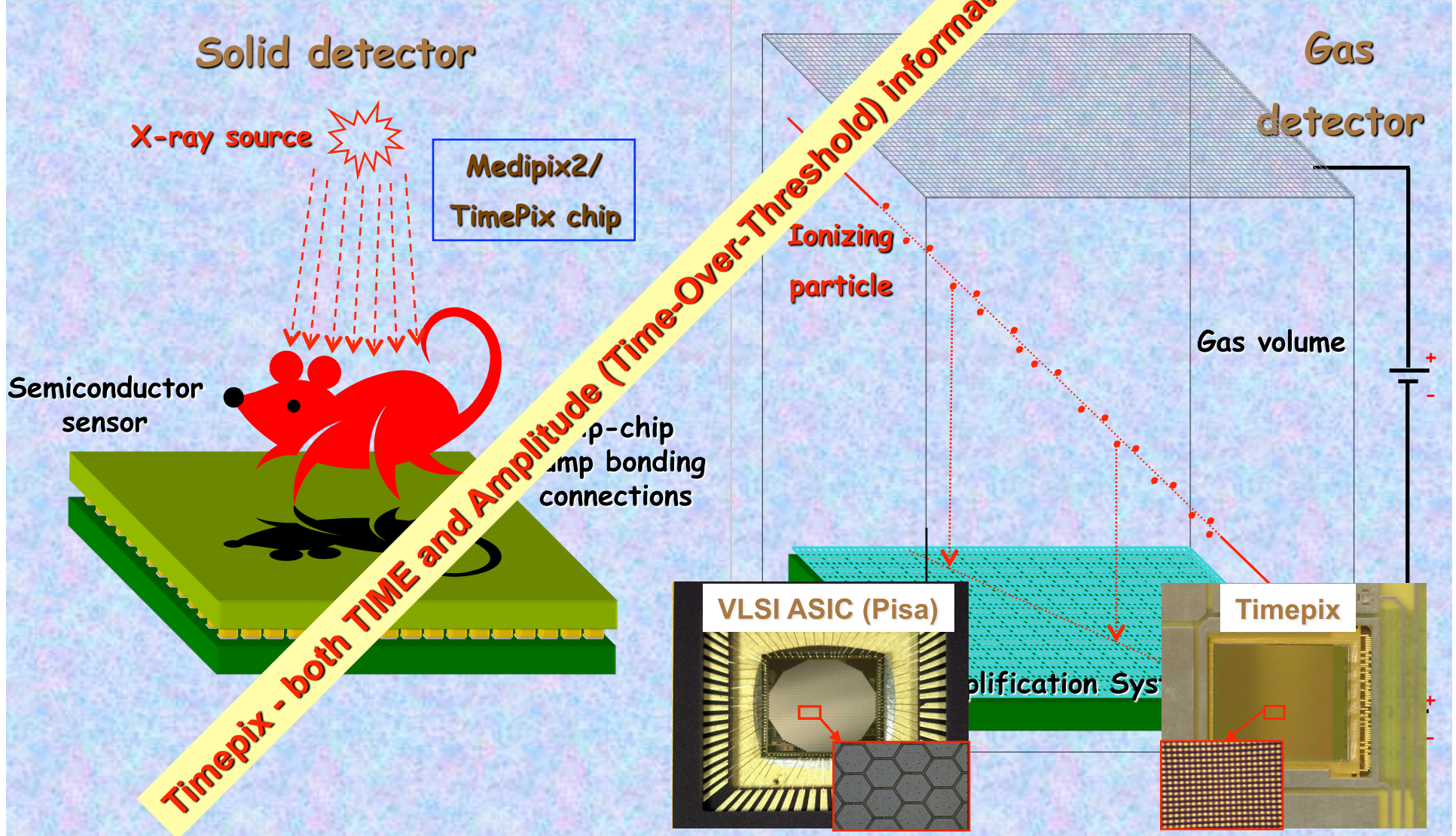
- **Very high gains** ($>10^5$) can be achieved with TGEMs in some gases, especially in mixtures of Ne with a small concentration of quenchers
- TGEM can operate in badly quenched gases as well as in gases in which are strong UV emitters. This may open a possibility of using **windowless detectors** for some RICH designs
- If necessary TGEMs can operate in “**hadron blind mode**” with zero and even reversed electric field in the drift region which allows strongly suppress the ionization signal from charged particles



Measurements with 3-GEM for Hadron Blind Detector for Phenix @ RHIC

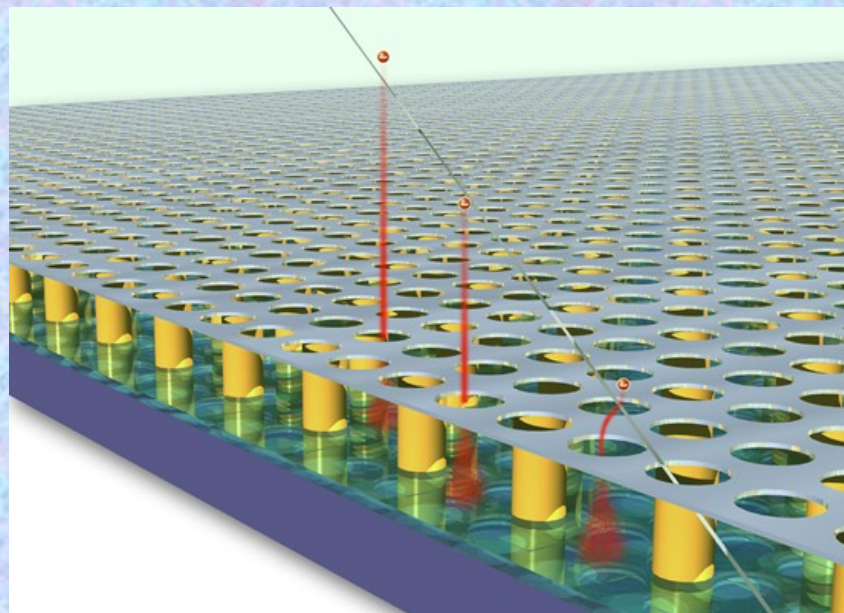
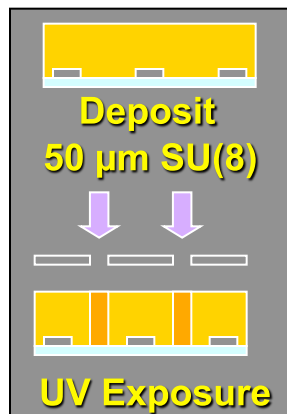
Pixel Readout of Micro-Pattern Gas Detector

Gas Detector Readout by multi-pixel CMOS array (used as charge collecting anode)
CMOS readout concept → Analog VLSI ASIC (Pisa), Medipix2 / TIMEPIX Chips



Micromegas/Ingrid + Timepix Detector

InGrid: integrate Micromegas & pixel chip by Si-wafer post-processing technology
 • Grid robustness & Gap/Hole accuracy

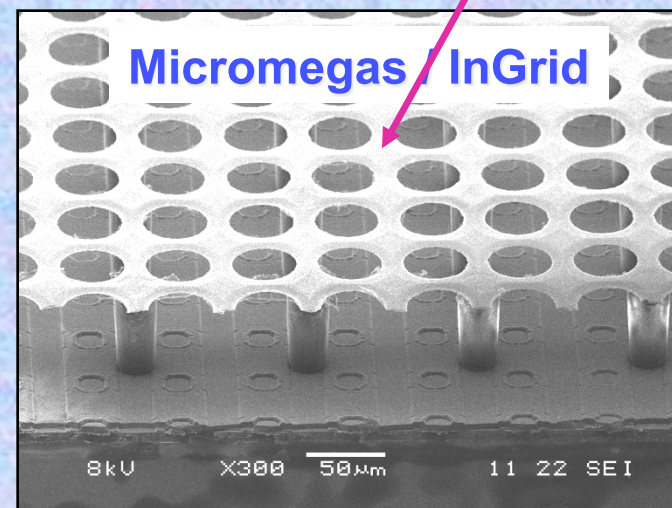
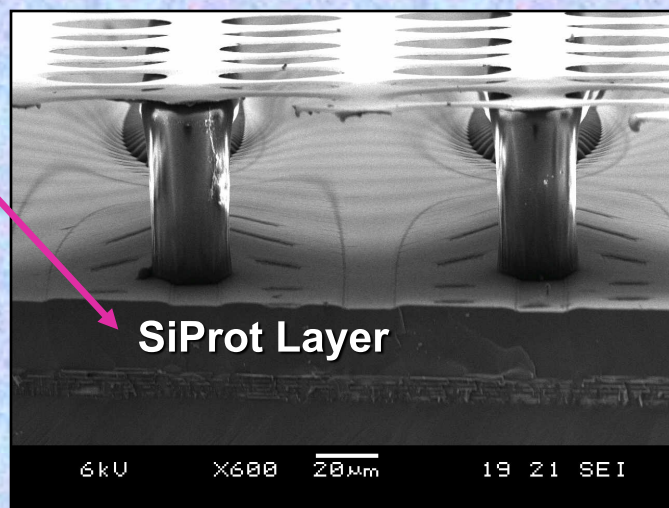


Micromegas/Ingrid + SiProt + Timepix Detector:

Apply Si_3N_4 (high resistivity layer 3-20 μm)

for discharge quench
& SPARK
PROTECTION

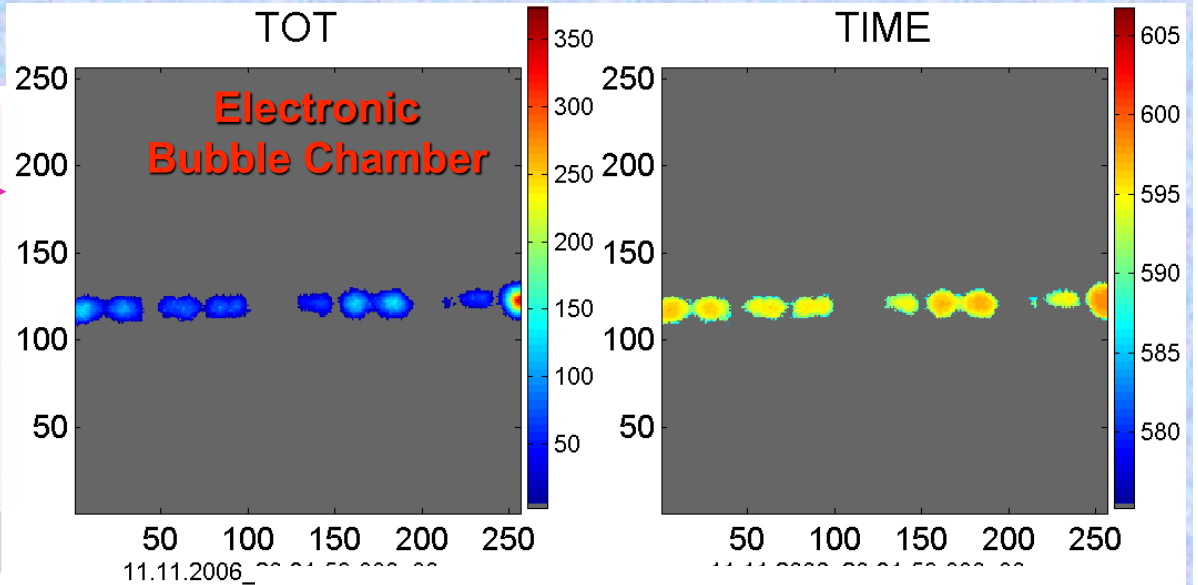
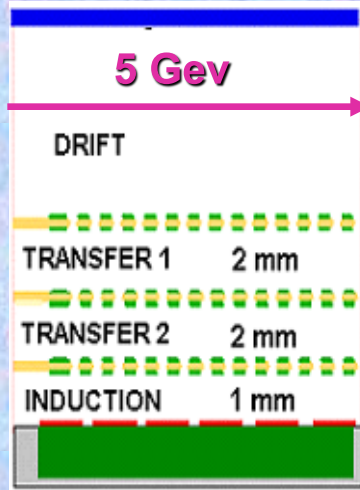
before InGrid
production



GEM/Micromegas + Timepix Readout @ 5 GeV Electron Beam

Triple GEM + Timepix:

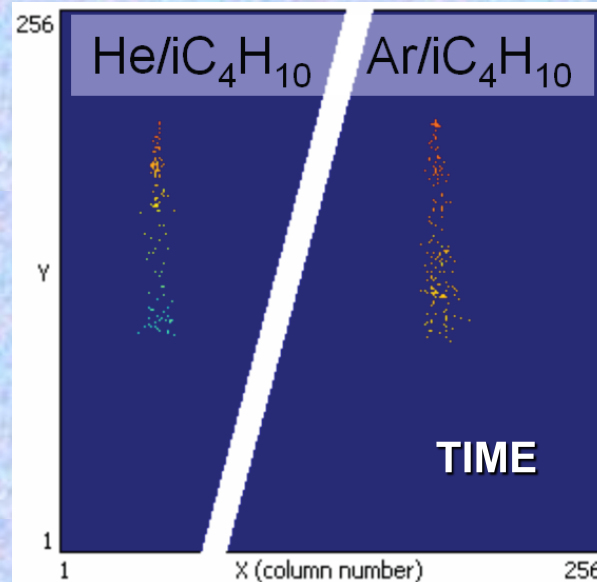
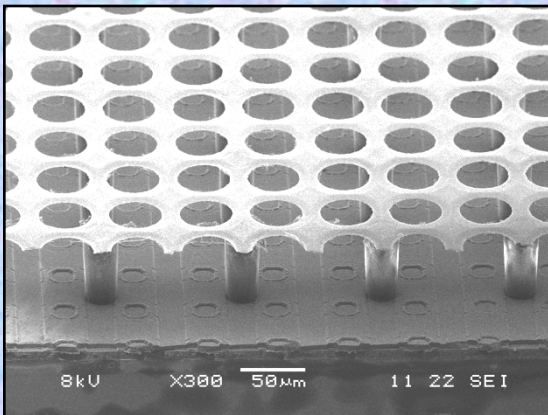
Operated in checker-board pattern of TOT (charge) and TIME (time)



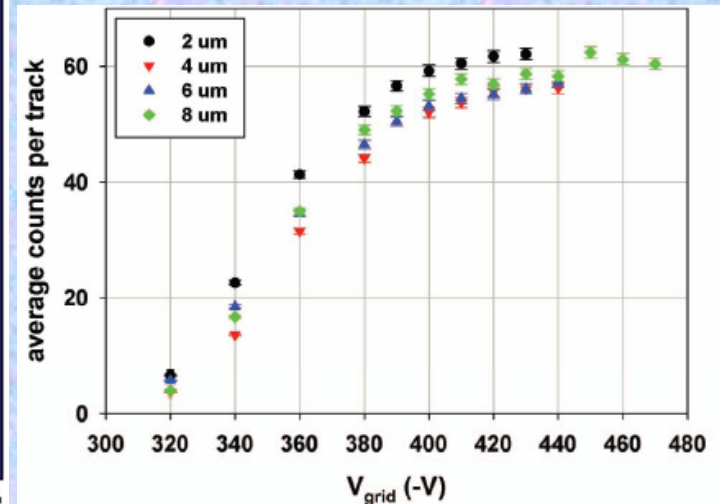
M. Titov, Nucl. Instr. and Meth. A581 (2007) 25.

Micromegas/ Ingrid + Timepix:

Studies of SiProt layer thickness (efficiency & discharges):



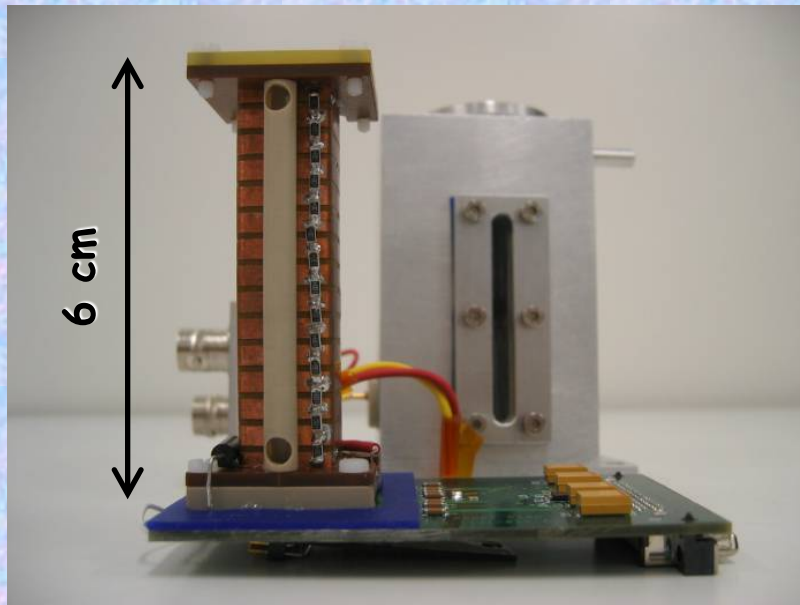
<Nhits> per track vs Si₃N₄ layer thickness:



Y. Bilevych et al., 2009 IEEE NSS/MIC Conference Record.

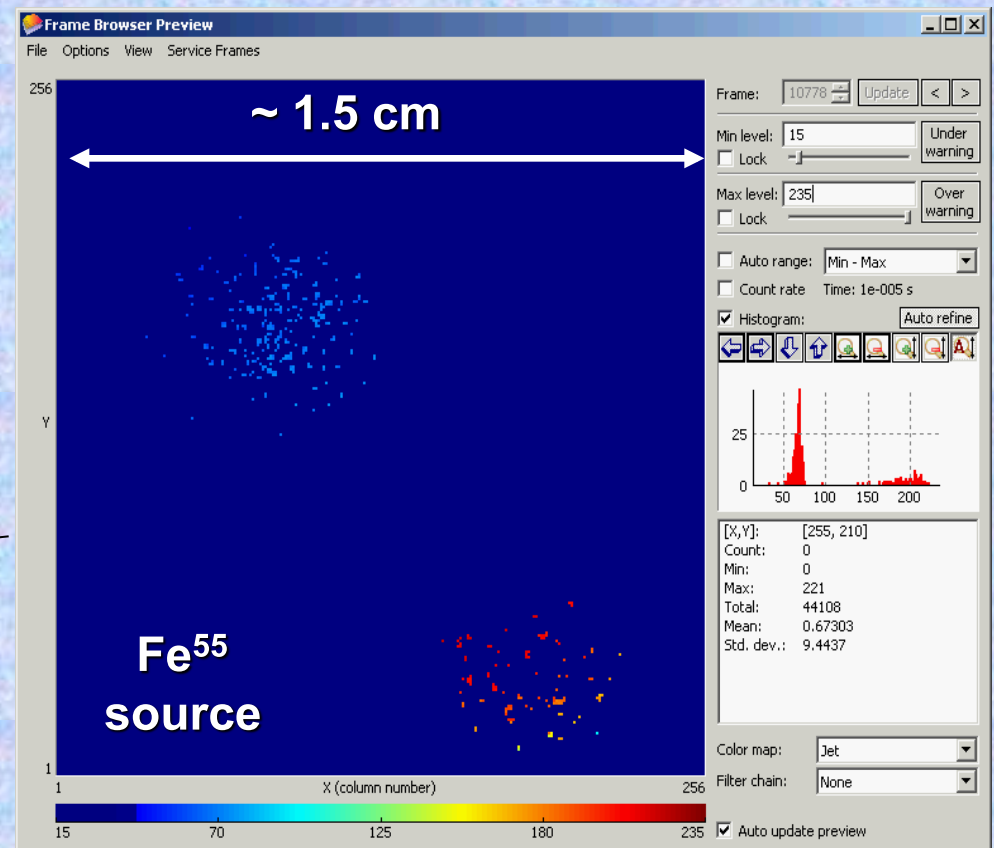
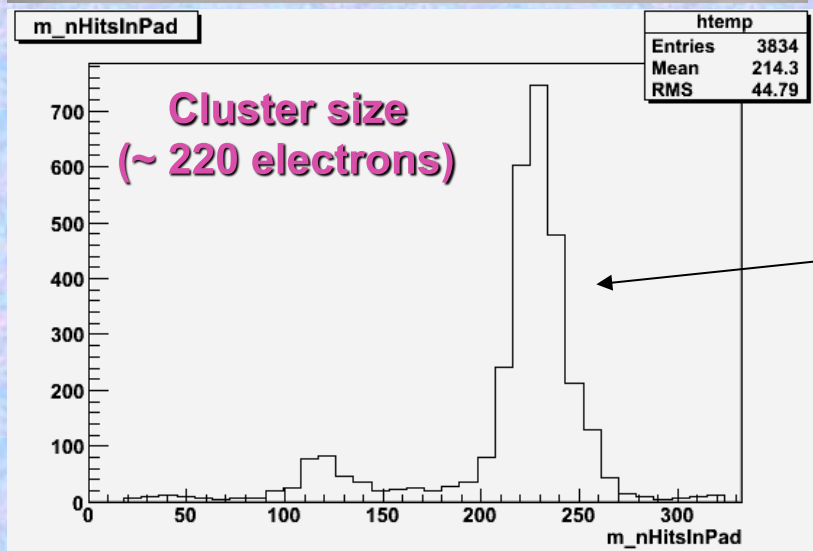
Micromegas/Ingrid + Timepix & microTPC

μ TPC with a 6 cm height field cage
Size: 4 cm x 5 cm x 8 cm



Observe electrons (~ 220) from an X-ray (5.9 keV) conversion one by one and count them

→ Study single electron response



Micromegas/Ingrid + Timepix & Discharges

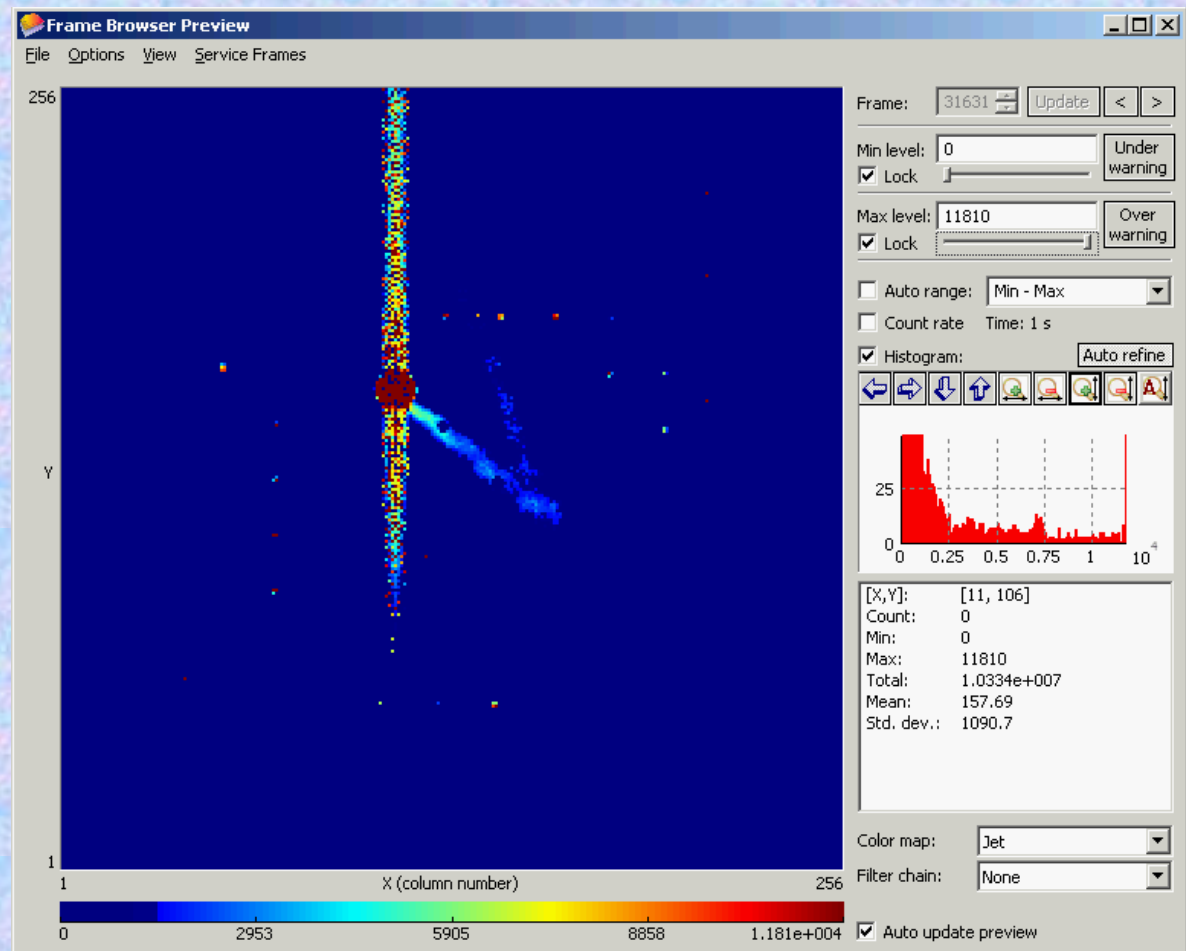
- Strong electric field (70 – 100 kV/cm) over the Si-pixel chip
- Provoke discharges by introducing small amount of Thorium in the Ar gas
 - Thorium decays to Radon 222 which emits 2 alphas of 6.3 & 6.8 MeV ($\sim 10^5$ e)

- Round-shape images of discharges are being recorded

- Perturbations in the concerned columns

- Threshold ?
- Power ?

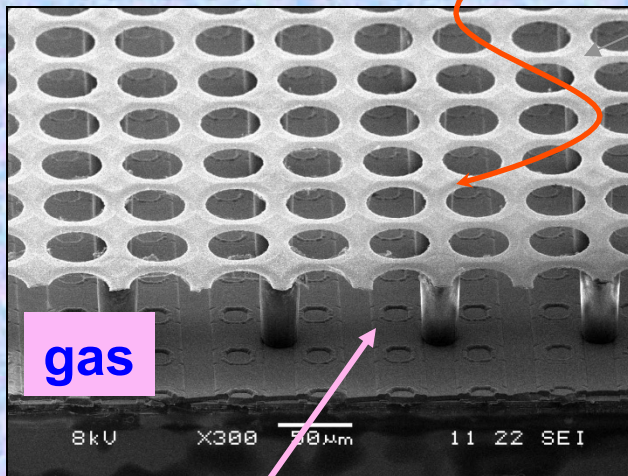
Chip keeps working !



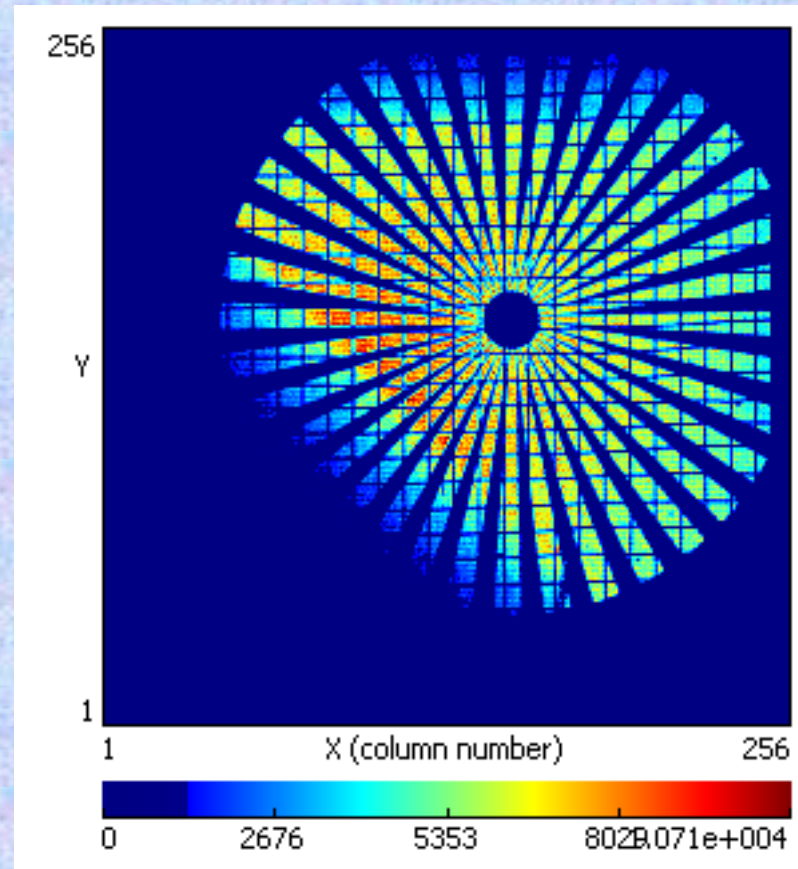
Integrating Photon Detectors and Electronics

**MICROME GAS (InGrid)
covered with CsI** photon

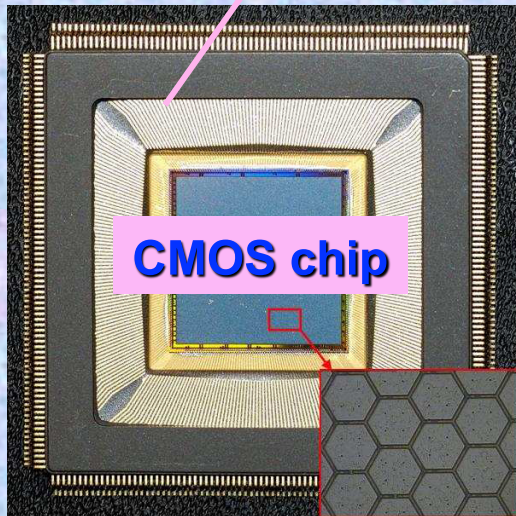
CsI photocathode



2D UV Image of a 10mm diameter mask



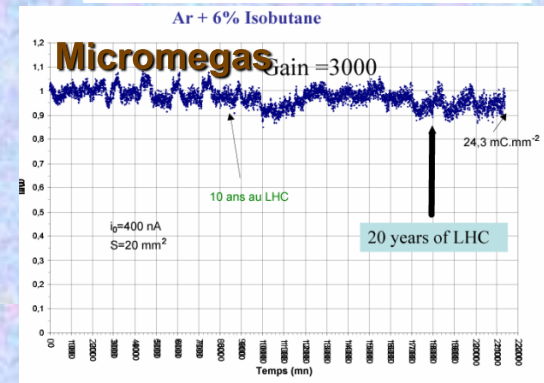
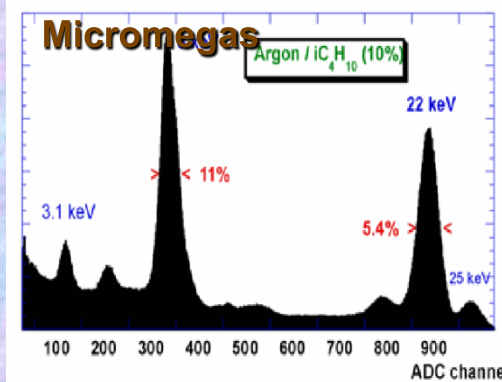
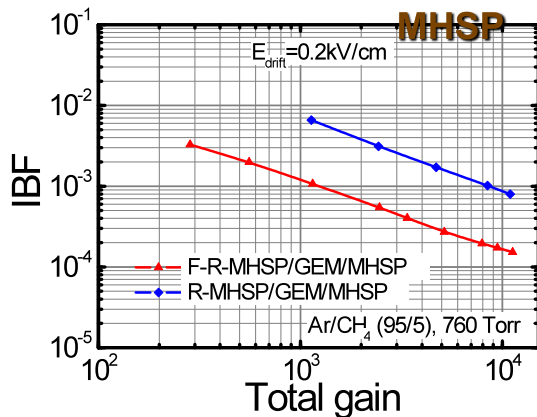
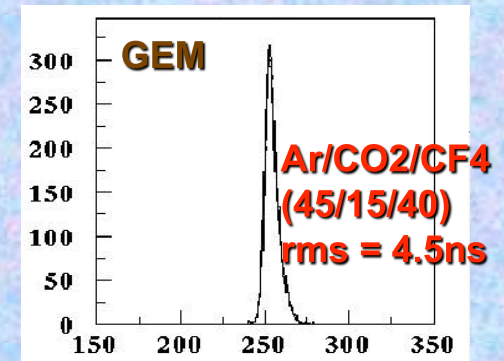
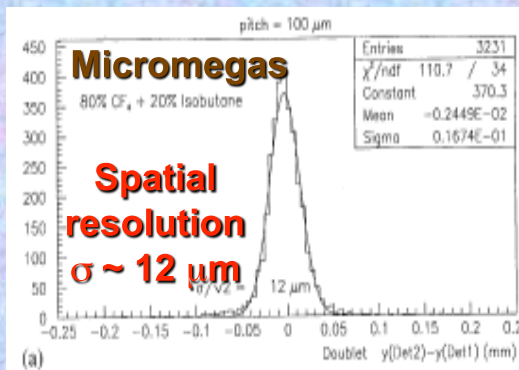
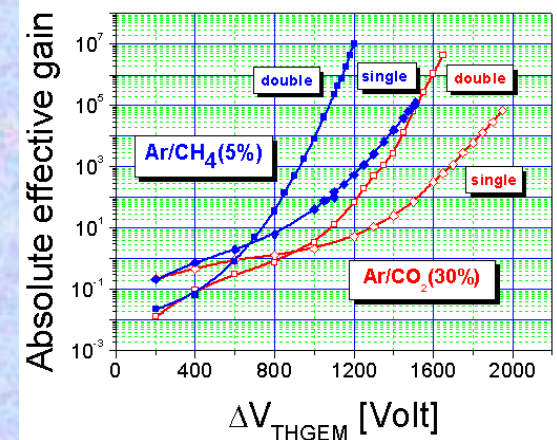
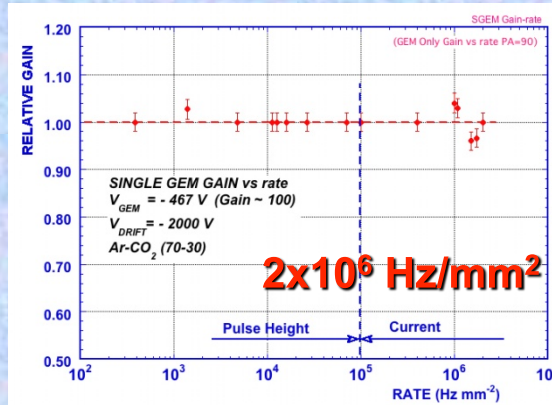
CMOS chip



**Chip area: 14x14mm².
(256x256 pixels of 55x55 µm²)**

Micro-Pattern Gas Detectors Performance Summary

- Rate Capability
- High Gain
- Space Resolution
- Time Resolution
- Energy Resolution
- Ageing Properties
- Ion Backflow Reduction
- Photon Feedback Reduction



RD 51 Collaboration - Working Groups

Advance Technological Developments of Micro-Pattern Gas Detectors

RD51 – Micropattern Gas Detectors

| | WG1 MPGD Technology & New Structures | WG2 Characterization | WG3 Applications | WG4 Software & Simulation | WG5 Electronics | WG6 Production | WG7 Common Test Facilities |
|-----------------------------------|---|---|---|---|--|--|--|
| Objectives | Design optimization Development of new geometries and techniques | Common test standards Characterization and understanding of physical phenomena in MPGD | Evaluation and optimization for specific applications | Development of common software and documentation for MPGD simulations | Readout electronics optimization and integration with MPGD detectors | Development of cost-effective technologies and industrialization | Sharing of common infrastructure for detector characterization |
| Tasks | Large Area MPGDs | Common Test Standards | Tracking and Triggering | Algorithms | FE electronics requirements definition | Common Production Facility | Testbeam Facility |
| | Design Optimization New Geometries Fabrication | Discharge Protection | Photon Detection | | General Purpose Pixel Chip | | |
| | | Ageing & Radiation Hardness | Calorimetry | Simulation Improvements | Large Area Systems with Pixel Readout | | |
| | Development of Rad-Hard Detectors | Charging up and Rate Capability | Cryogenic Detectors | Common Platform (Root, Geant4) | Portable Multi-Channel System | Industrialization | Irradiation Facility |
| Development of Portable Detectors | Study of Avalanche Statistics | X-Ray and Neutron Imaging | Discharge Protection Strategies | | Collaboration with Industrial Partners | | |
| | | | Astroparticle Physics Appl. | Electronics Modeling | | | |
| | | | Medical Applications | | | | |
| | | | Synchrotron Rad. Plasma Diagn. Homeland Sec. | | | | |

RD 51 Collaboration Organization

Consolidation around common projects: large area MPGD R&D, CERN/MPGD Production Facility, electronics developments, software tools, beam tests

WG1: large area Micromegas, GEM; THGEM R&D; resistive anode readout; design optimization (discharge protection)

WG2: single-electron response, avalanche fluctuations, photo detection with THGEM, GOSSIP/Ingrid (radiation tolerance, discharge protection, rate effects)

WG3: applications beyond HEP, industrial applications (X-ray diffraction, homeland security)

WG4: microtracking; neBEM field solver, electroluminescence simulation tool, Penning transfers, GEM charging up; MM transparency and signal

WG5: scalable readout system; Timepix multi-chip MPGD readout

WG6: CERN MPGD Production Facility; TT Network

WG7: RD51 test beam facility (November 2009 - 8 groups/5 setups)

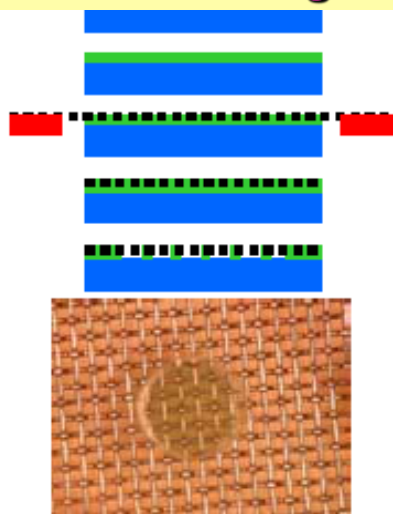
RD 51 WG1- MPGD Technology and New Structures

Objective: Detector design optimization, development of new multiplier geometries and techniques.

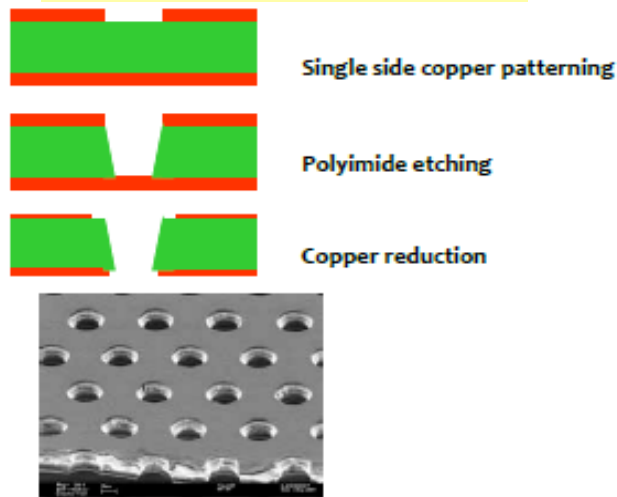
- **Development of Large Area MPGD (production of demonstrators)**



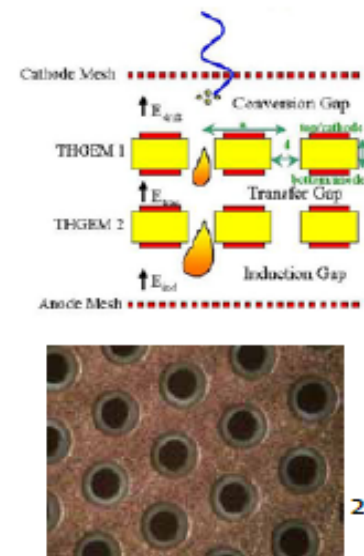
Bulk Micromegas



NEW - Single mask GEM technique

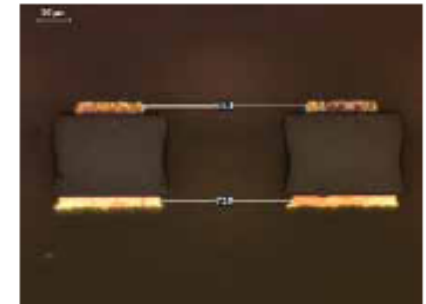
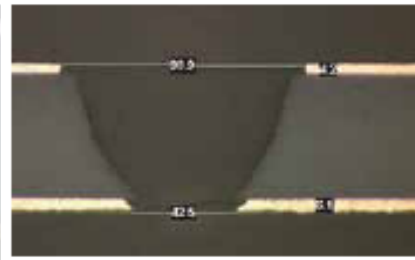
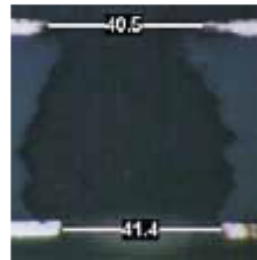


THGEM

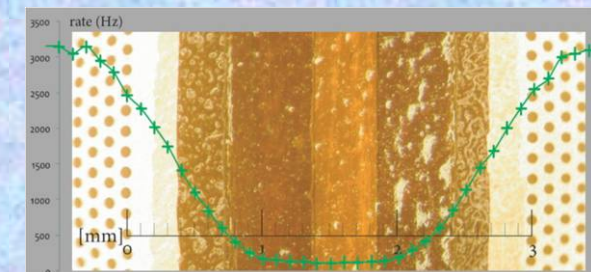
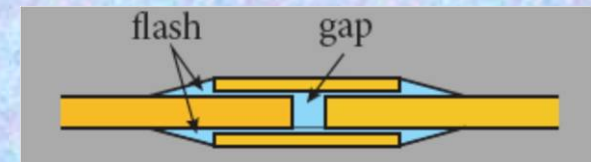


Large Area GEM Detector Development

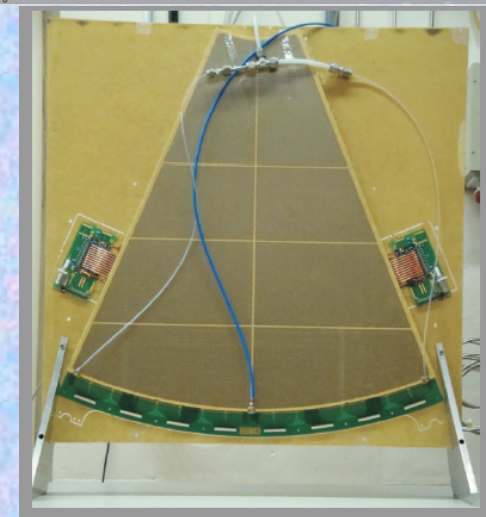
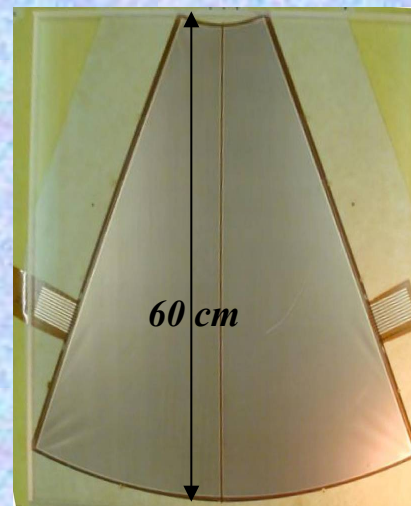
**New single mask technology:
Development and evaluation
With small prototypes**



**GEM foils splicing
Technology development
and tools**



**TWO-SECTORS TRIPLE-GEM
PROTOTYPE FOR
TOTEM T1 UPGRADE
(60x60 cm²)**



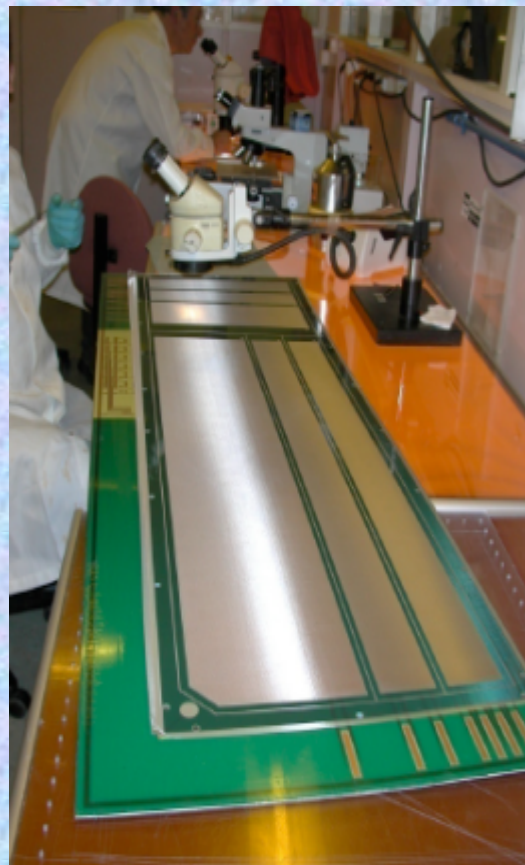
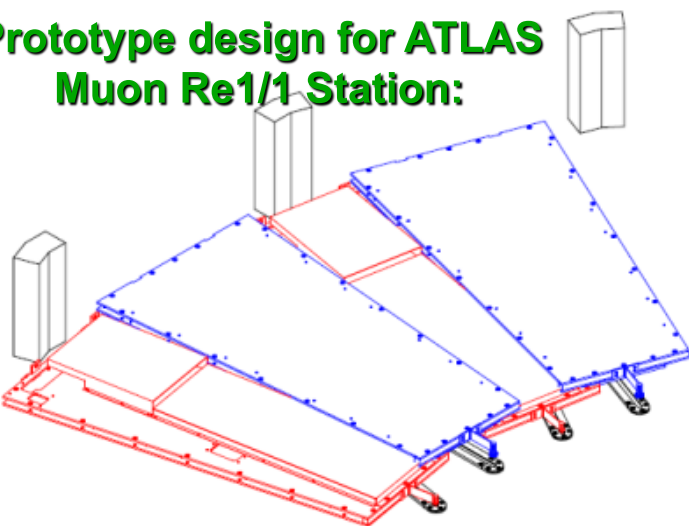
Large Area Micromegas Detector Development

ATLAS MAMMA Collaboration:

On the road to large area detectors:
(1.5 * 0.5 m²) - Half the final size

Segmented mesh,
250 and 500 μm strip pitches,
Longer strips (350 & 850 μm)

Prototype design for ATLAS
Muon Re1/1 Station:



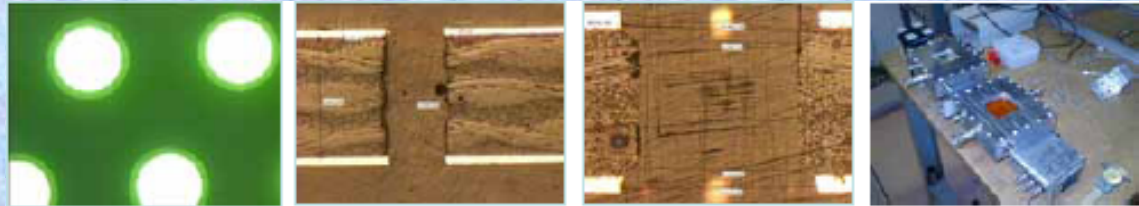
Study of resistive coatings for
spark protection (smaller prototypes)



**Uniformity, robustness, easy fabrication.
no support frames, small dead regions
& “Full path of industrial production”**

Development of UV Large Photon Detectors based on THGEM

**Technology
Development
& Prototype
Construction**



300x300mm² THGEM
90,000 0.5mm diameter holes
(Print Electronics, IL)

600x600mm² THGEM
600,000 0.4mm diameter holes
(Eltos, IT)



Industry: square-meters possible

Status: so far only “mechanical” electrodes

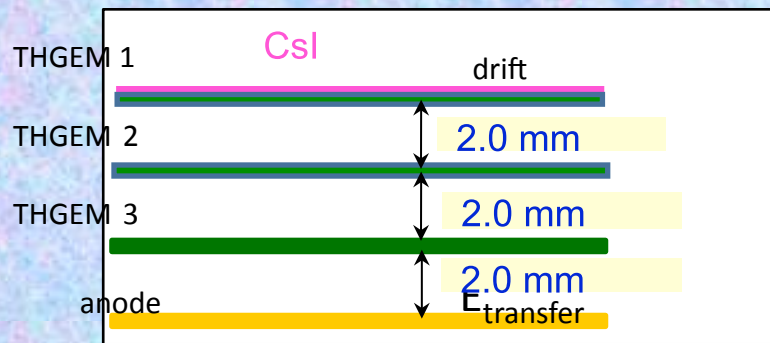
RD 51 WG2 - Common Characterization and Physics Issues

Objective 1: Development of common standards and comparison of different technologies, performance evaluation of different MPGD detectors.

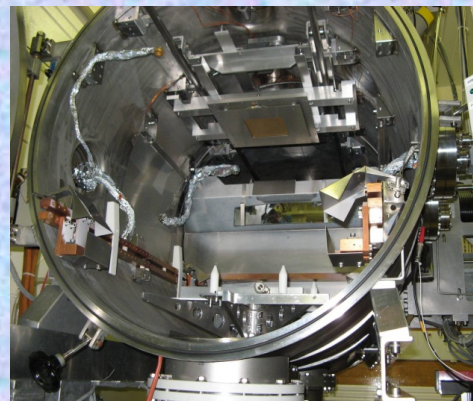
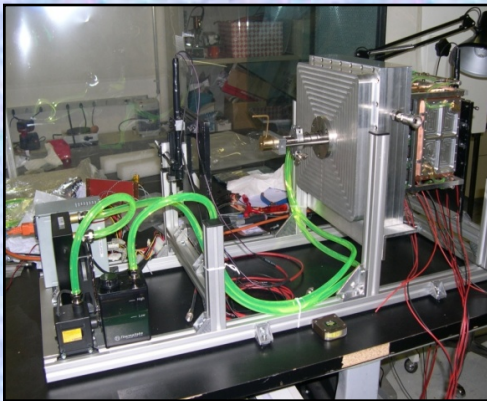
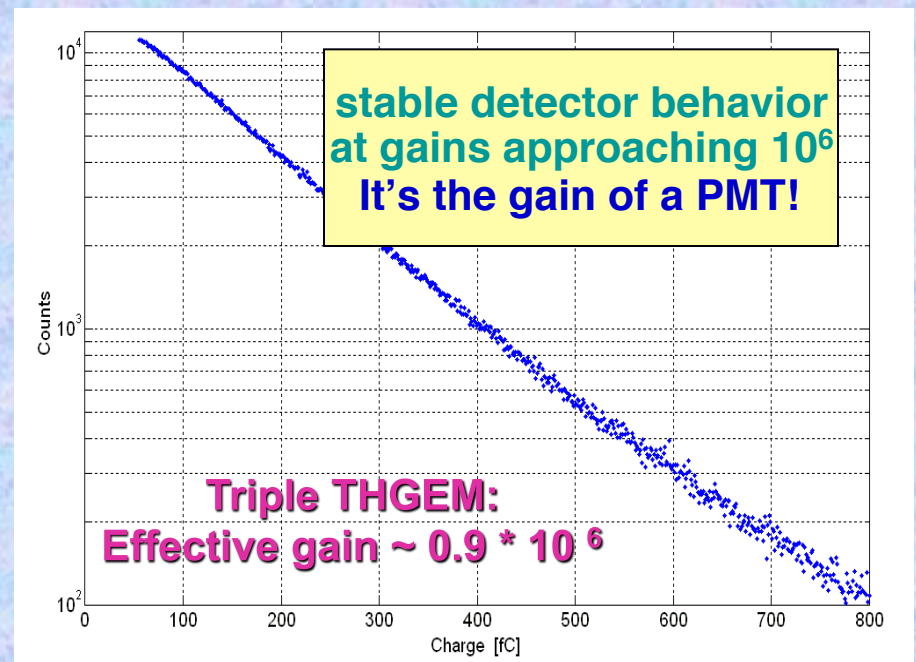
Objective 2: Development of radiation-hard gaseous detectors operating beyond the limits of present devices.

- Single electron response, charging up (gain stability) and rate capability issues

3 THGEM Structure:

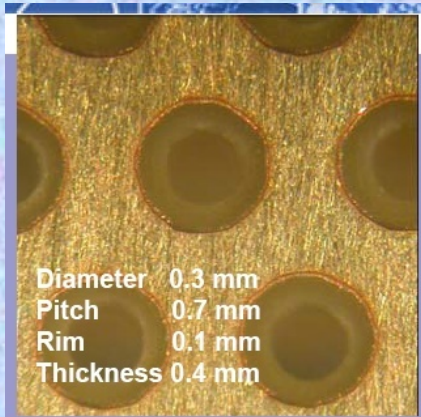


Amplitude distribution for single photons:

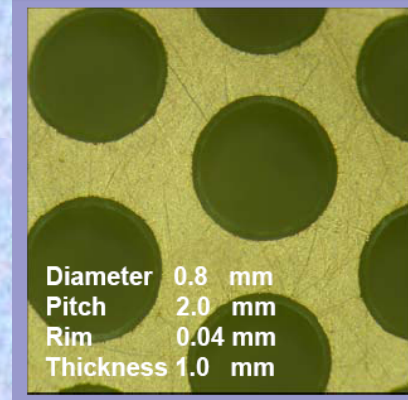


Detector Design Optimization and New Geometries

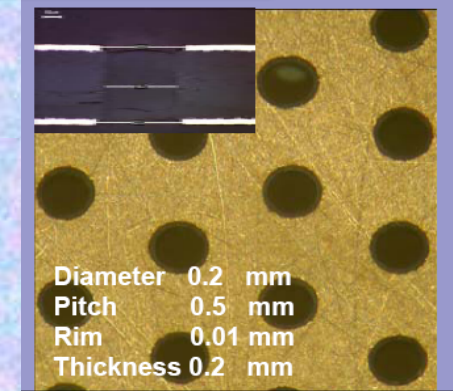
Choice of geometry (max. gain, stability) of THGEM Detectors:



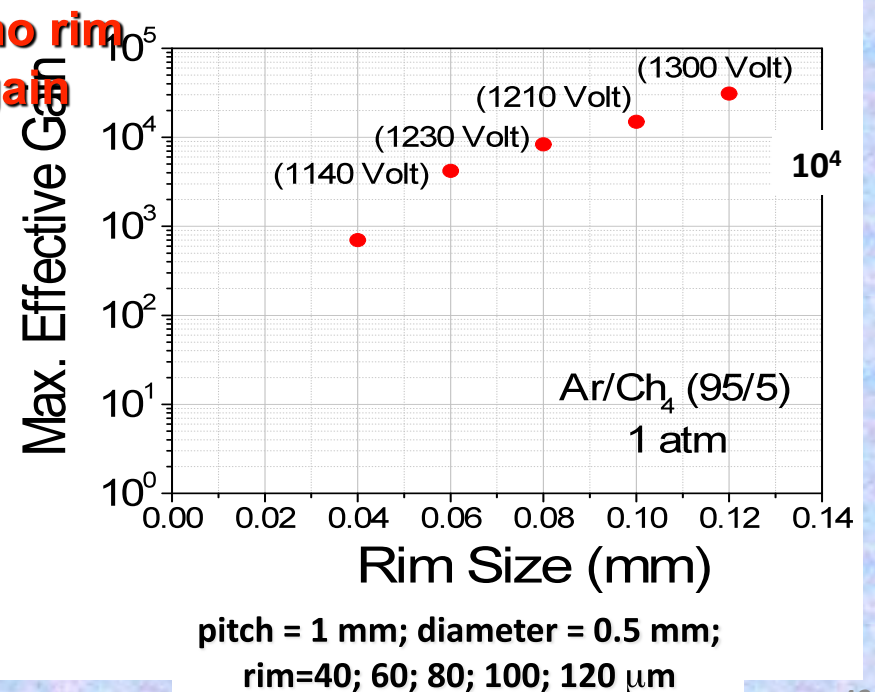
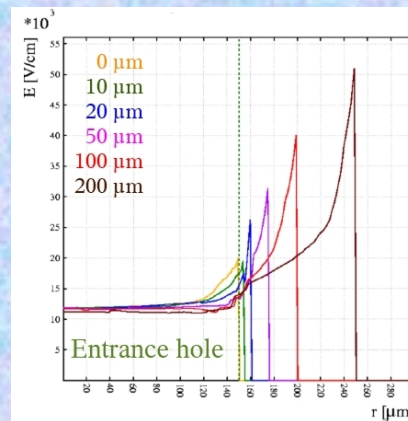
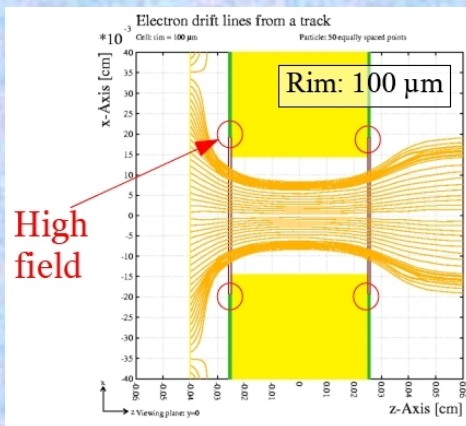
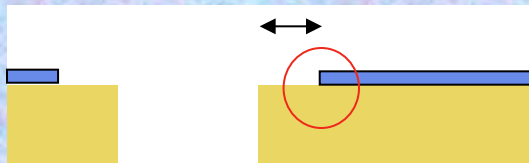
Mask etching + drilling; rim = 0.1mm



Drilling + chemical rim etching without mask

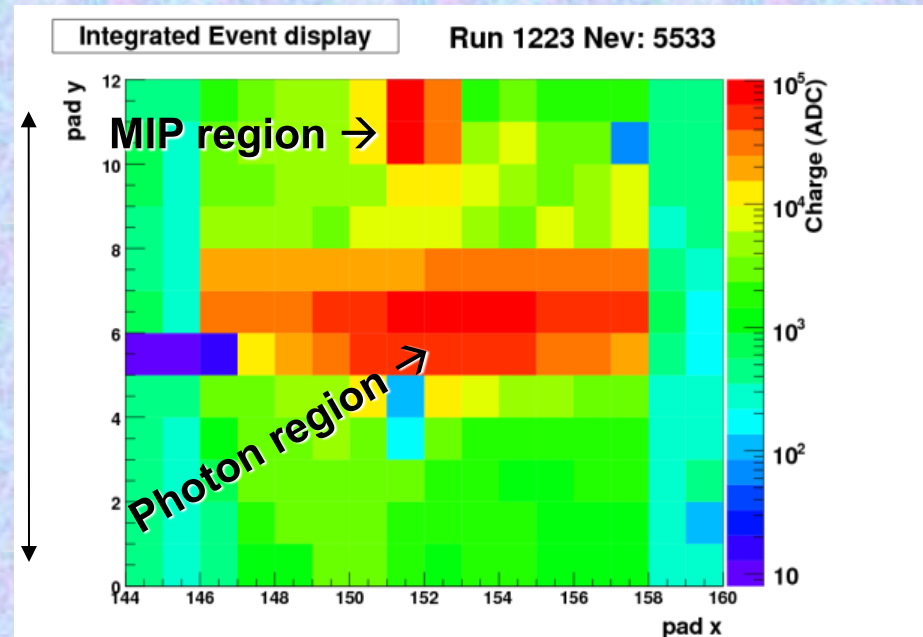
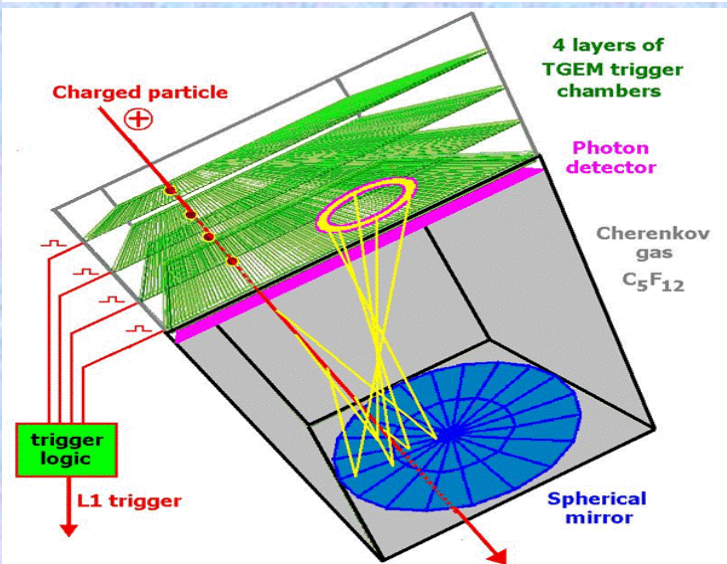
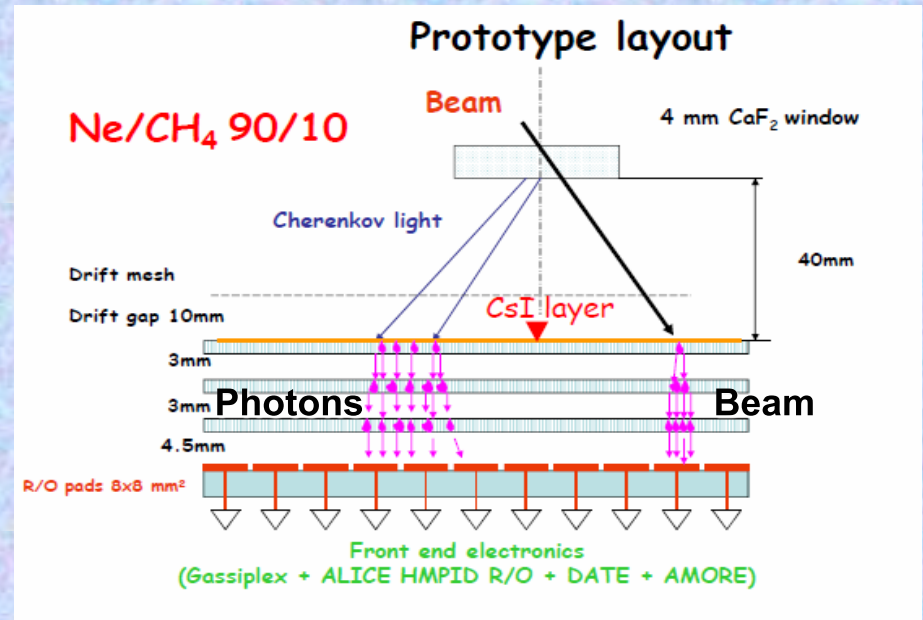
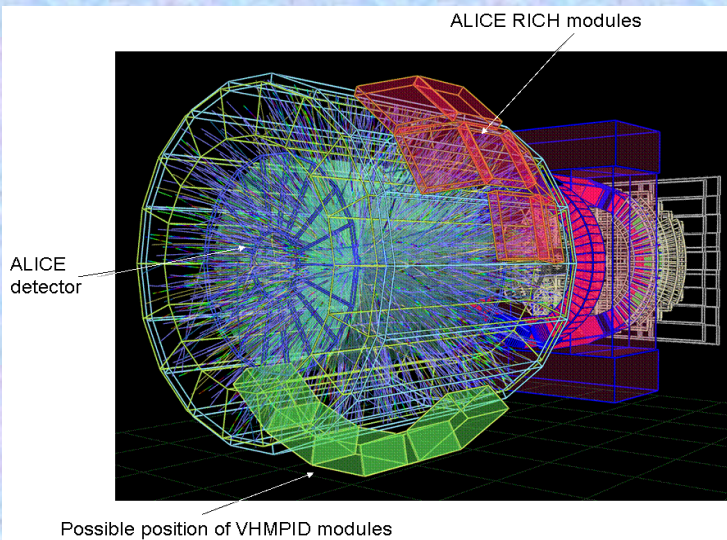


Best stability (no charging up): Holes with no rim
But: no-rim resulted in 10-100 times lower gain



Detection of Cherenkov Light with CsI coated triple THGEM

3THGEM Detector is proposed for Very High Momentum Particle Identification Detector (VHMPID) for ALICE

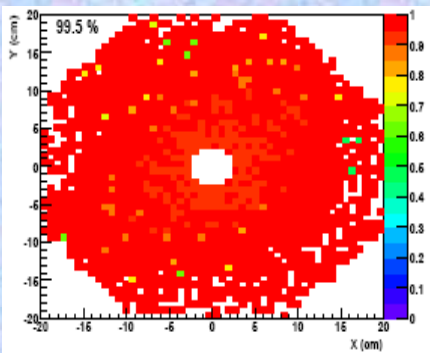
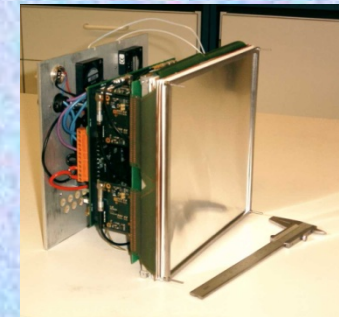
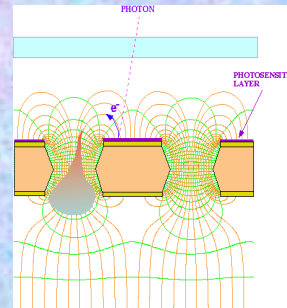
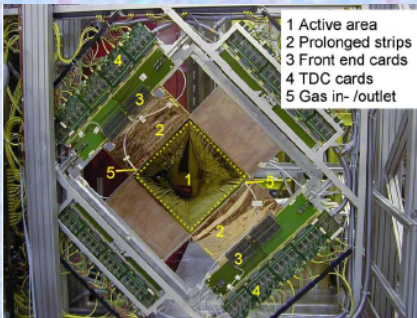


RD 51 WG3 - Applications

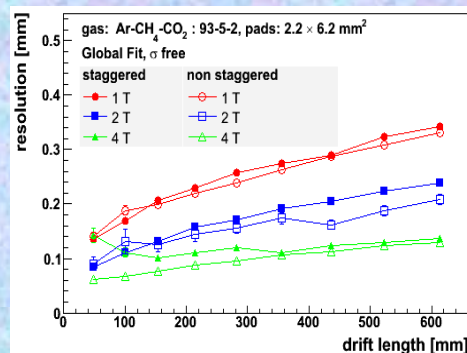
Objective: Evaluation and optimization of MPGD technologies for specific applications.

- MPGD based detectors for tracking and triggering (including Muon Systems).
- MPGD based Photon Detectors (e.g. for RICH)
- Applications of MPGD based Detectors for
 - Cryogenic Detectors for
 - X-ray and neutron imaging
 - Astroparticle physics applications
 - Medical applications.
 - Synchrotron Radiation, Plasma Diagnostics and Homeland Security applications.

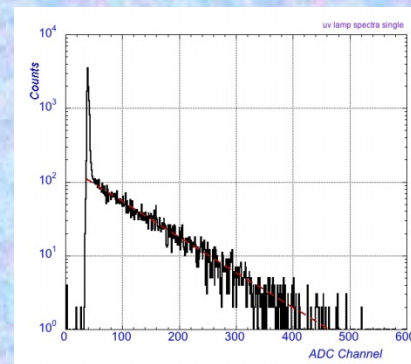
Applications area will benefit from the technological developments proposed by the Collaboration; however the responsibility for the completion of the application projects lies with the institutes themselves.



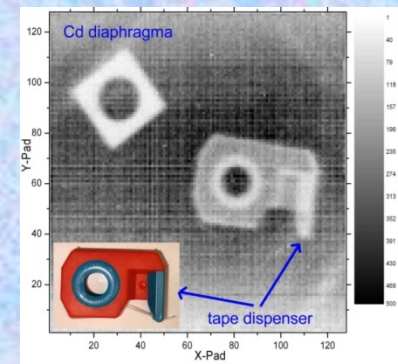
Tracking



TPC readout



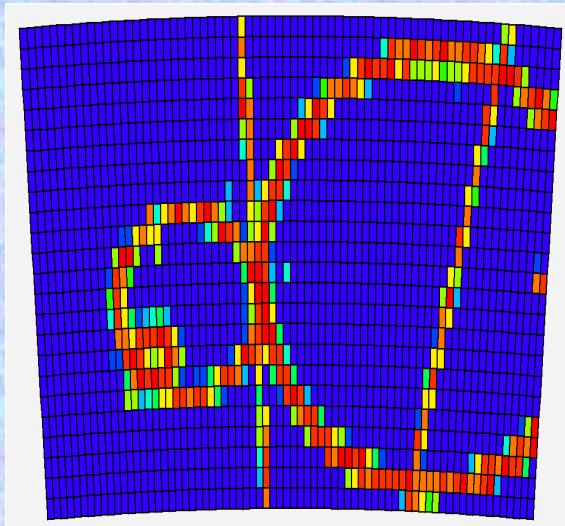
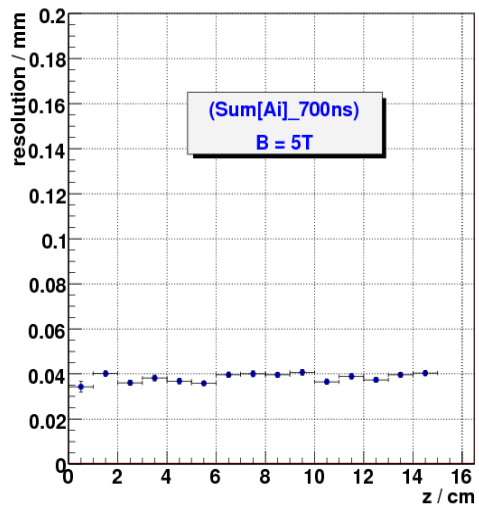
UV photon detection



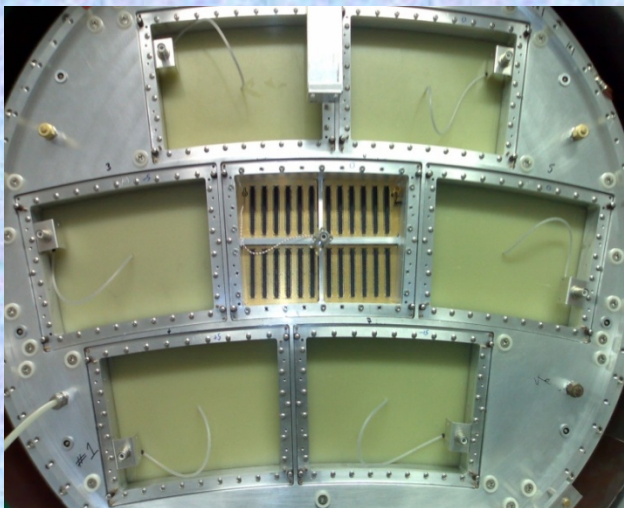
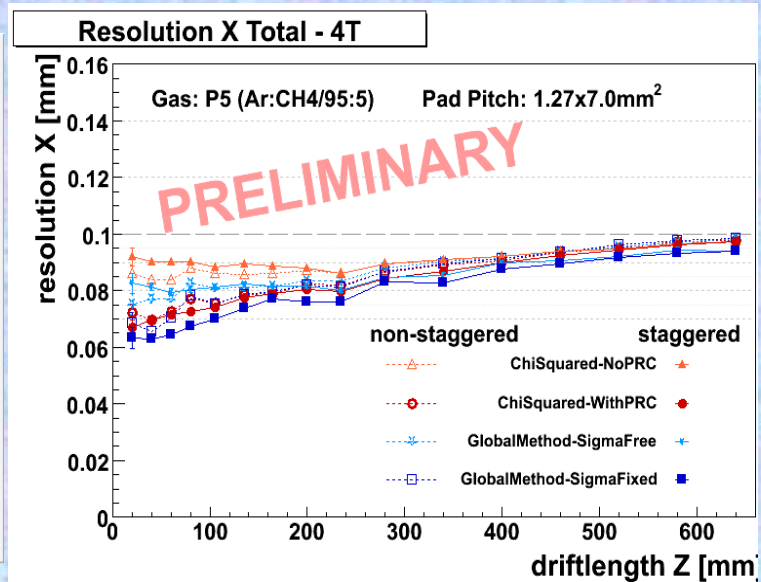
Neutron detection

Micromegas/GEM for the ILC TPC

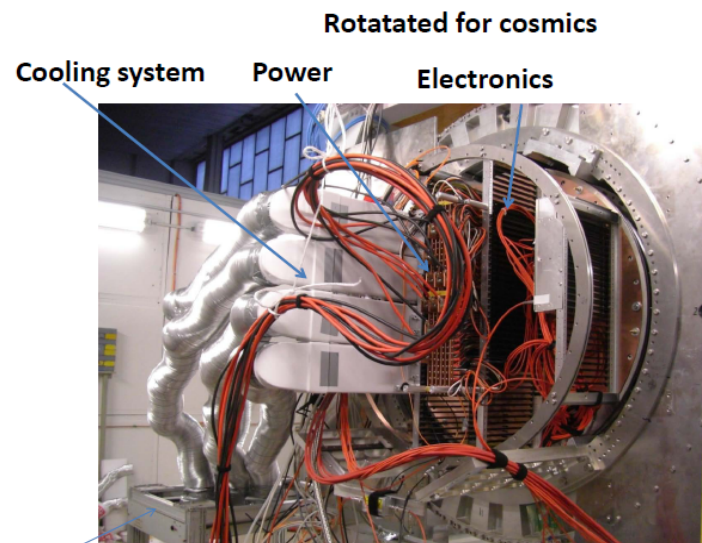
Micromegas TPC



GEM TPC



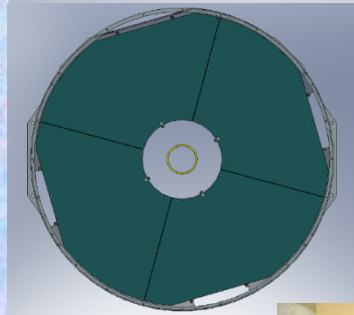
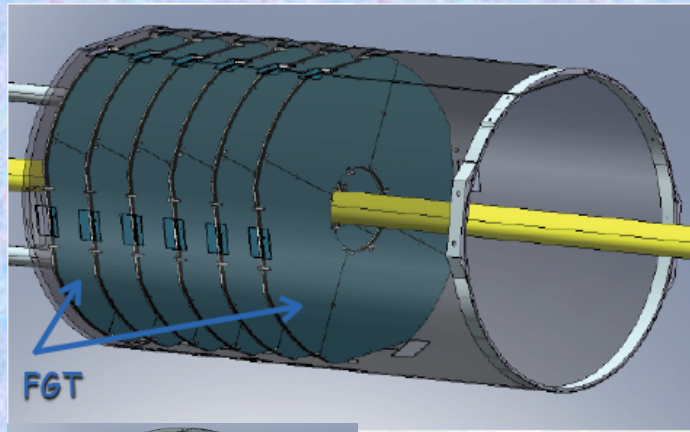
Large Prototype tests in 2009



Fans – now at a location with less magnetic field

GEM - Gas Electron Multiplier

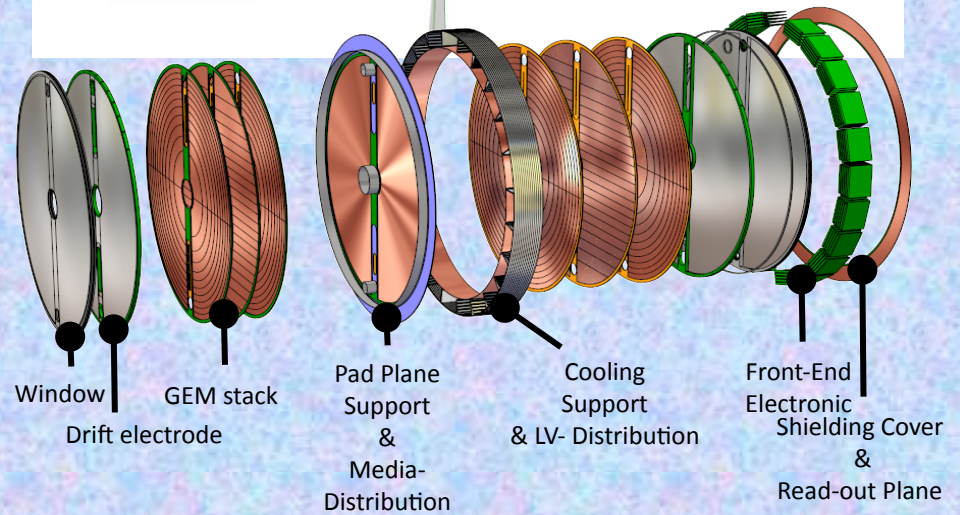
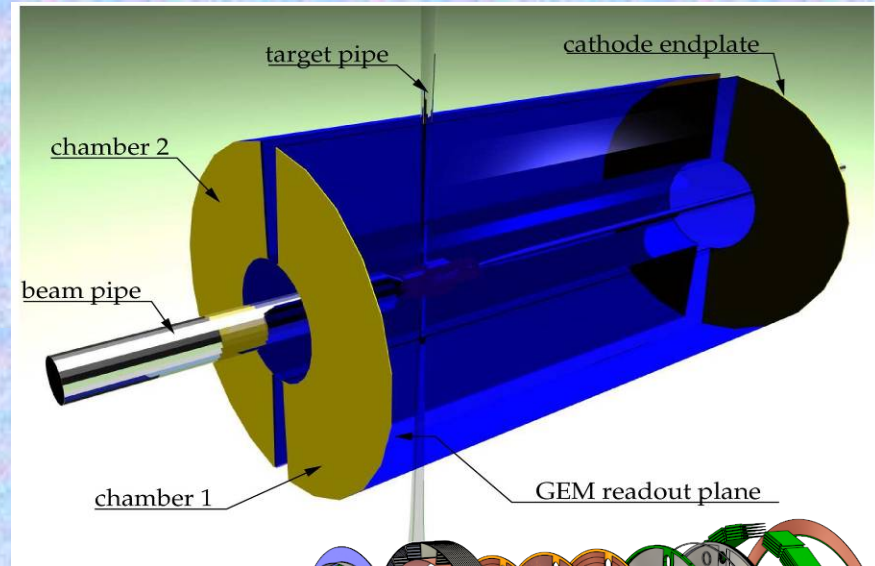
STAR GEM



Foils production
and Q&A by
the Tech-Etch
company

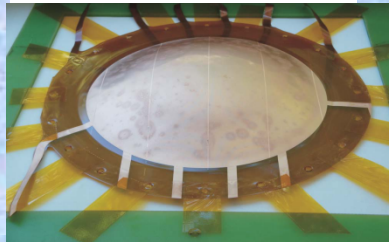
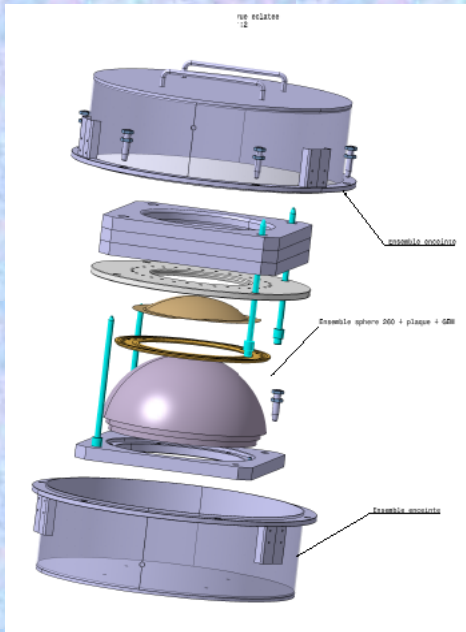
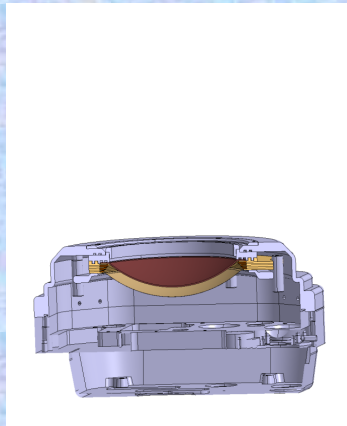
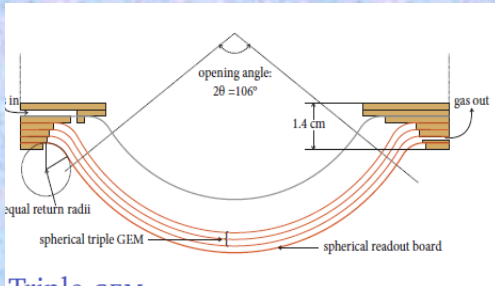


PANDA TPC and Planar Trackers

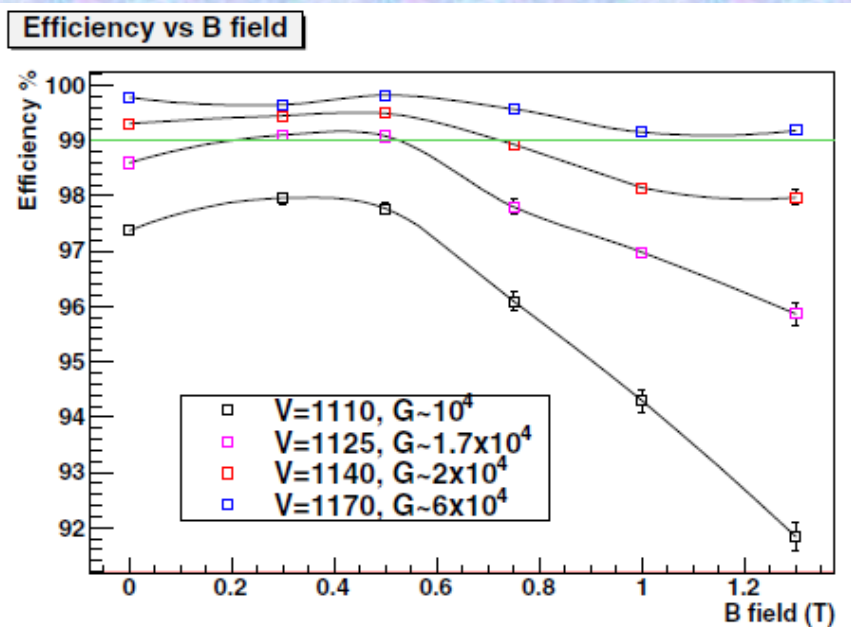
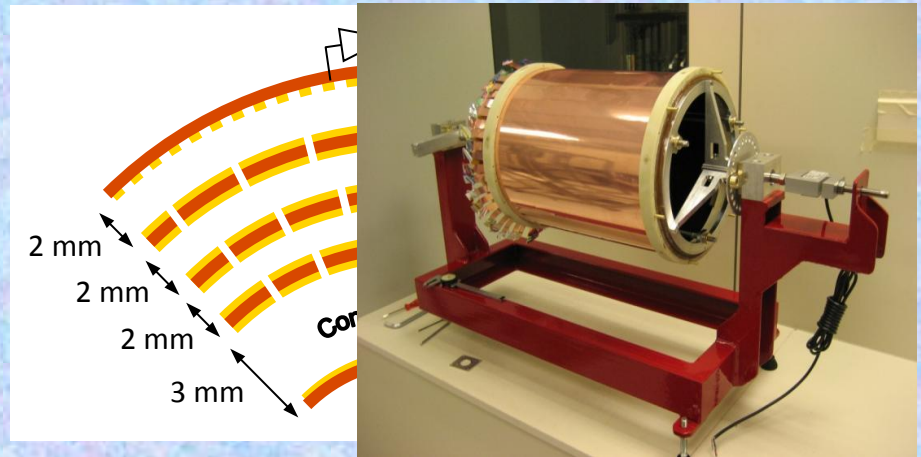


GEM - Gas Electron Multiplier

Spherical GEM for X-Ray diffraction application



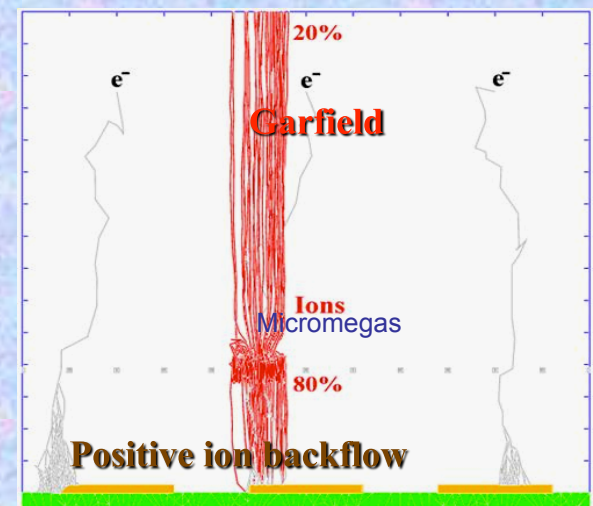
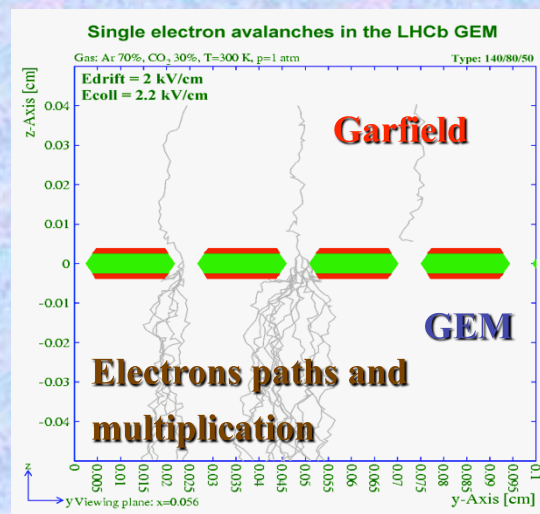
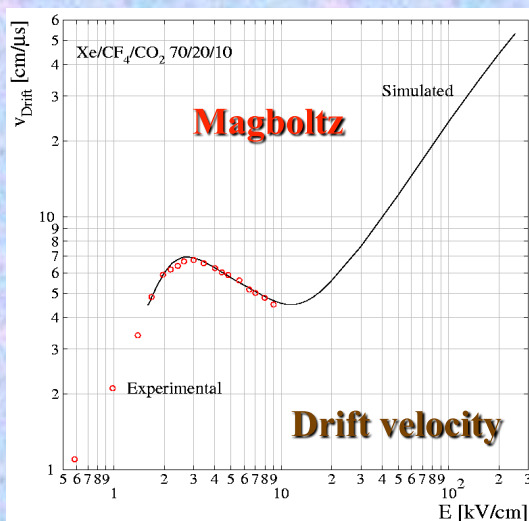
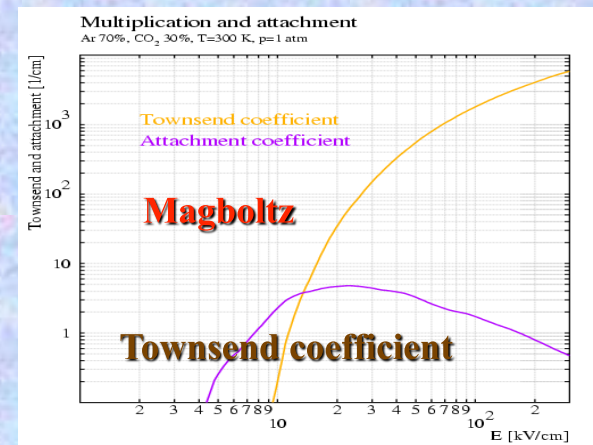
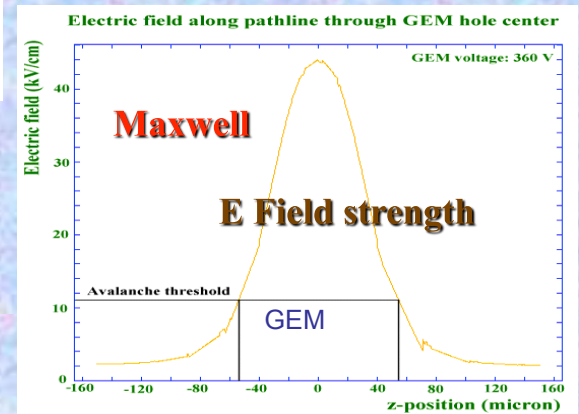
KLOE - Cylindrical Triple GEM



RD51 WG4 - Simulation and Software Tools

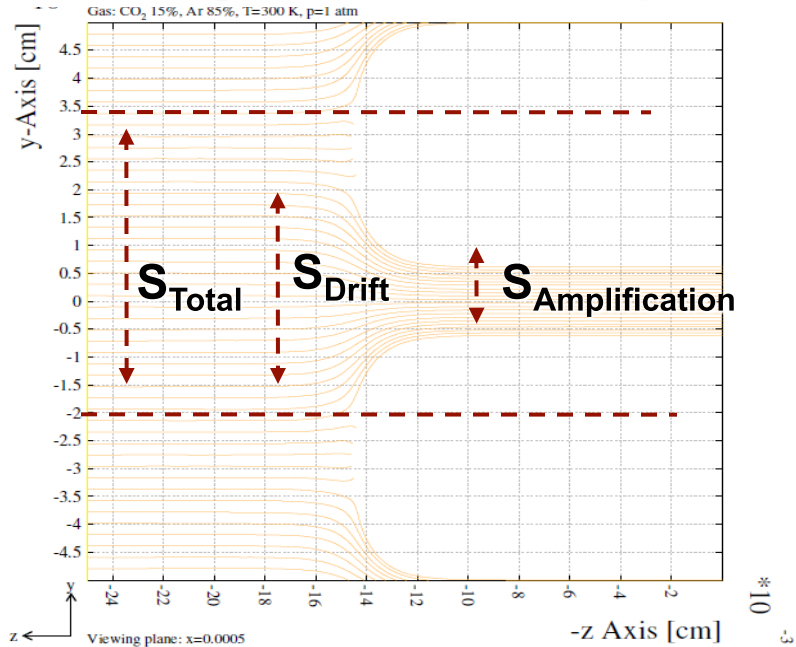
Objective: Development of common, open access software and documentation for MPGD simulations

- Development of common platform for detector simulations (gas detector simulation in Geant4, interface to ROOT).
- Development of algorithms (in particular in the domain of very small scale structures - implementation of nearly exact boundary element method interfaced to Garfield).
- Simulation improvements (penning transfer studies, photon excitation via excimers)

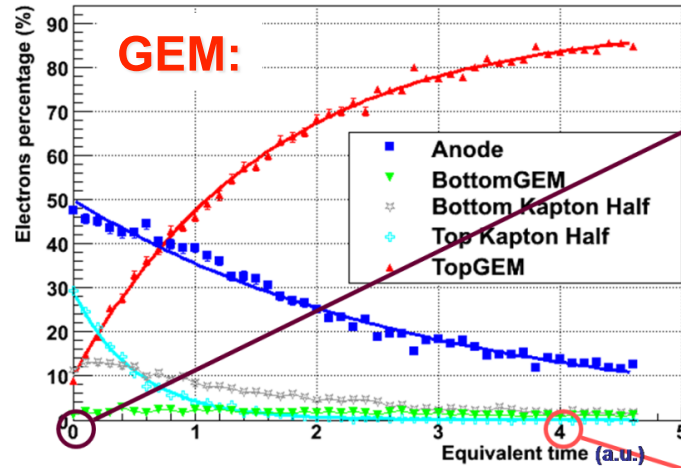


GEM and Micromegas: Charging-Up and Transparency Simulation

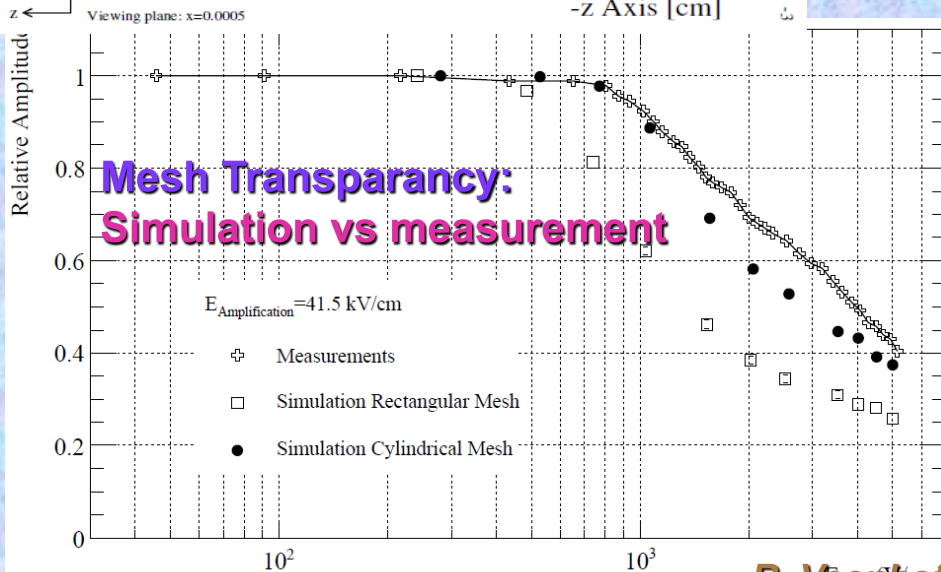
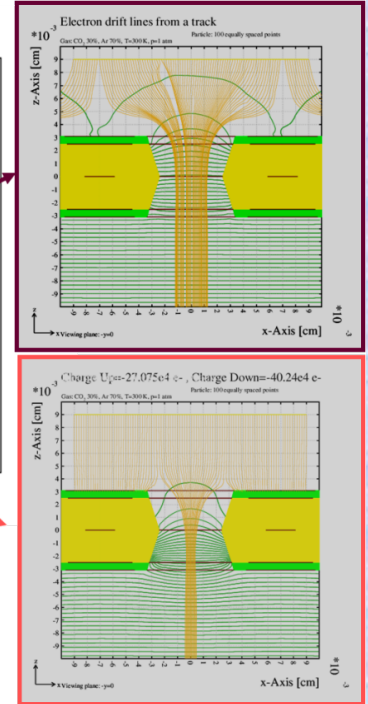
Micromegas Electron Transparency



Iterative method with "0.1s equivalent" charge step



First "manual" iterative method
GEM simulation with "0.1s
equivalent charge step



Mesh Transparency:
Simulation vs measurement

Micromegas Electron Transparency:

$$P(e\text{-collection}) = S_{\text{Drift}} / S_{\text{Total}}$$

$$= S_{\text{Amplification}} \times \text{Field-Ratio} / S_{\text{Total}}$$

$$\sim (\text{hole diameter})^2 \quad \sim (\text{wires pitch})^2$$

RD51 WG5: MPGD Electronics Developments

Objective: Readout electronics optimization and integration with detectors.

Definition of front-end electronics requirements for MPGDs

**Survey of existing conventional readout systems:
GASSIPLEX, ASDQ, CARIOCA, ALTRO, SUPER ALTRO; APV, VFAT**

| Name | Exp | Det | #ch | Shaper (ns) | Noise | Range (fC) | PoL | ADC | F (MHz) | P/ch. (mW) | Feat. | Tech | Rad hard |
|-------------|-----------|-----------|-----|----------------------------|--------------------------------------|---------------------------|------|------|------------|-------------|------------|-----------------|----------|
| APV25 | CMS | Si strip | 128 | 50 | 270+38e/pF | 20 | both | A | 40 | 2.7 | PD, PR | 0.25 CMOS | 10 |
| AFTER | T2K | TPC | 72 | 100-2000 | (350-1800) + s-gauss (22-1.8)e/pF | 19 | both | A | 1-50 (100) | 7.5 | VG, VS | 0.35 CMOS | no |
| MSGCROC | DETNI | Gas strip | 32 | T: 25 E: 85 | 2000e @ 40pF | 800 | both | A, 1 | 2ns TDC | | VG, ZS | 0.35 CMOS | no |
| Beetle | LHCb | | 128 | 25 | 500+50e/pF | 17.5 | both | A/1 | 40 | 5.2 | F-OR | 0.25 CMOS | 40 |
| VFAT | TOTEM | | 128 | 22 | 650+50e/pF | 18.5 (cal) 2000 th<100 | both | 1 | 40 | 4.47 | F-OR | 0.25 CMOS | 50 |
| NINO | ALICE | TPC | 8 | 1 | 1900+165/pF | 2000 | both | 1 | async | 30 | BR | 0.25 CMOS | no |
| CARIOCA | LHCb | MWPC | 8 | <15 @ 220pF | 2000+40e/pF | 250 | both | 1 | async | 46 | BR | 0.25 CMOS | 20 |
| PASA+ ALTRO | ALICE TPC | TPC | 16 | 190 _{thm} s-gauss | 570e @ 20 pF | 160 | both | 10 | 20 | < 40 | BC, TC, ZS | 0.35, 0.25 CMOS | |
| SVX4 | CDF, D0 | Si strip | 128 | 100-360 | 410+45e/pF | 60fC | neg | 8 | 106 (212) | 2 | ZS | 0.25 CMOS | 20 |
| SPIROC | ILC, T2K | SIPM | 36 | A: 25-175 T: 10 | A: 1/11pe; T: 1/24pe | 2000 pe | neg | 8-12 | 100ps TDC | 0.025 pulse | dual-gain | 0.35 SiGe | no |

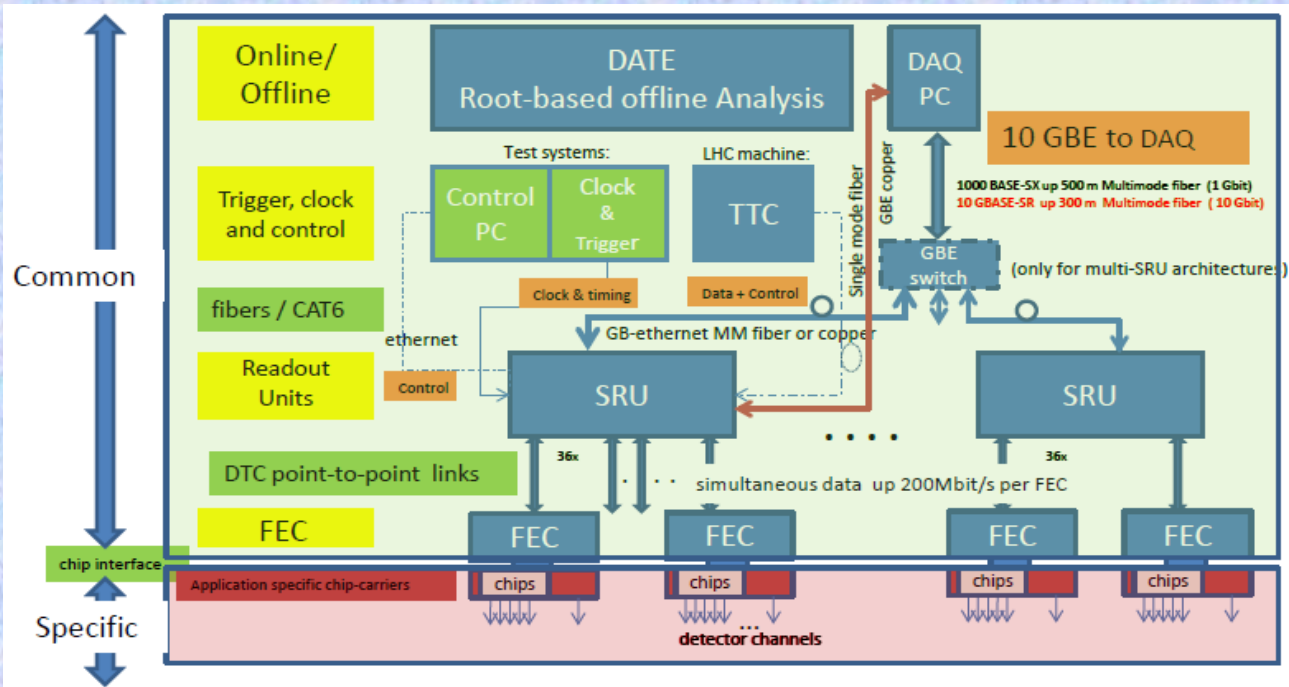
Legend: PD = peak detection, PR = pile-up rejection, VG = variable gain, VS = variable shaping, F-OR = fast-OR, BR = baseline restorer, BC = baseline correction, TC = tail correction, DC = data compression, ZS = zero suppression

- shaping time: 5ns .. 1us
- dynamic range: <100fC
- power: < 10 mW/ch (?)
- ADC accuracy: 10 bits (?)
- TDC accuracy: 1ns

From Chip Matrix to the “Ideal MPGD Chip” → develop 2-3 chip concepts for the MPGDs

We need an APV25 chip with variable gain and shaping time like the AFTER chip, dynamic range like MSGCROC, integrated fast-OR like Beetle, integrated ADC like SVX4, digital signal processor like ALTRO

Development of Portable Multi-Channel DAQ Systems for MPGD

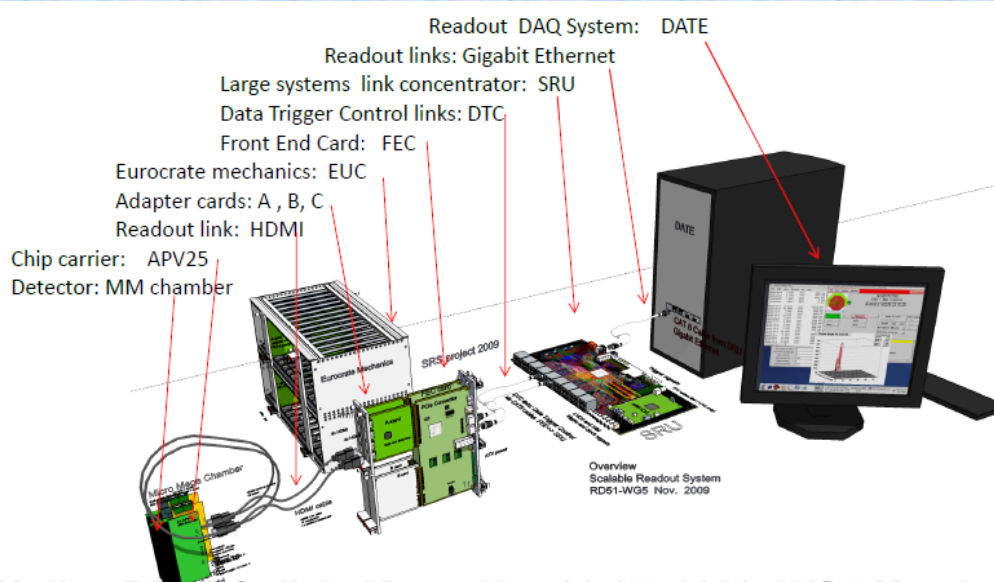


**“RD51 Common Project”
(financed by the RD51)→**

**First prototype system
to be ready in June 2010**

- Scalability from small to large system
- Common interface for replacing the chip frontend
- Integration of proven and commercial solutions for a minimum of development
- Default availability of a very robust and supported DAQ software package.

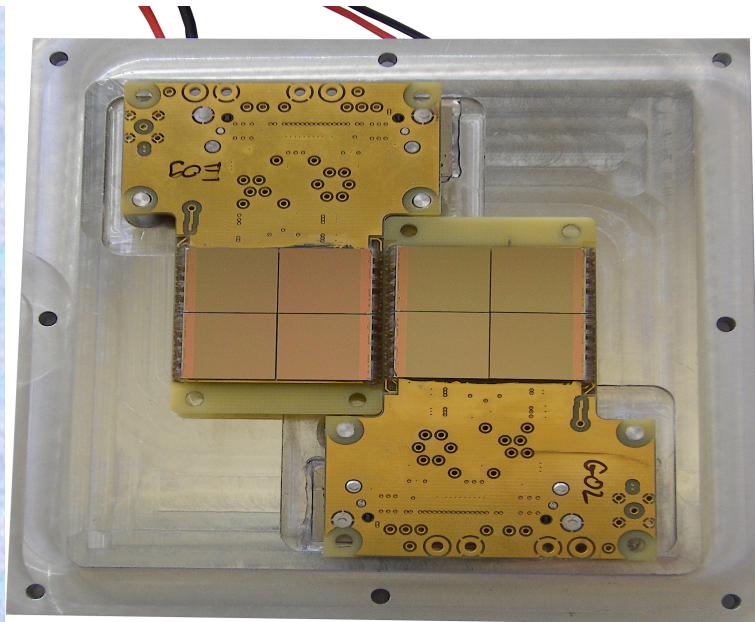
→ Scalable Readout System



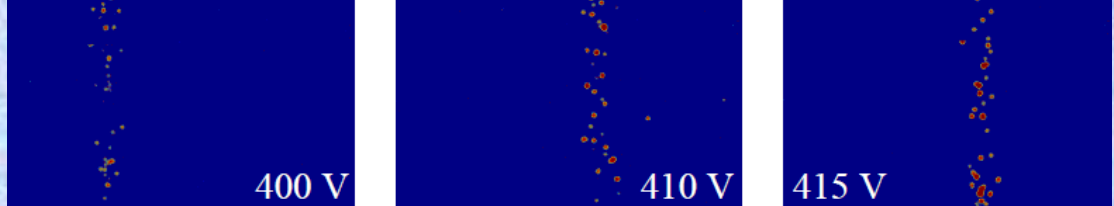
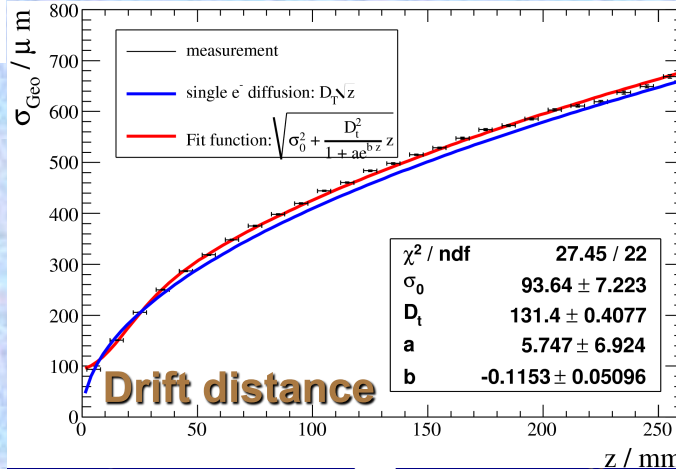
H. Muller, RD51 Collab. Meet., Nov.23-25, 2009, WG5 Meeting

Development of Large Area Detectors with Pixel Readout

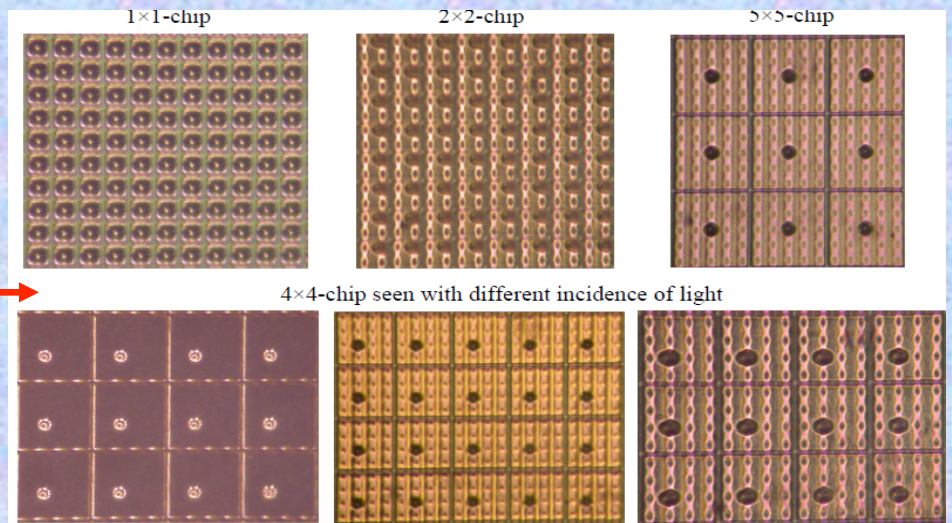
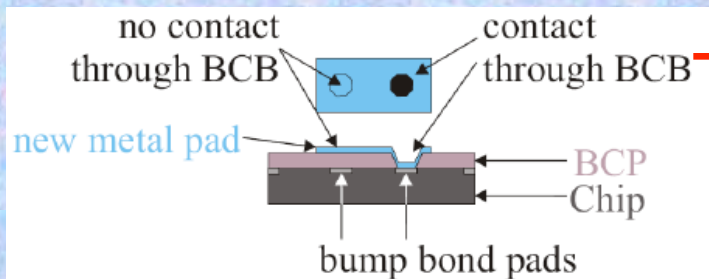
8 Timepix Readout Matrix (~ 3* 6 cm²)
55*55 μm² pixel size



4 Chips + 3GEM (150 GeV muons after drifting 25 cm)



Test chips with larger pixels:
 expensive to design new chips, easier to combine pixels by post-processing
 (55*55, 110*110, 220*220, 275*275 μm²)



J. Kaminski et al, RD51 Collab. Meet., Nov.23-25, 2009, WG7 Report

RD 51 WG6 - MPGD Production

Objective: Development of cost-effective technologies and industrialization

1) Current: CERN-MPGD workshop is the UNIQUE MPGD production facility (generic R&D, detector components production, quality control)

| Detector Technology | Currently produced cm * cm | Future Requirements cm * cm |
|-------------------------|-------------------------------|-----------------------------------|
| GEM | 40 * 40 | 50 * 50 |
| GEM, single mask | 70 * 40 | 200 * 50 |
| THGEM | 70 * 50 | 200 * 100 |
| RTHGEM, serial graphics | 20 * 10 | 100 * 50 |
| RTHGEM, Kapton | 50 * 50 | 200 * 100 |
| Micromegas, bulk | 150 * 50 | 200 * 100 |
| Micromegas, microbulk | 10 * 10 | 30 * 30 |

**RD51
Collaboration
Survey:**

2) Future MPGD R&D: Reinforcement of CERN-MPGD workshop infrastructure to produce 2x1m Bulk Micromegas and 2x0.5 m GEMs has been approved by CERN Management (Nov. 2009)

3) Technology Industrialization → transfer “know-how” from CERN workshop to industrial partners for MASS PRODUCTION

Technology Industrialization (potential partners)

THGEM Technology – ELTOS S.p.A. (Italy)

GEM Technology

- New Flex (Korea, Seoul)
- Tech-ETCH (USA, Boston)
- Scienergy (Japan, Tokyo)

Micromegas Technology

- TRIANGLE LABS (USA, Nevada)
- SOMACIS (Italy, Castelfidardo)
- CIRE (France, Paris)

Technology Transfer - Contract summary

12/9/2008

SUMMARY

CERN has developed, and owns all rights to a technology concerning Radiation Detectors of Very High Performance and Planispherical Parallax-Free X-Ray Imager using Gas Electron Multipliers (GEM foil technology). GEM technology is a proven concept of gas amplification that was introduced in 1996 by Fabio Sauli and GEM foils are currently being manufactured at a small workshop on CERN premises by the TS/DEM group. Furthermore, the use of GEM foils as gas detectors is also covered by a patent owned by CNRS (the CAT patent) to which CERN has a sub-licensable license.

SciEnergy is a Japanese company developing, manufacturing and selling X-Ray detectors systems. This company works closely with Hamagaki Laboratory (U. Tokyo) in Japan, and it is through the latter's involvement in the RD51 Collaboration that SciEnergy's interest in GEM foils grew. After initial contacts with participants to the RD51 Collaboration, SciEnergy approached CERN to request a license from CERN to manufacture and sell GEM foils and GEM based detector systems both to the R&D community and commercial end-users.

Scienergy, Japan signed license contract for GEMs

Partnership agreement for the development and implementation of spherical GEMs for X-Ray diffraction detectors

INCREASING EFFICIENCY OF TECHNOLOGY TRANSFER

ACTIVITIES IN MEMBER STATES

(Reported in CERN-Council-S/049,
September 7, 2009)

REPORT ON THE ACTIVITIES OF THE TECHNOLOGY TRANSFER NETWORK WITHIN THE FRAMEWORK OF THE EUROPEAN STRATEGY FOR PARTICLE PHYSICS

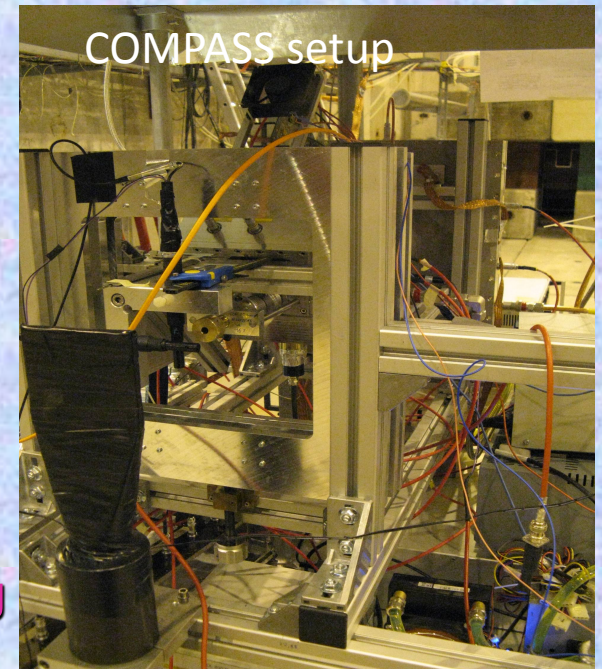
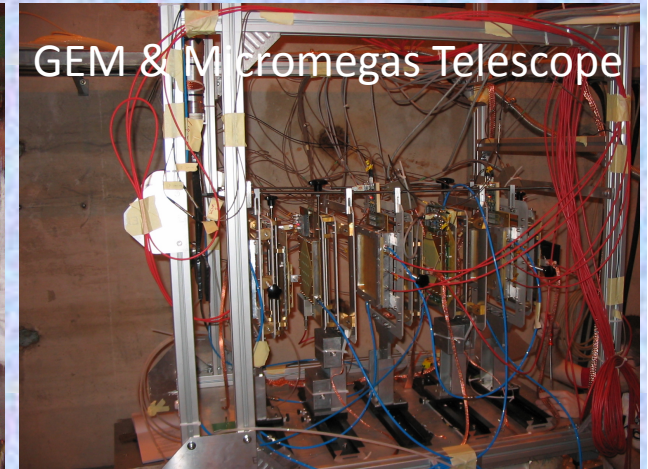
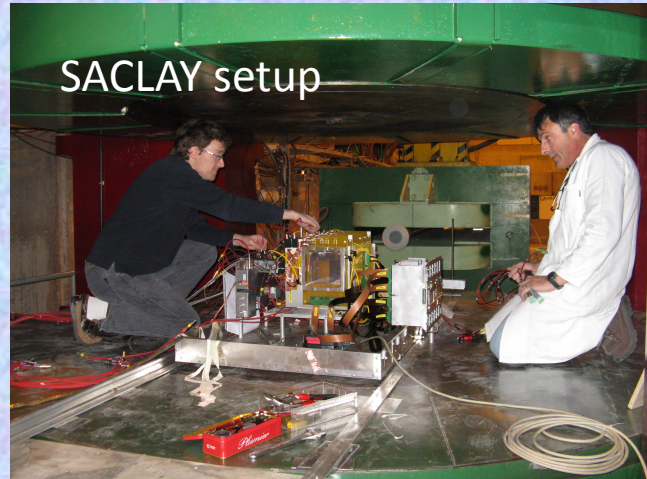
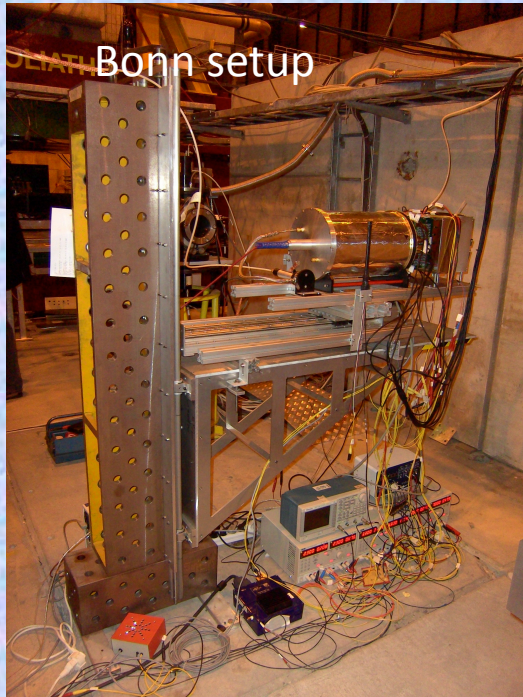
- **“One-stop licensing for industry” (bridging the gap between institutes and industry)**
- **The IP coming from the HEP research community is better identified and more visible**

The RD-51 collaboration² on Micro Pattern Gaseous Detectors (MPGD) accounts for more than 50 institutes including non-PP institutes interested in developing detectors targeted to their research needs. Detector developments rely on PP technologies, such as Gaseous Electron Multipliers (GEM), MicroMESH Gaseous Structure (MicroMEGAS), front-end readout and software. MPGD technologies are owned by organisations that are members of the TT Network and constitute therefore a very good case for technology pooling. Industry is willing to manufacture the technologies for the community's needs but has also shown interest in commercializing detectors provided a better understanding of the market potential is made available.

The TT Network considers MPGD as very illustrative of the PP community's assets and will therefore focus the first pilot on this case.

RD 51 WG7 - Common Test Facility

Objective: Design and maintenance of common infrastructure for detector characterization (“semi-permanent” test-beam infrastructure at CERN SPS@H4 beam)



- 8 RD51 groups have been taking data in parallel during the last test beam campaign (Oct. 22 – Nov. 2, 2009)

Summary and Outlook

- **RD51 aims at facilitating the development of advanced gas-avalanche detector technologies and associated electronic-readout systems → Many successful common projects were initiated during the first year of collaboration**
- **Industrial methods of MPGD production allows to extend technology to $\sim \text{m}^2$ areas → many potential MPGD applications within the HEP and beyond;**
- ***Collaboration with industrial partners is ongoing;***
- ***Progress in micro-pattern detector developments promises to extent the applicability of gaseous detectors to the precision tracking at high counting rates (large area coverage, low material budget, spatial resolution $\sim 30\text{-}50 \mu\text{m}$)***
- ***Modern, sensitive & low noise electronics will enlarge the range of applications***